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(12) **United States Patent**
Torii et al.

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(45) **Date of Patent:** **Aug. 6, 2013**

(54) **NONVOLATILE SEMICONDUCTOR
MEMORY DEVICE**

(56) **References Cited**

(75) Inventors: **Satoshi Torii**, Kawasaki (JP); **Kazuhiro Mizutani**, Kawasaki (JP); **Toshio Nomura**, Kawasaki (JP); **Masayoshi Asano**, Kawasaki (JP); **Ikuto Fukuoka**, Kawasaki (JP); **Hiroshi Mawatari**, Kawasaki (JP); **Motoi Takahashi**, Kawasaki (JP)

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(73) Assignee: **Fujitsu Semiconductor Limited**,
Yokohama (JP)

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(21) Appl. No.: **13/188,869**

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(22) Filed: **Jul. 22, 2011**

(Continued)

(65) **Prior Publication Data**
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Primary Examiner — Hoai V Ho
Assistant Examiner — James G Norman
(74) *Attorney, Agent, or Firm* — Westerman, Hattori, Daniels & Adrian, LLP

Related U.S. Application Data

(60) Division of application No. 12/411,938, filed on Mar. 26, 2009, now Pat. No. 8,014,198, which is a continuation of application No. PCT/JP2006/319591, filed on Sep. 29, 2006, and a continuation of application No. PCT/JP2007/068849, filed on Sep. 27, 2007.

(57) **ABSTRACT**

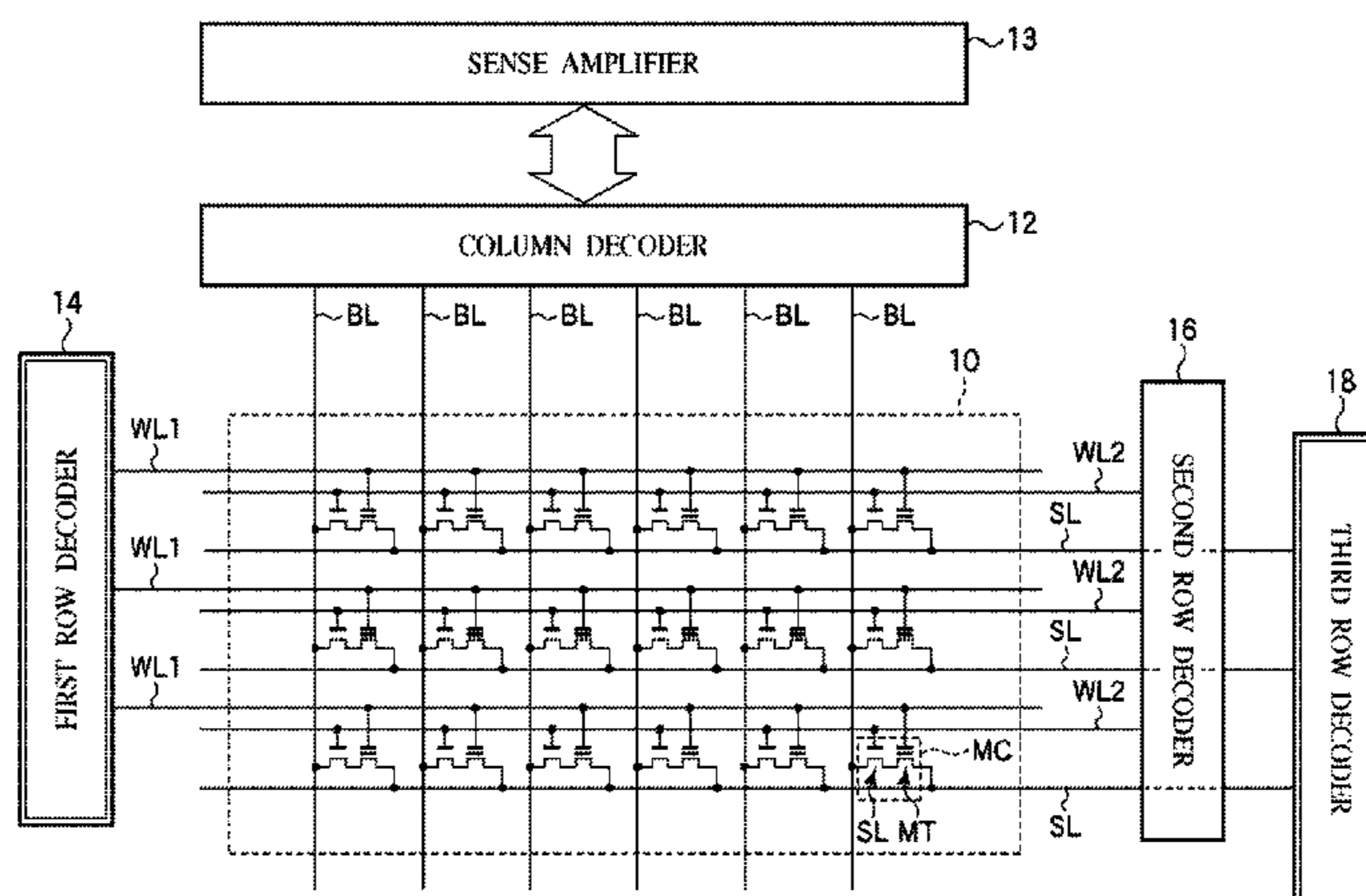
A nonvolatile semiconductor memory device including a memory cell array of memory cells arranged in a matrix, each of which includes a selecting transistor and a memory cell transistor; a column decoder controlling the potential of bit lines; a voltage application circuit controlling the potential of the first word lines; a first row decoder controlling the potential of the second word lines; and a second row decoder controlling the potential of the source line. The column decoder is formed of a circuit whose withstand voltage is lower than the voltage application circuit and the second row decoder.

(51) **Int. Cl.**
G11C 16/04 (2006.01)
G11C 16/06 (2006.01)
H01L 29/792 (2006.01)

(52) **U.S. Cl.**
USPC **365/185.05**; 365/185.18; 257/324;
257/E29.309

(58) **Field of Classification Search**
None
See application file for complete search history.

7 Claims, 70 Drawing Sheets



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Taiwanese Office Action dated Oct. 22, 2008, issued in corresponding Taiwanese Patent Application No. 095137268.

* cited by examiner

FIG. 1

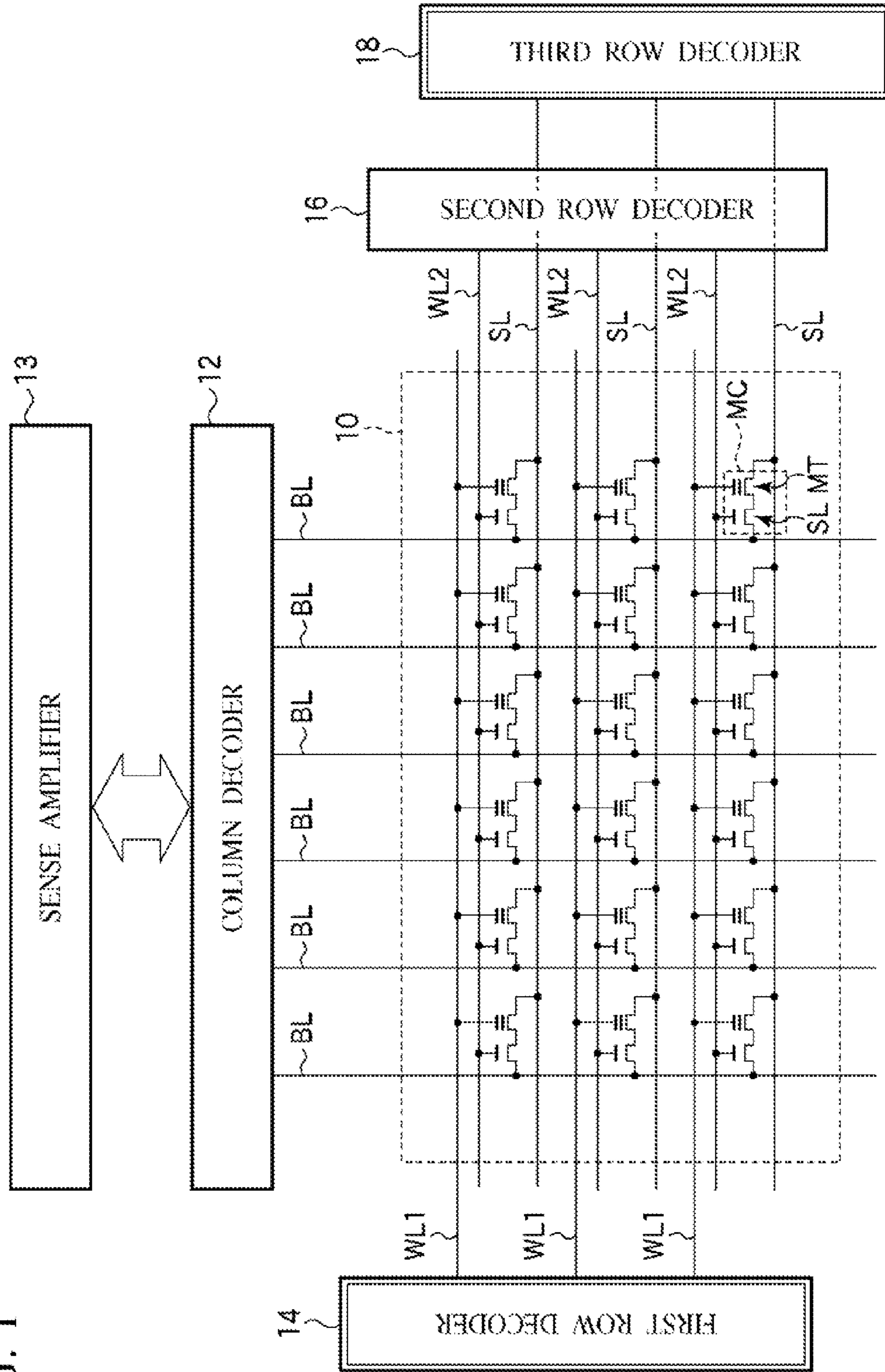


FIG. 2

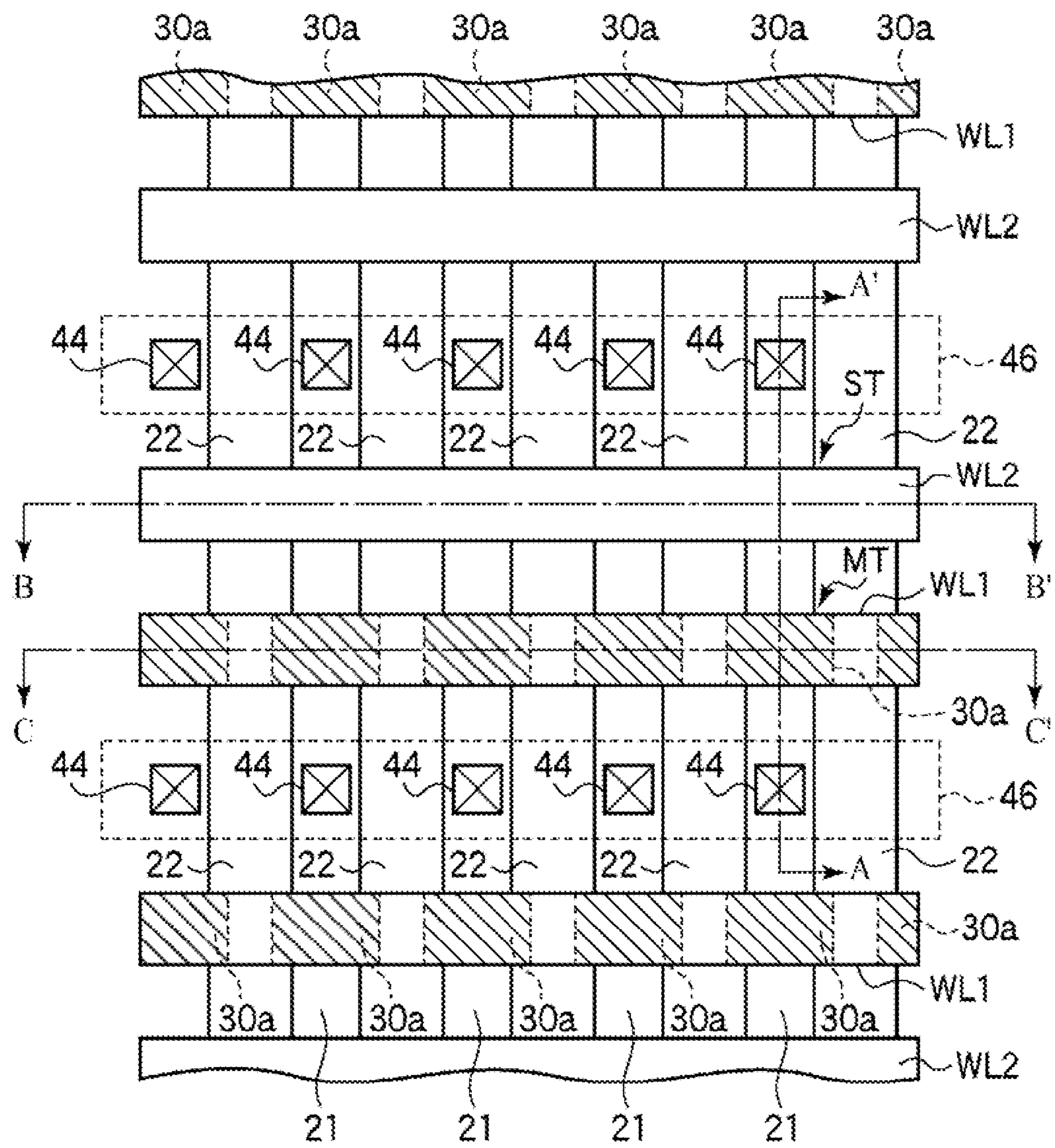


FIG. 3

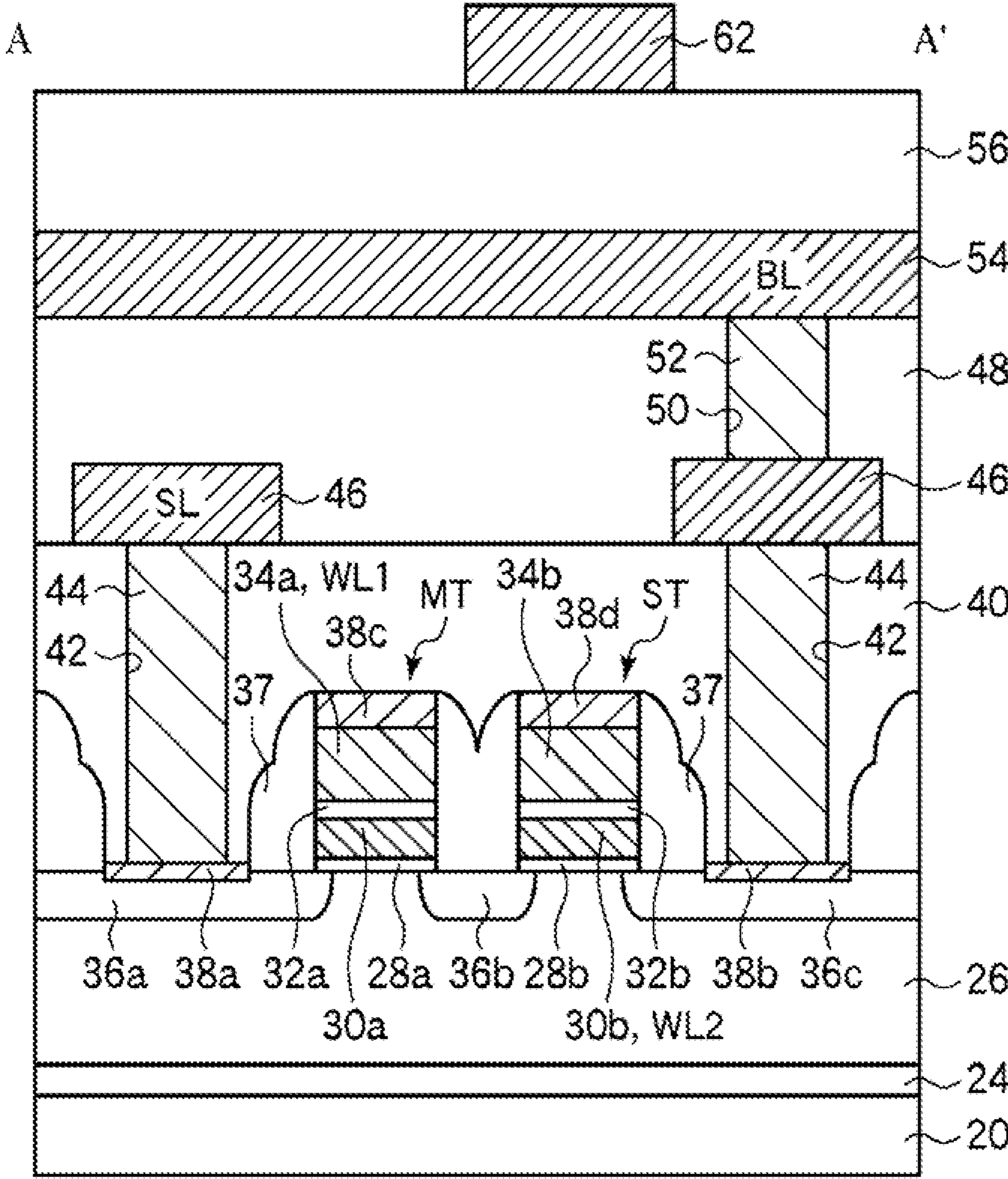


FIG. 4

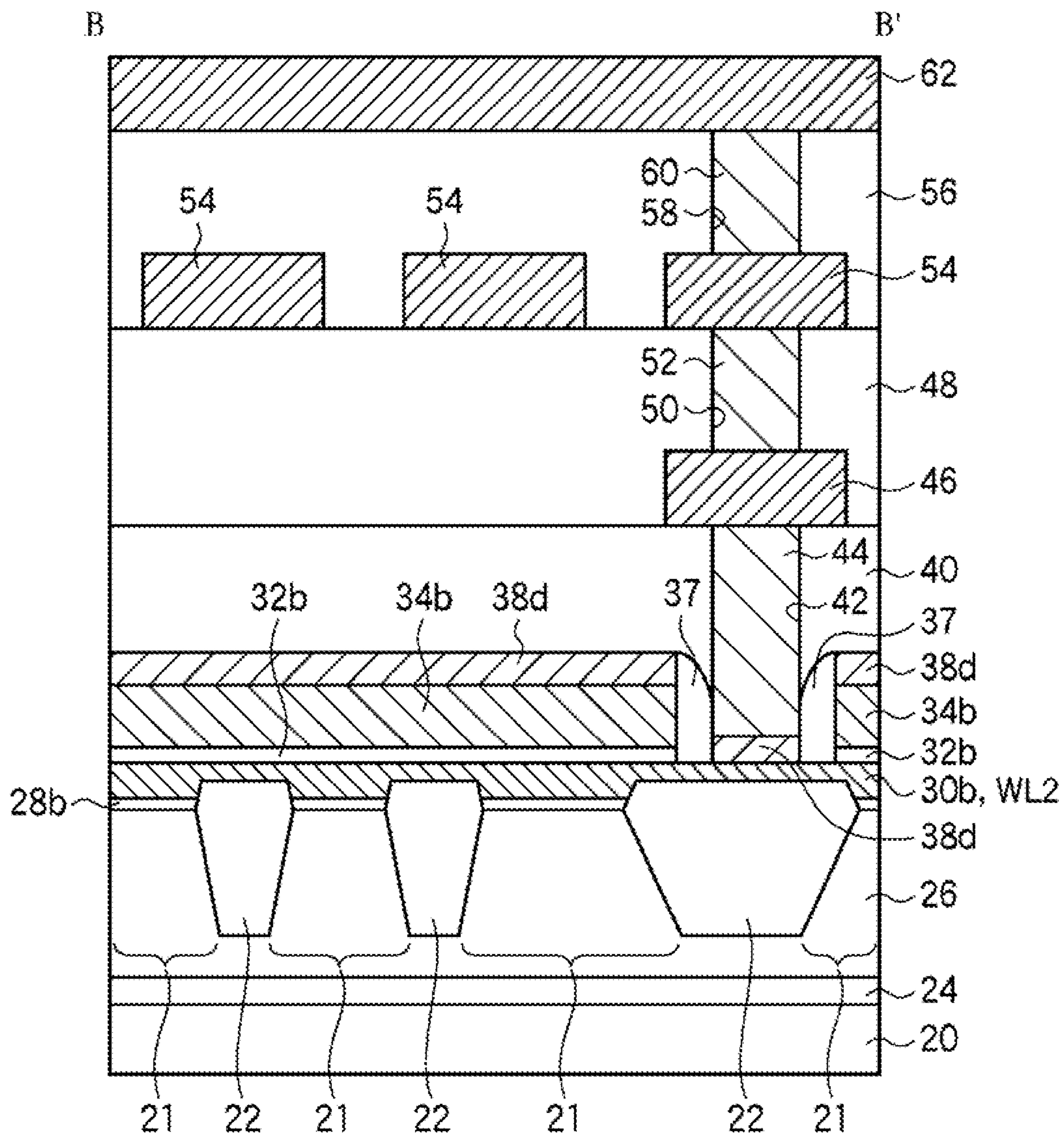


FIG. 5

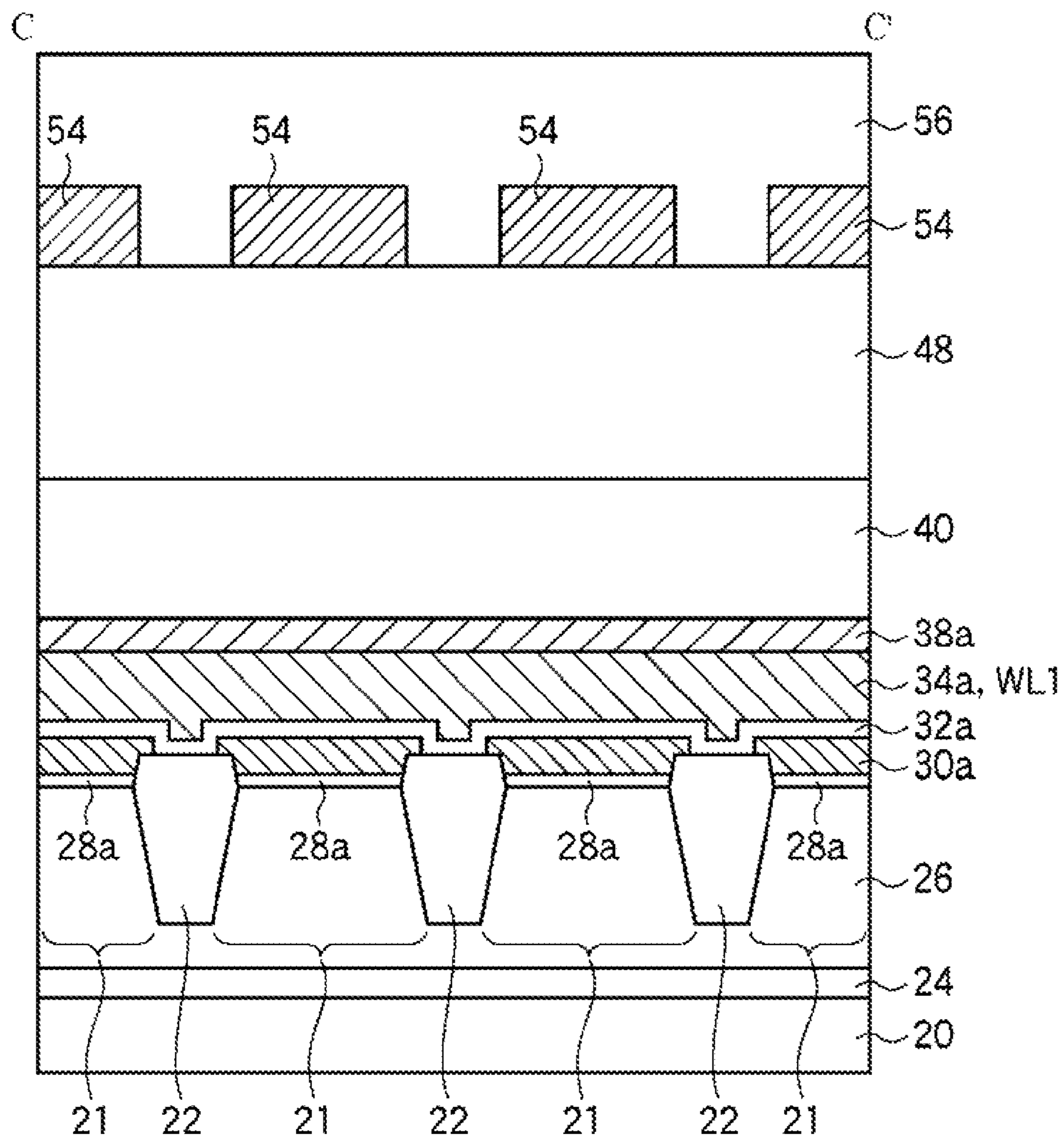
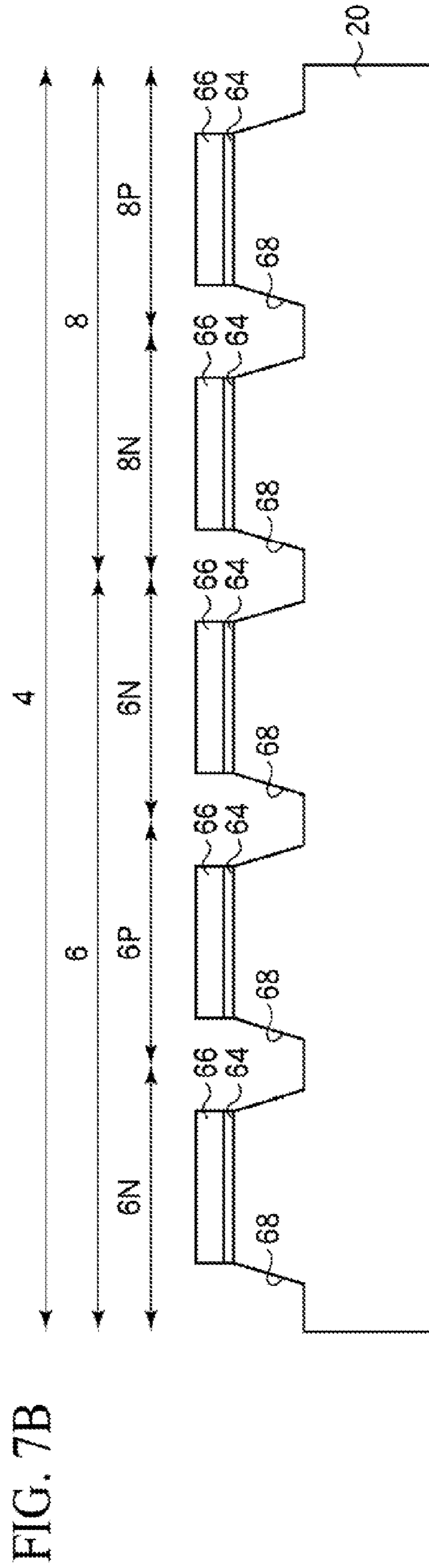
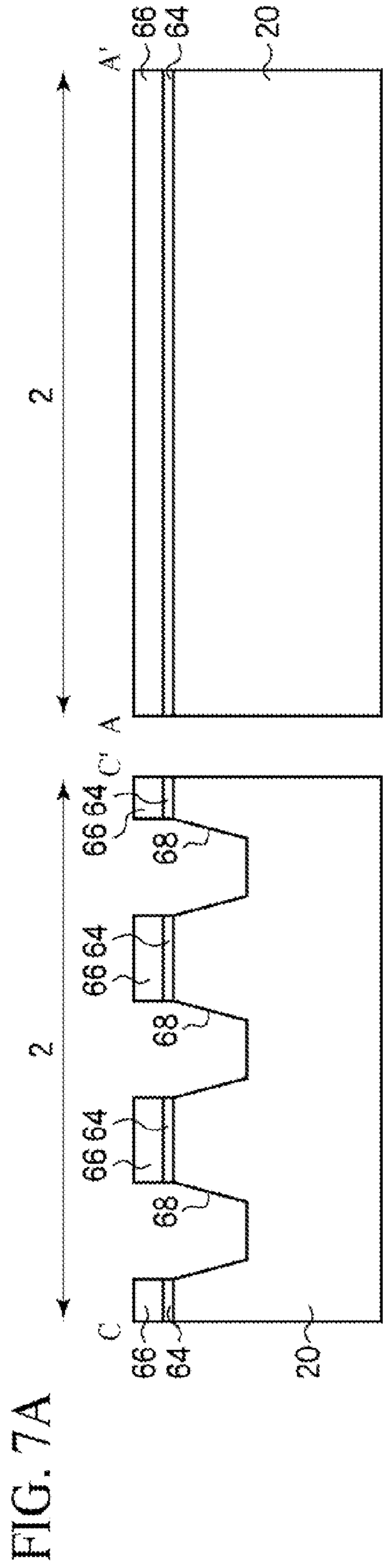
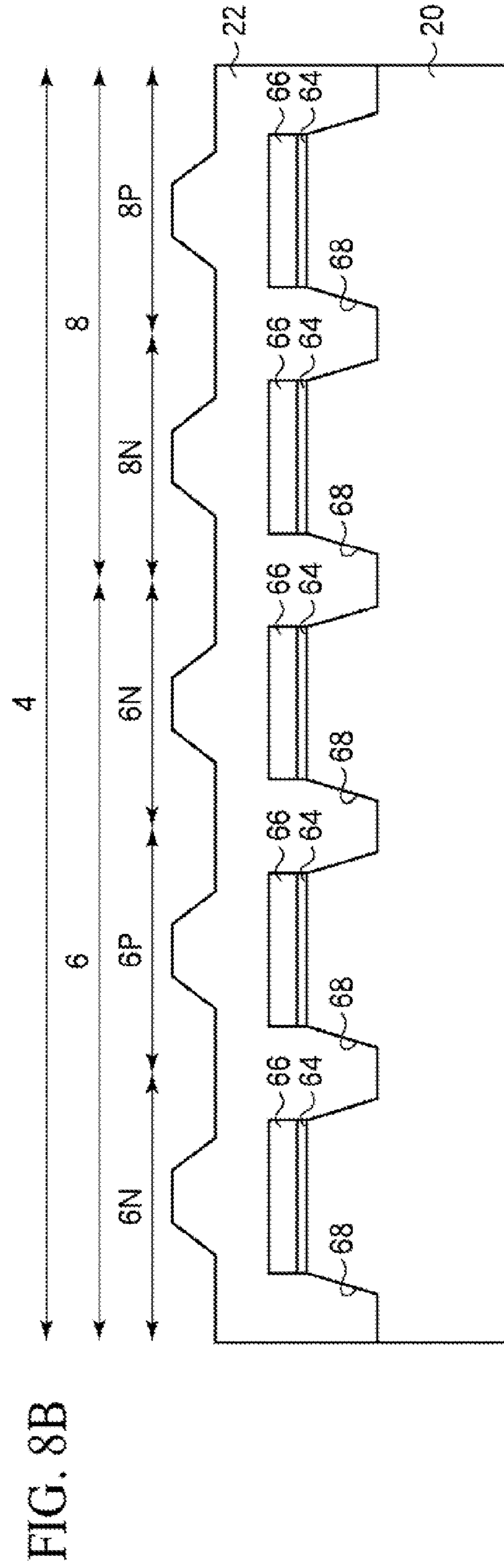
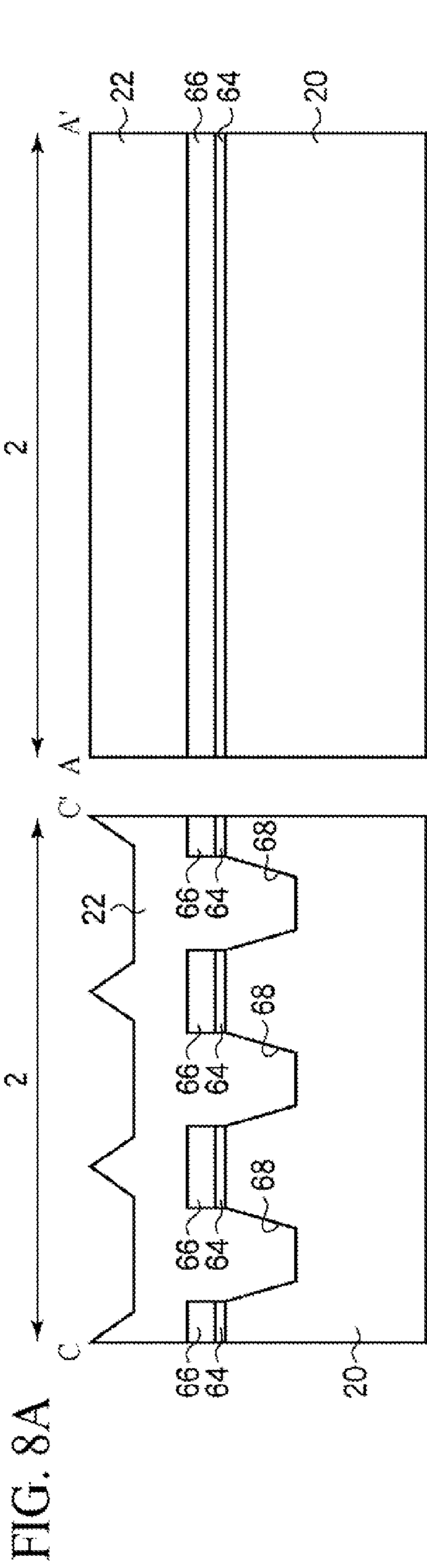
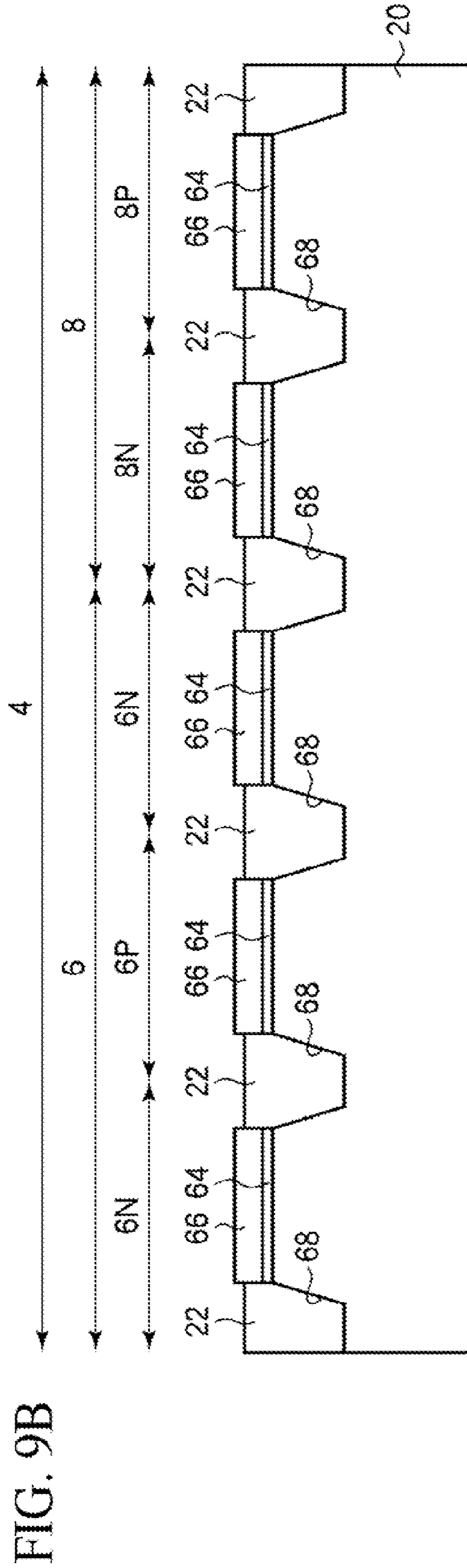
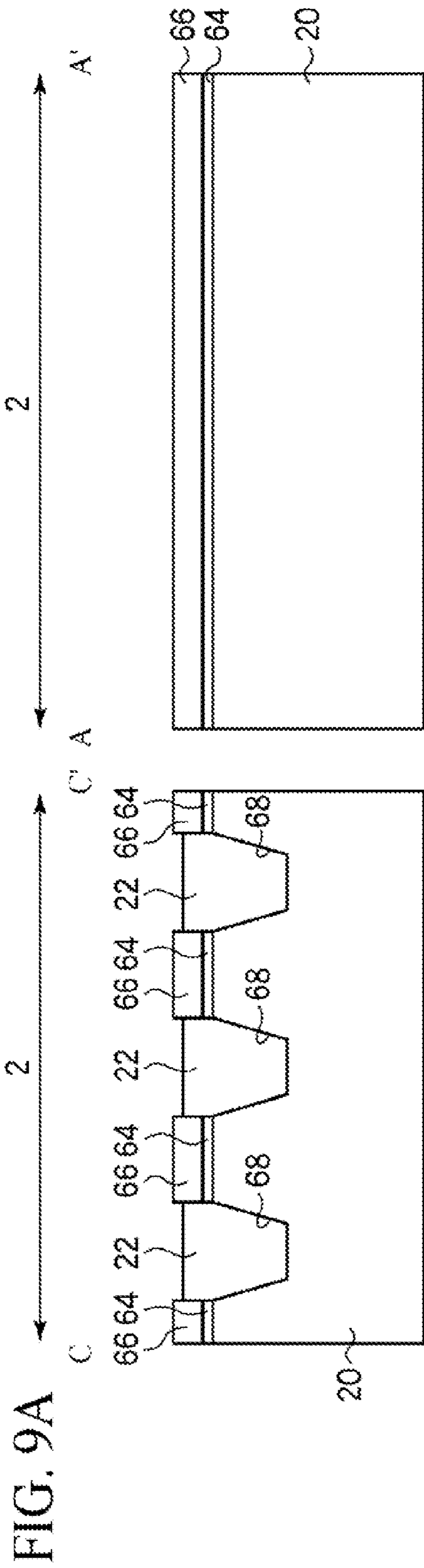


FIG. 6

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	CONSTANTLY V _{cc}	V _{cc} (0V)	0V
WRITE	0V (F)	5V (0V or F)	9V (0V or F)	V _{cc} (F)	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	+9V







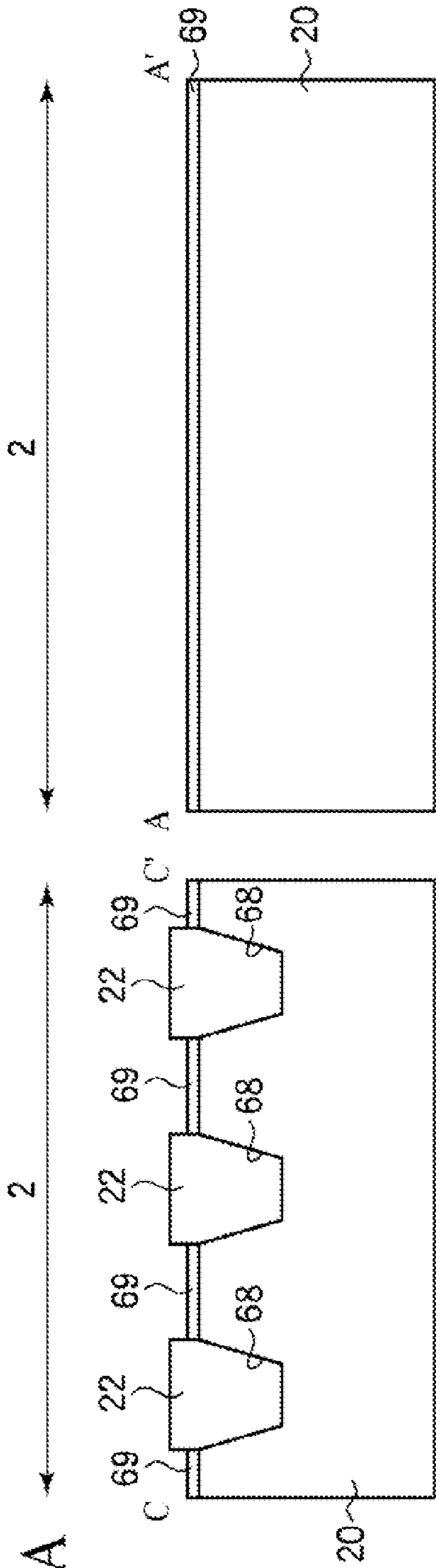


FIG. 10A

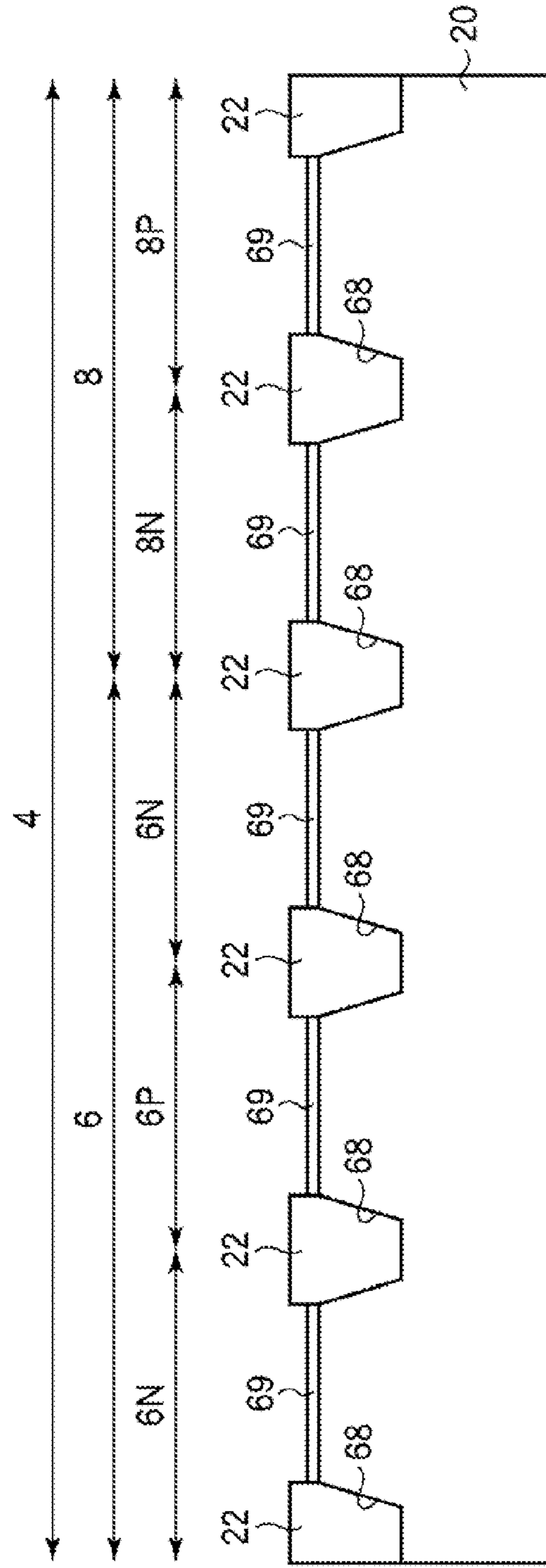
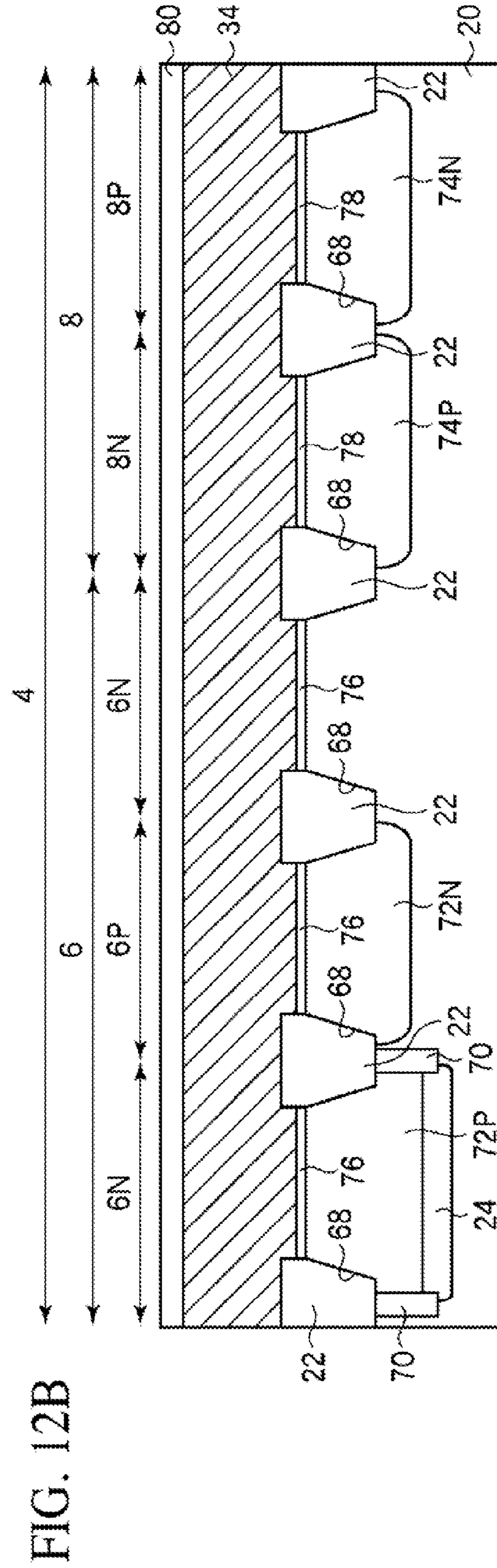
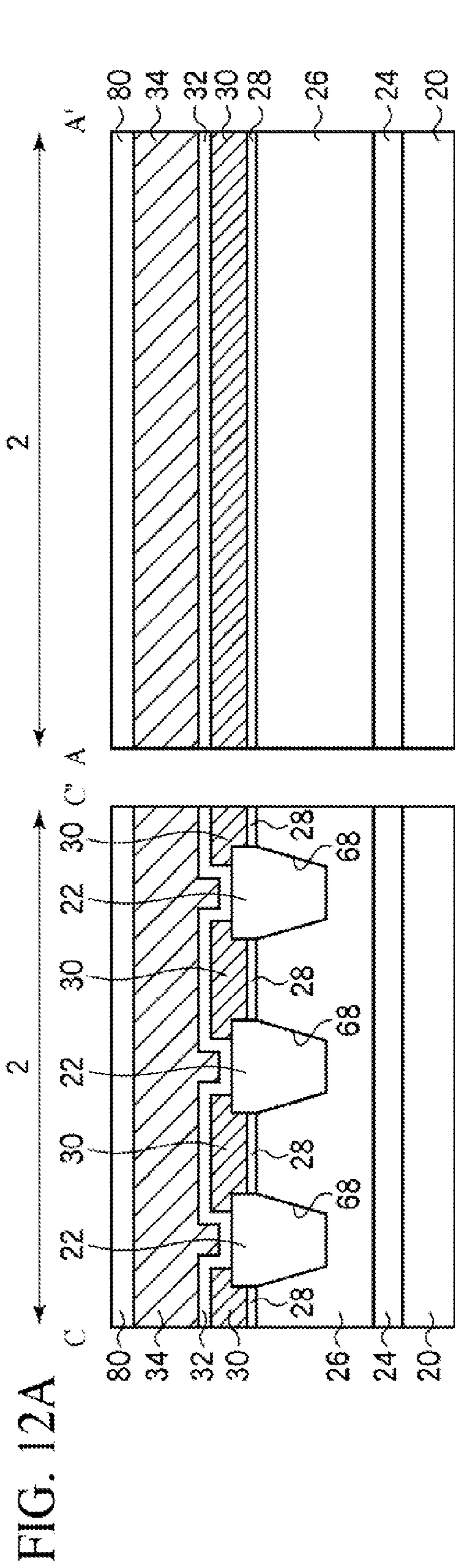
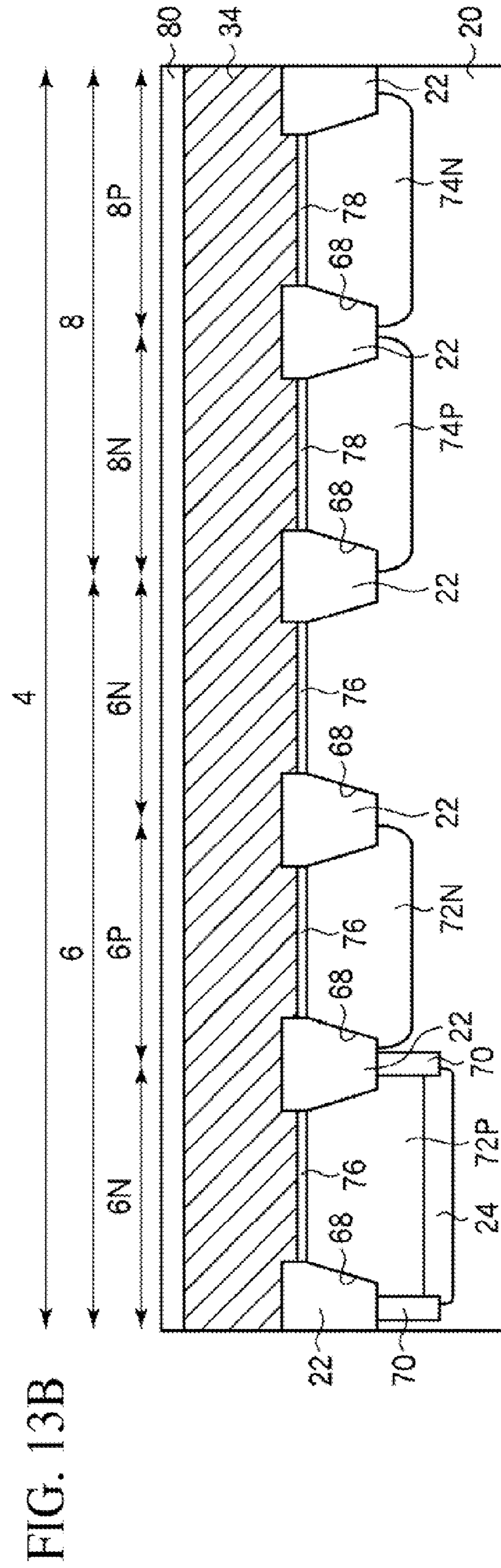
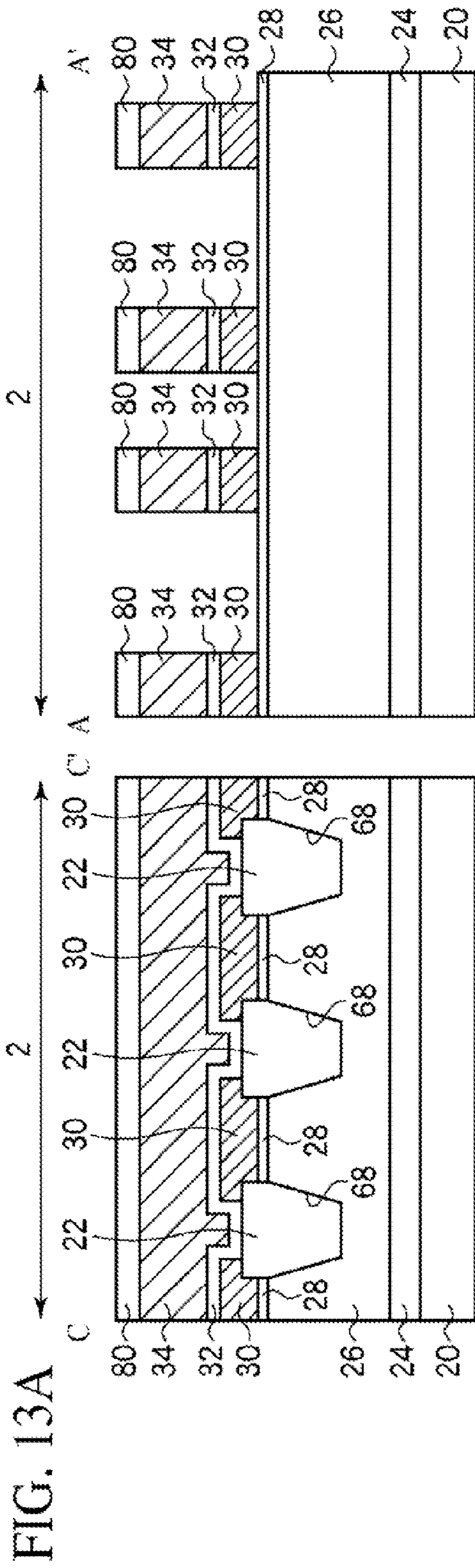
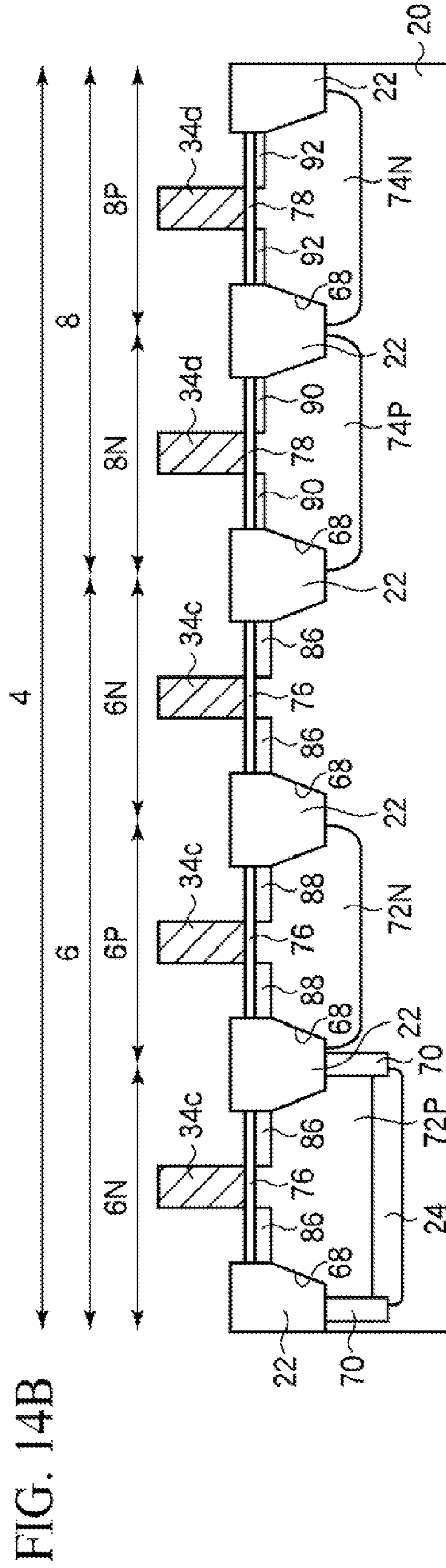
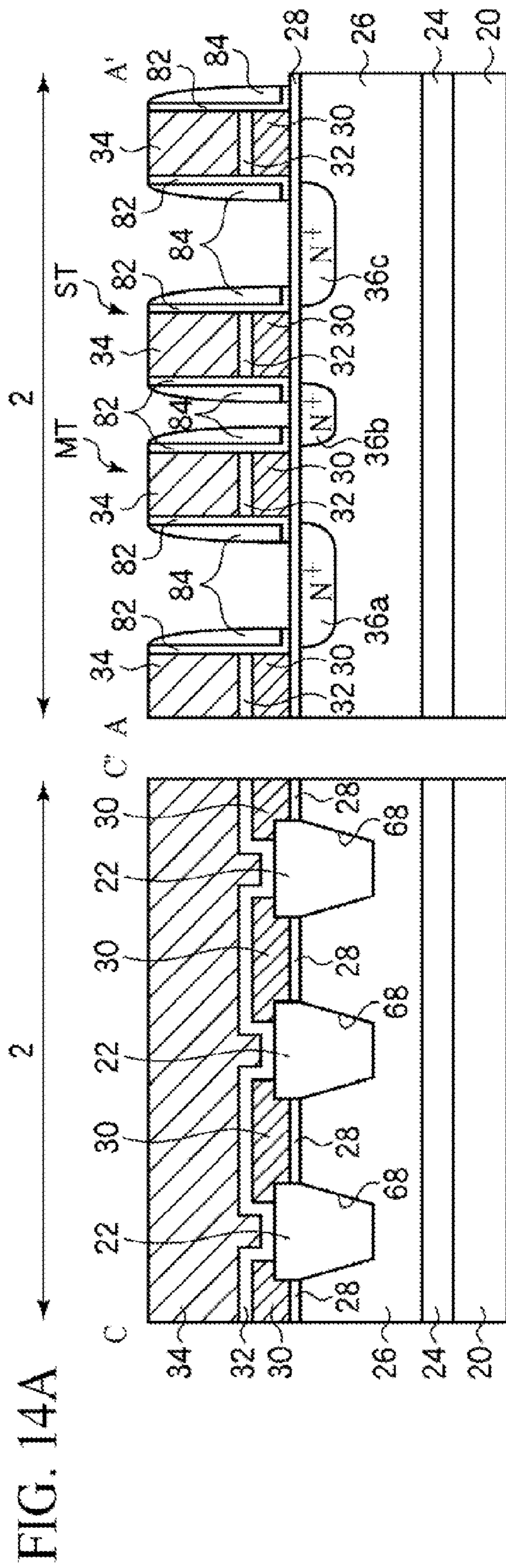
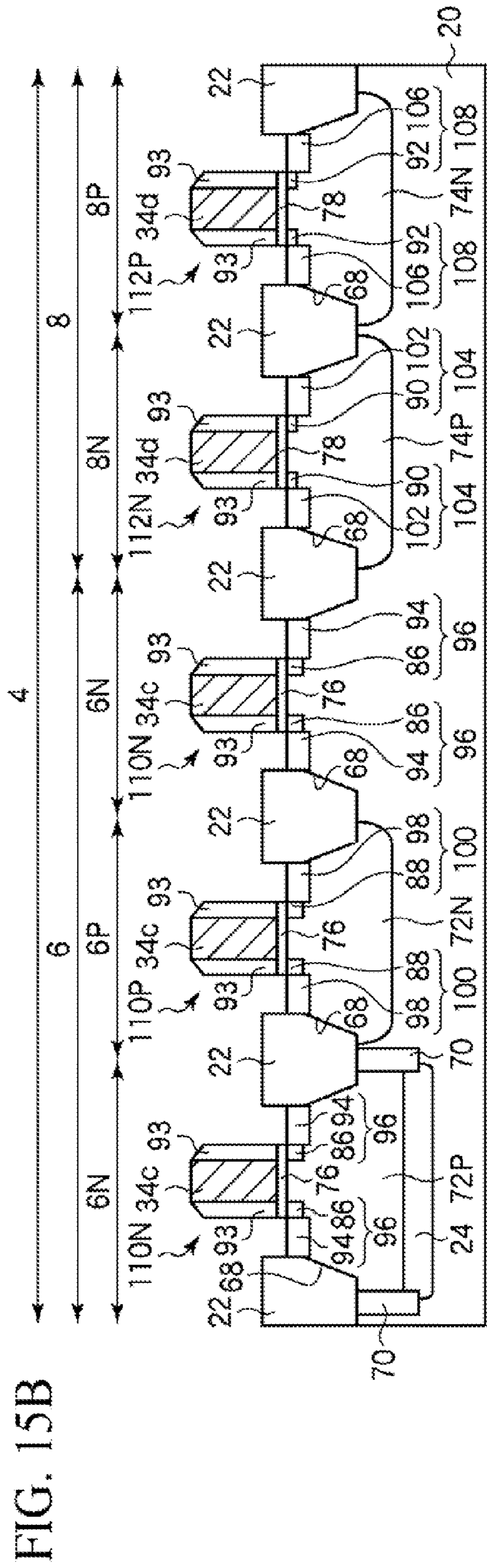
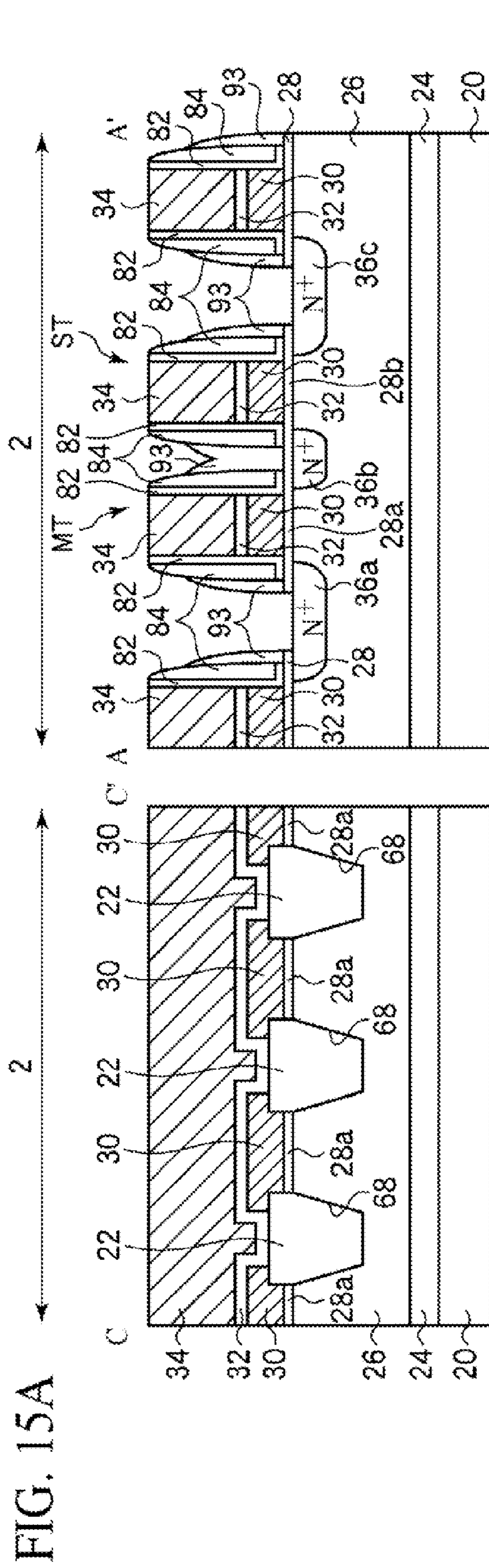


FIG. 10B









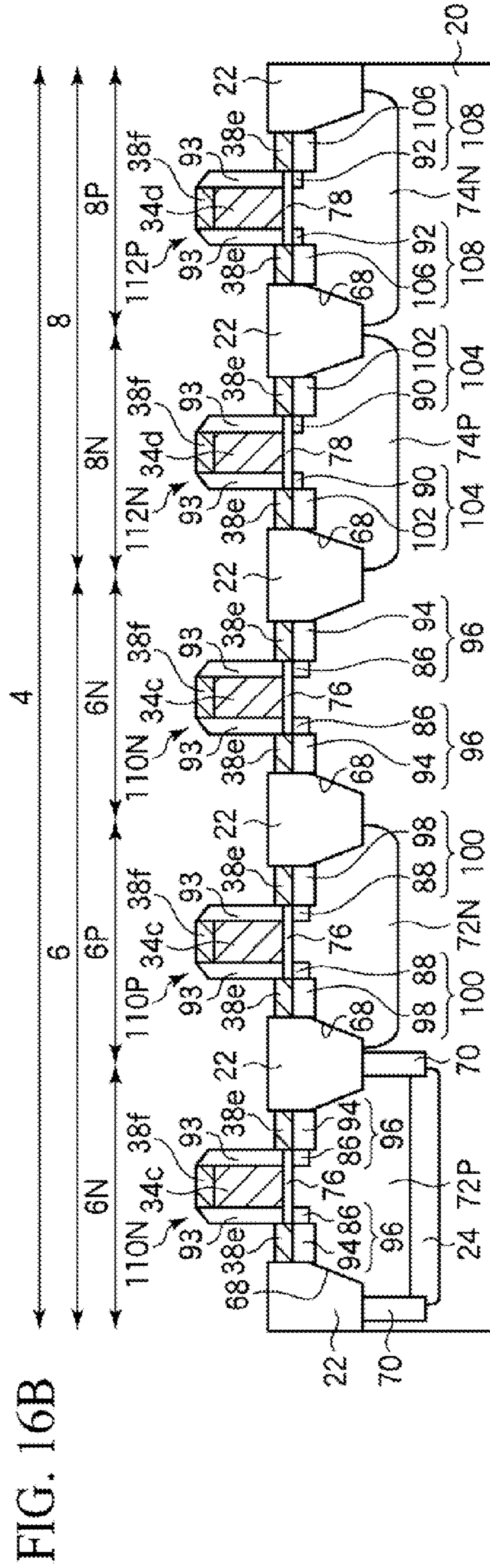
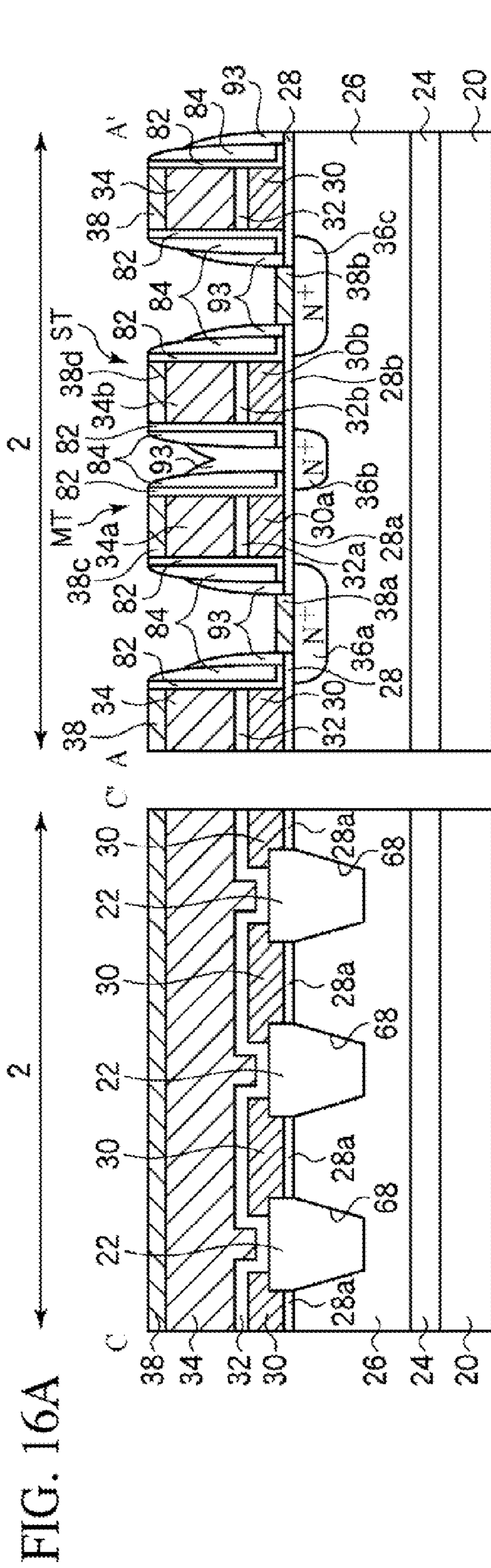


FIG. 17

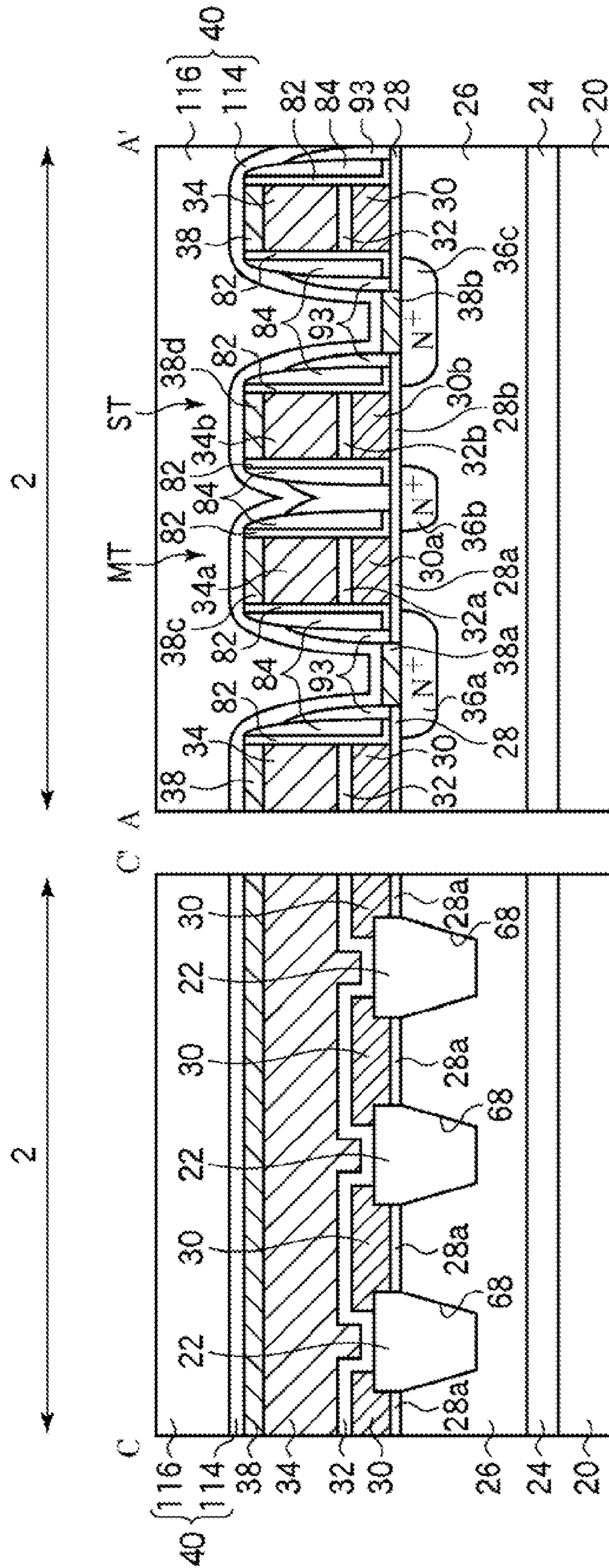


FIG. 19

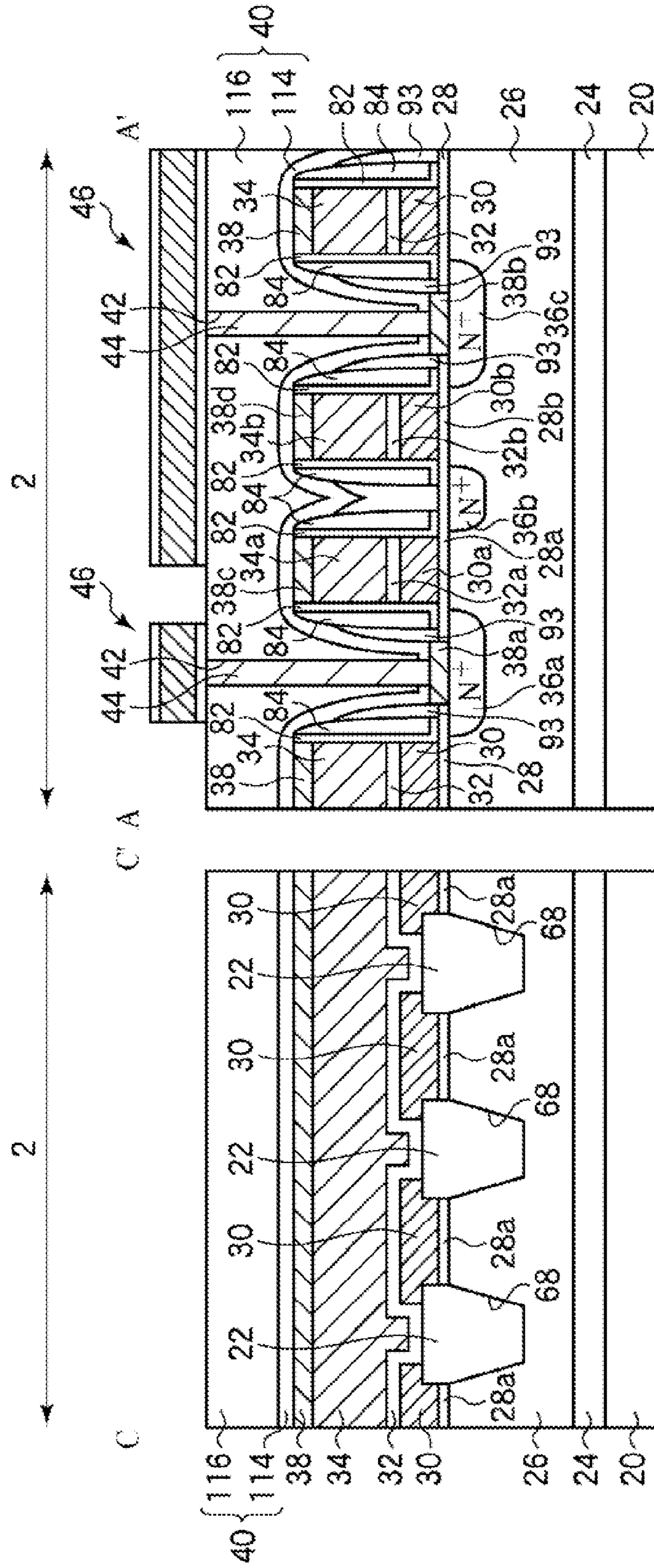
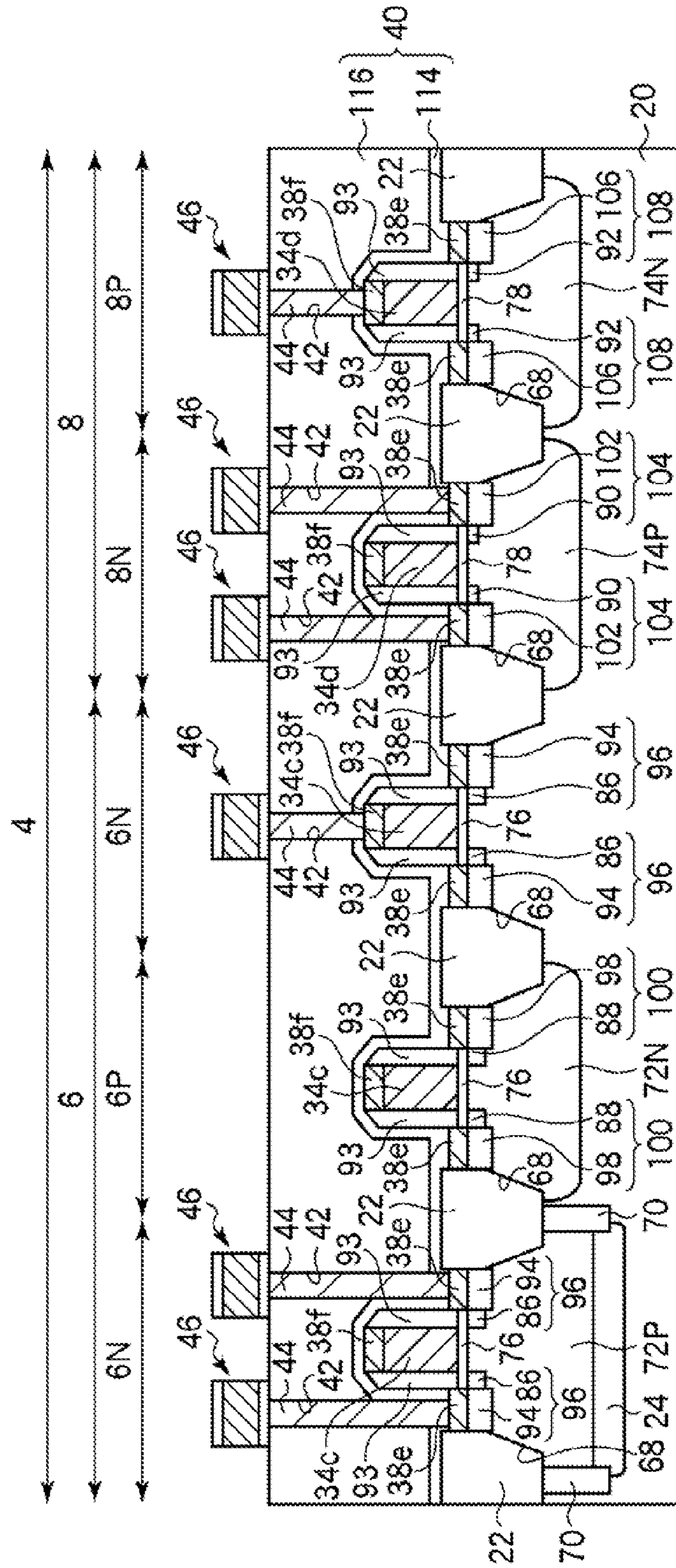


FIG. 20



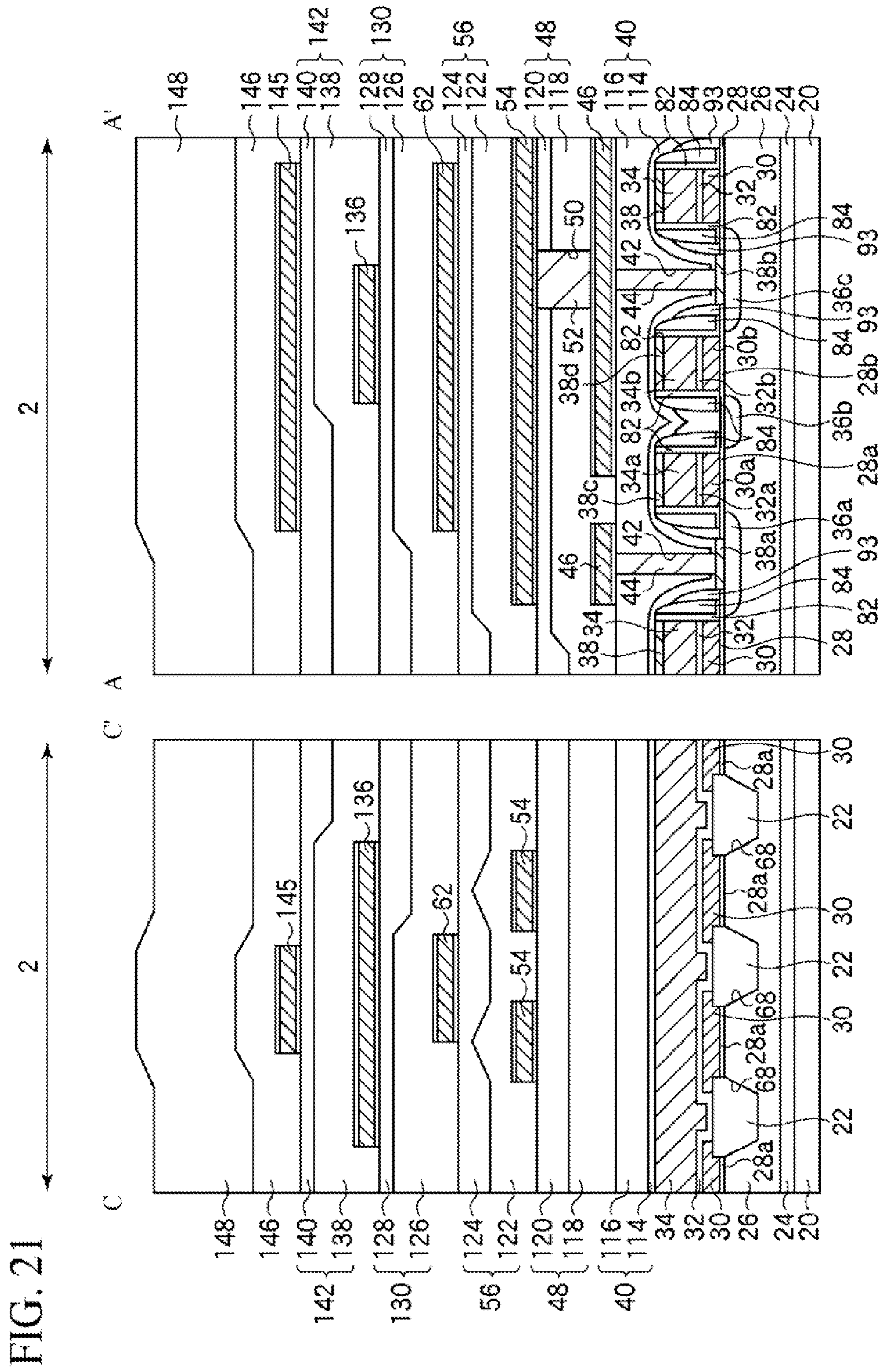


FIG. 23

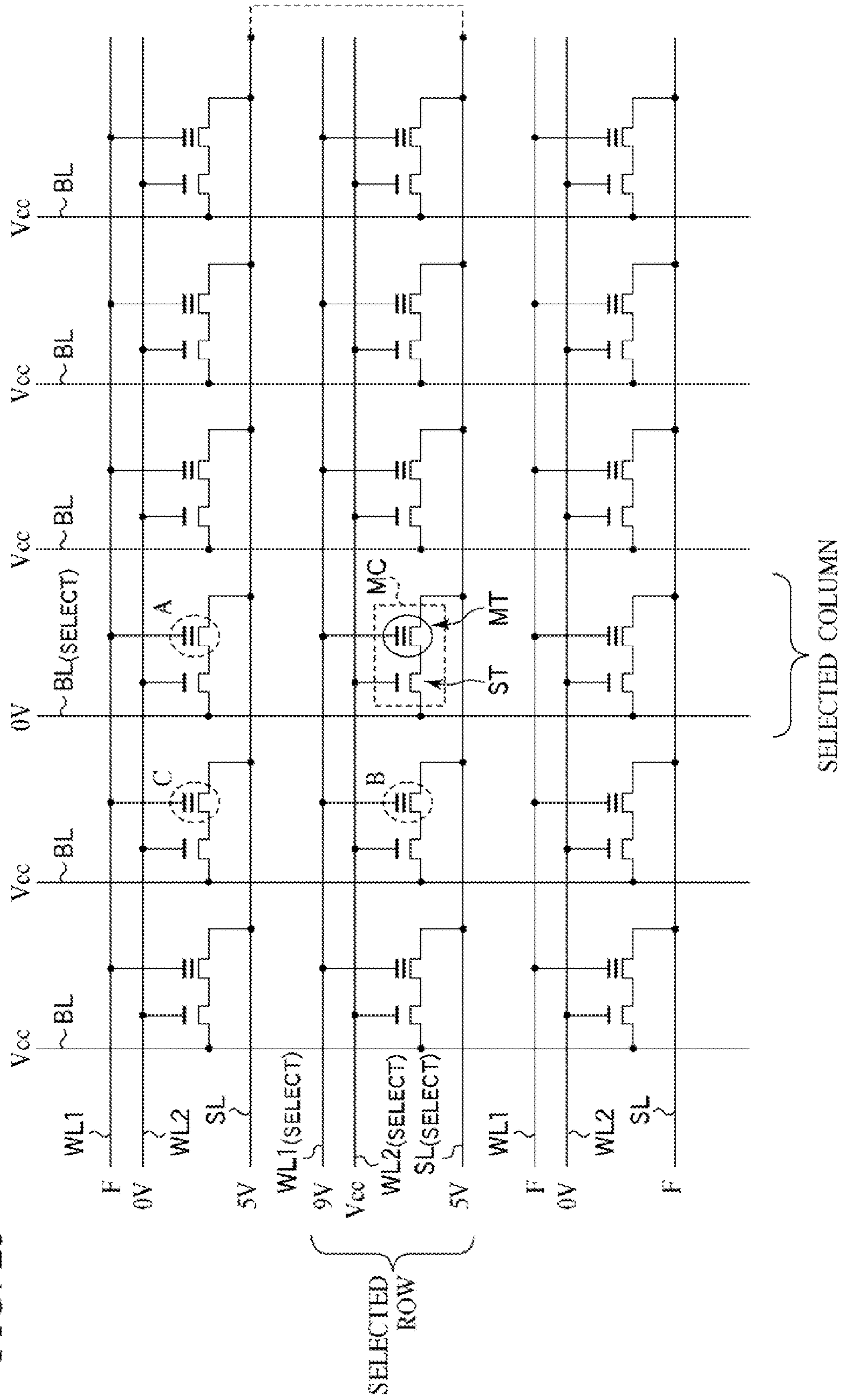


FIG. 24

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	CONSTANTLY V _{cc}	V _{cc} (0V)	0V
WRITE	0V (V _{cc})	5V (0V or F)	9V (0V or F)	V _{cc} (0V)	0V
ERASE	FLOATING	FLOATING	...9V	FLOATING	+9V

FIG. 25

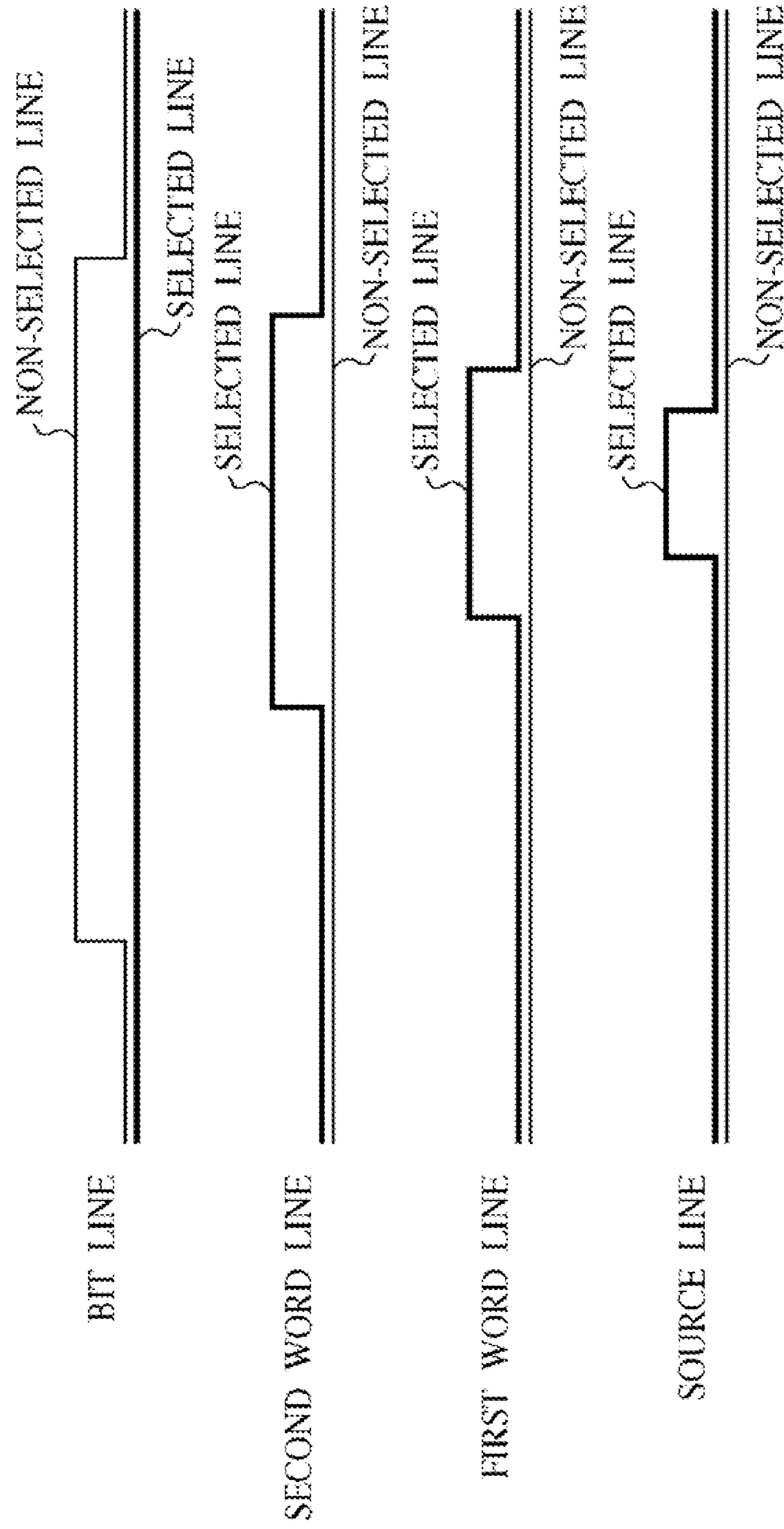


FIG. 26

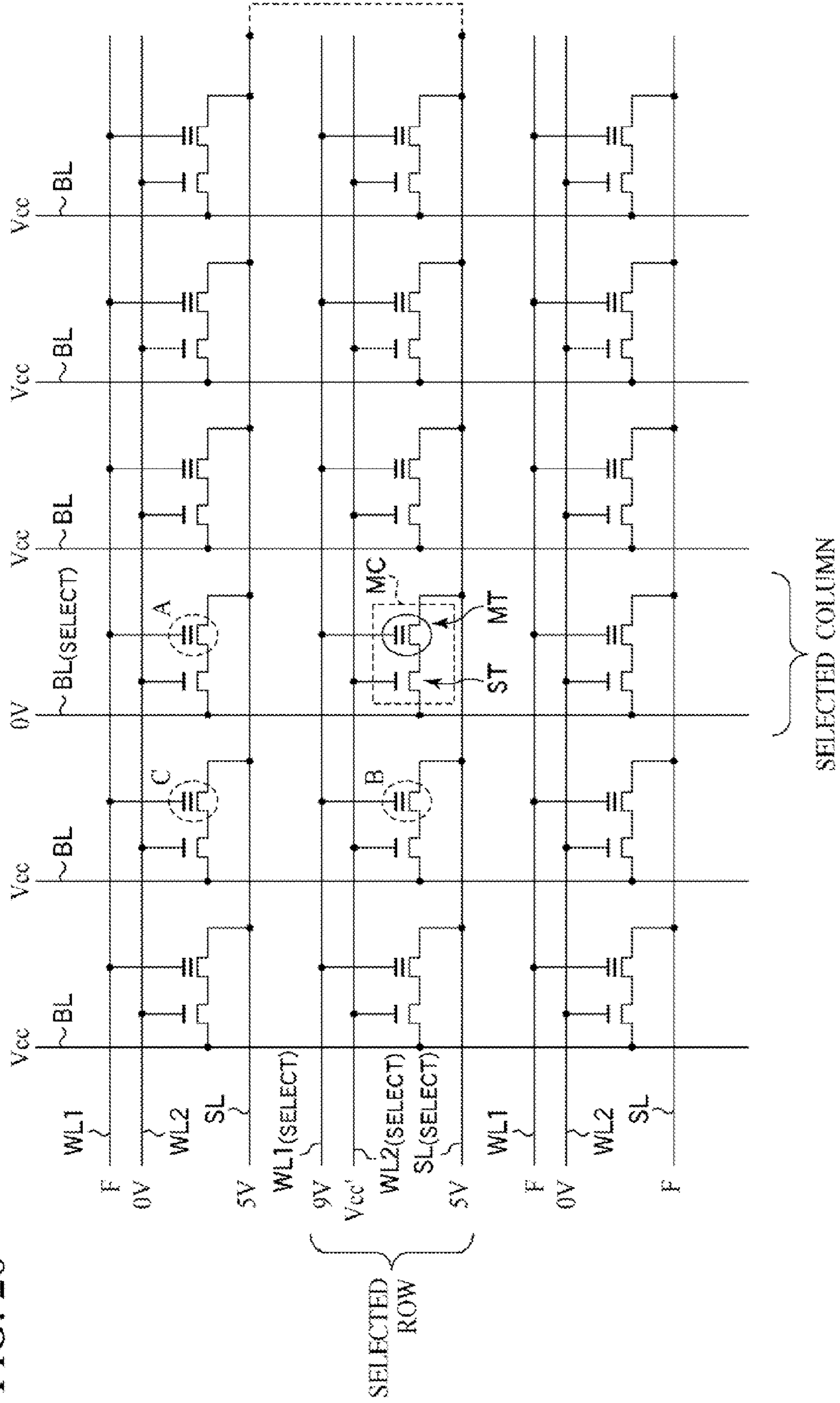


FIG. 27

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	CONSTANTLY V _{cc}	V _{cc} (0V)	0V
WRITE	0V (V _{cc})	5V (0V or F)	9V (0V or F)	V _{cc'} (0V)	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	+9V

FIG. 28

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	V _{cc} (V _{cc})	V _{cc} (0V)	0V
WRITE	0V (V _{cc})	5V (0V or F)	V step (0V or F)	V _{cc} (0V)	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	+9V

FIG. 29

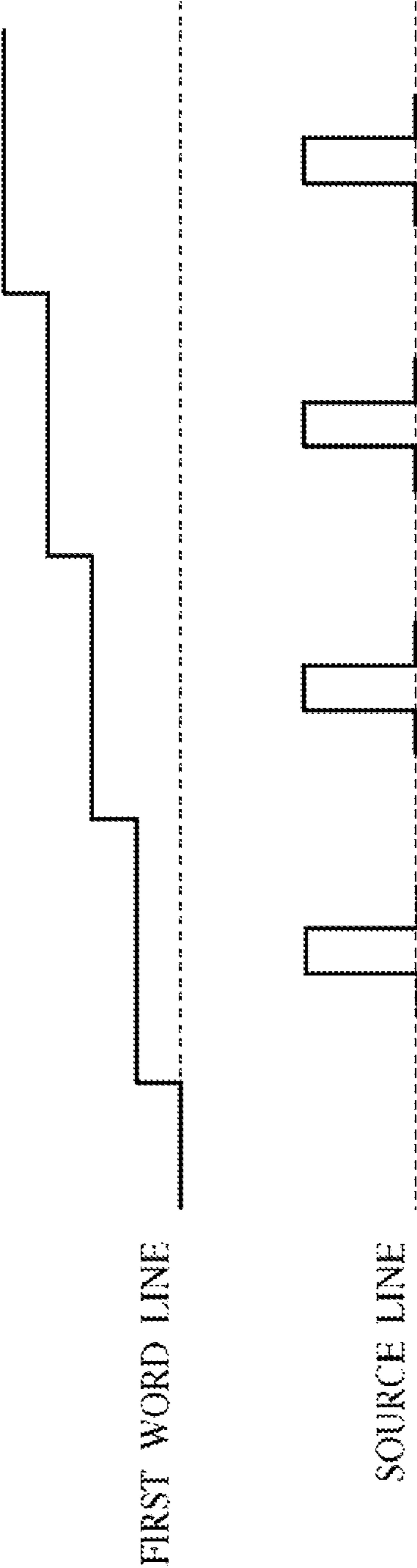
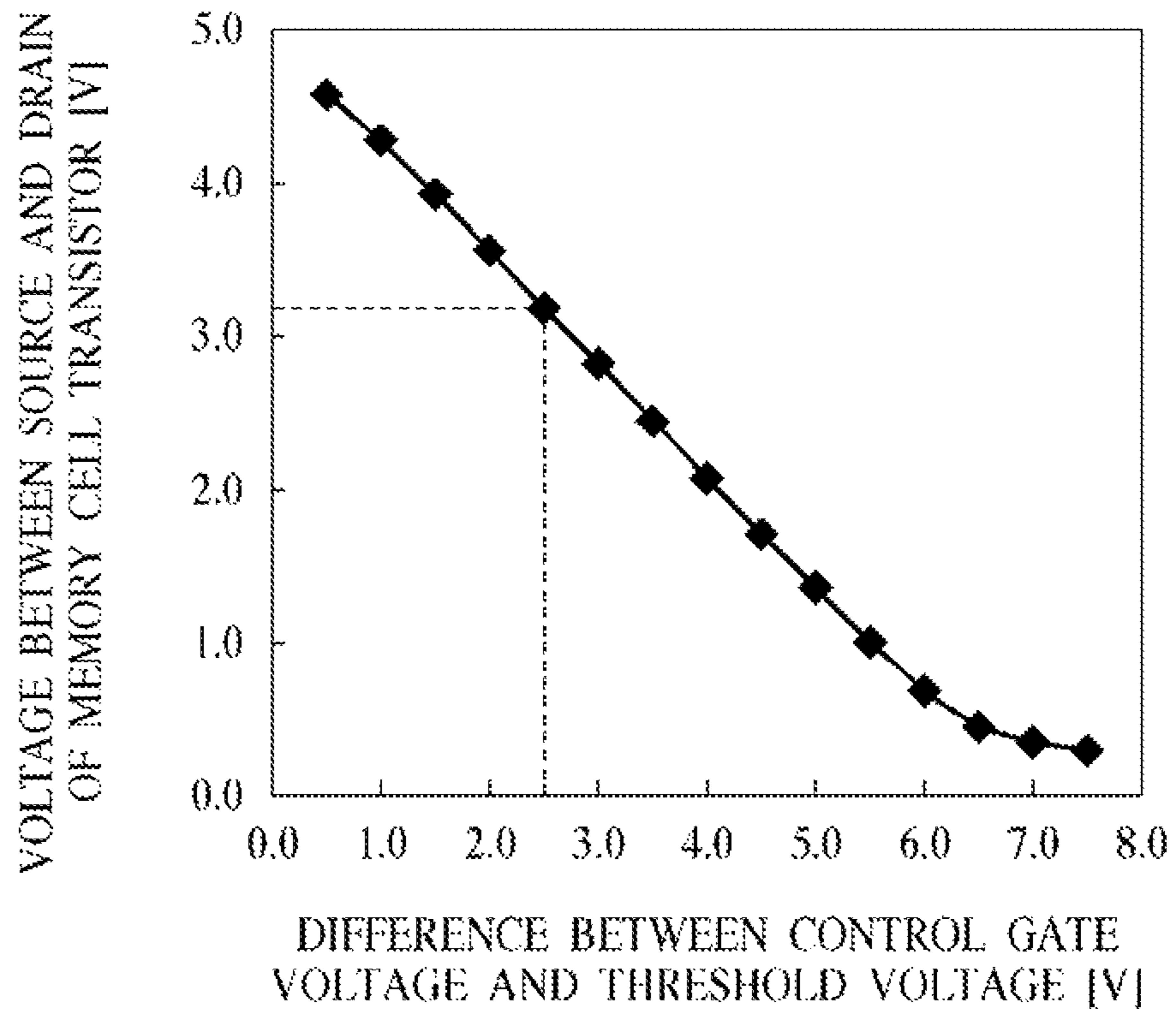


FIG. 30



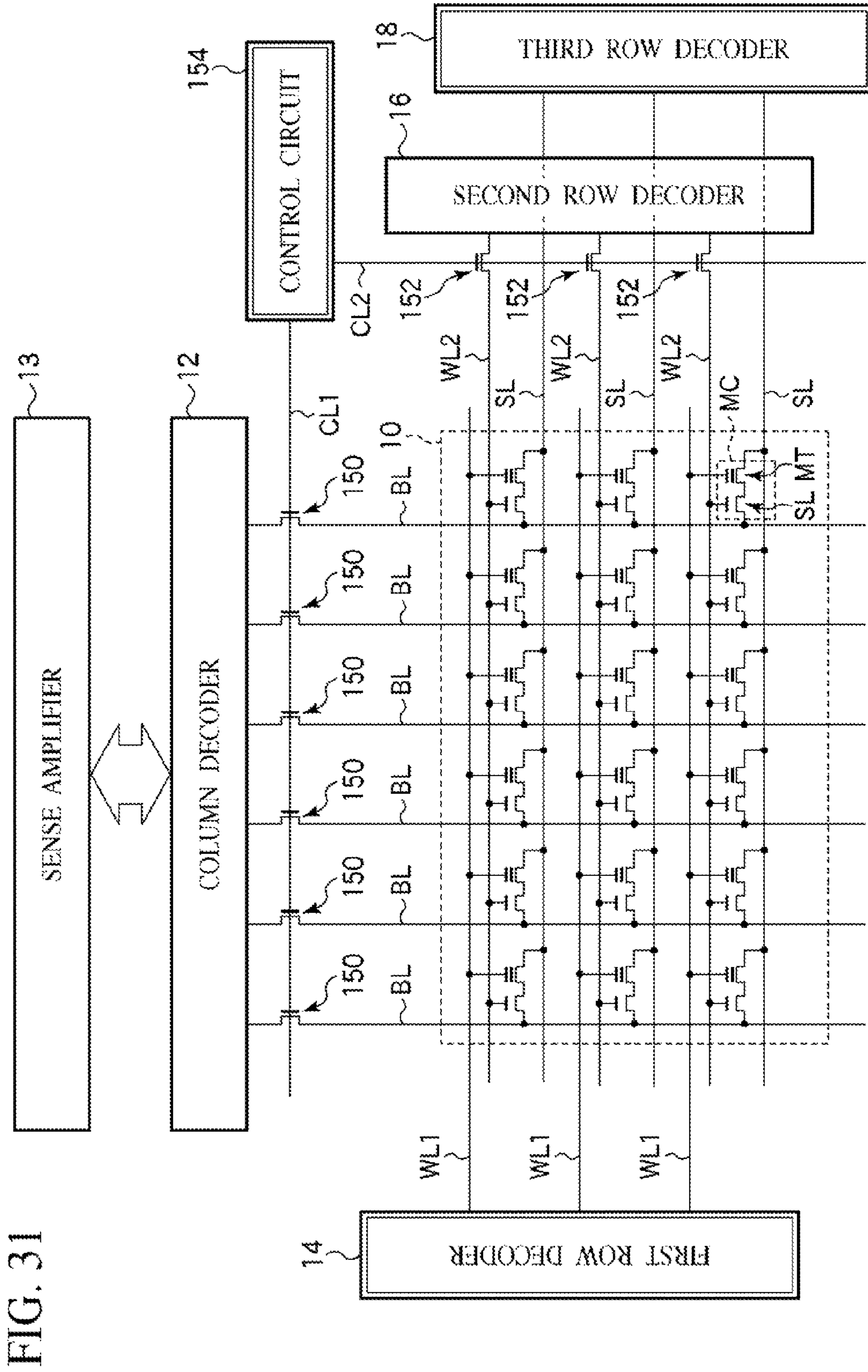


FIG. 31

FIG. 32

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	FIRST CONTROL LINE	SECOND CONTROL LINE	WELL
READ	V _{cc} (0V)	0V (0V)	V _{cc} (V _{cc})	V _{cc} (0V)	5V	5V	0V
WRITE	0V (V _{cc})	5V (0V or F)	9V (0V or F)	V _{cc} (0V)	5V	5V	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	0V	0V	+9V

FIG. 33

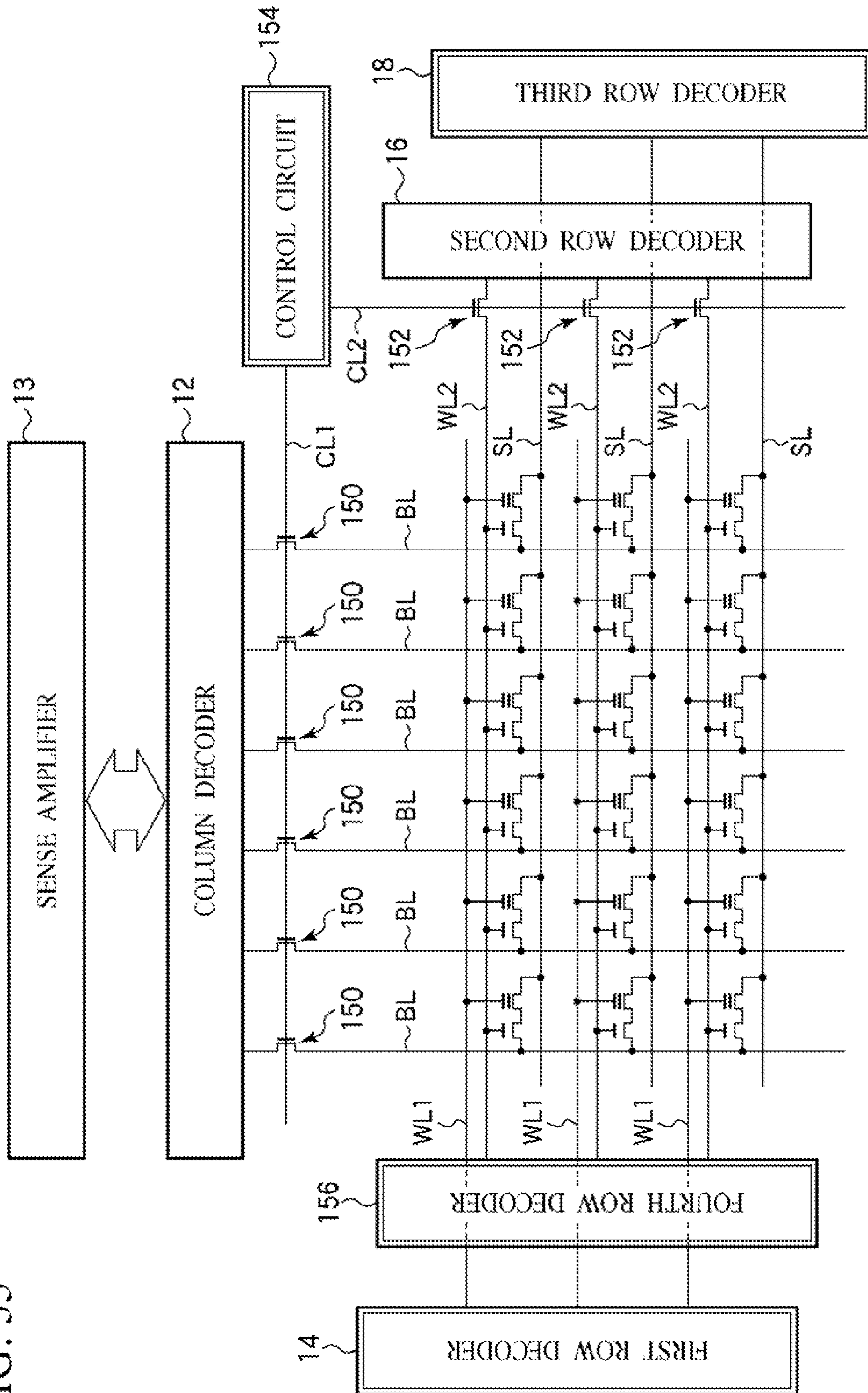


FIG. 34

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	FIRST CONTROL LINE	SECOND CONTROL LINE	WELL
READ	V _{cc} (0V)	0V (0V)	V _{cc} (V _{cc})	V _{cc} (0V)	5V	5V	0V
WRITE	0V (F)	5V (0V or F)	9V (0V or F)	4V (0V)	5V	0V	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	0V	0V	+9V

FIG. 35

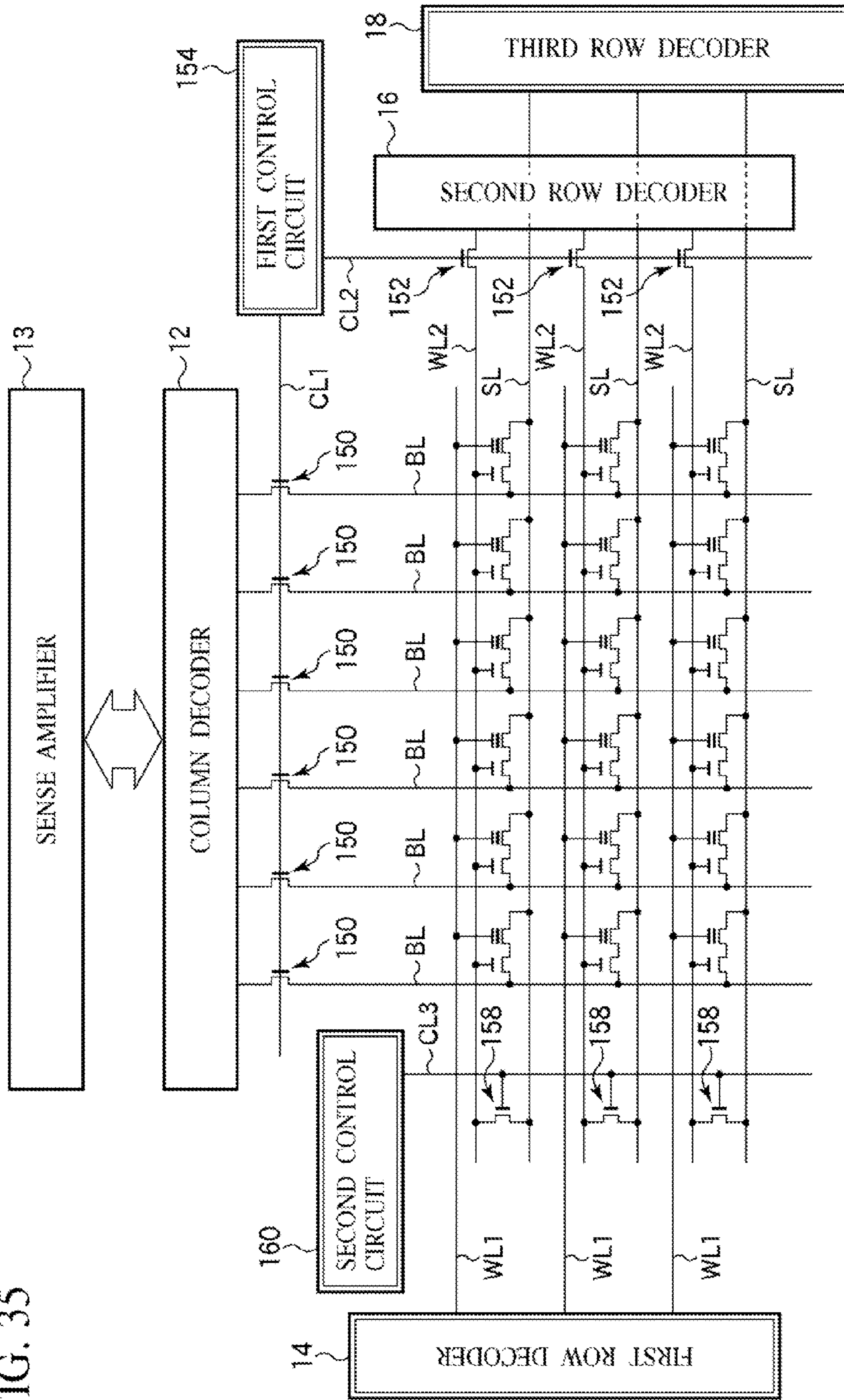


FIG. 36

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	FIRST CONTROL LINE	SECOND CONTROL LINE	THIRD CONTROL LINE	WELL
READ	V _{cc} (0V)	0V (0V)	V _{cc} (V _{cc})	V _{cc} (0V)	5V	5V	0V	0V
WRITE	0V (F)	5V (0V or F)	9V (0V or F)	5V (0V)	5V	0V	6V	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	0V	0V	0V	+9V

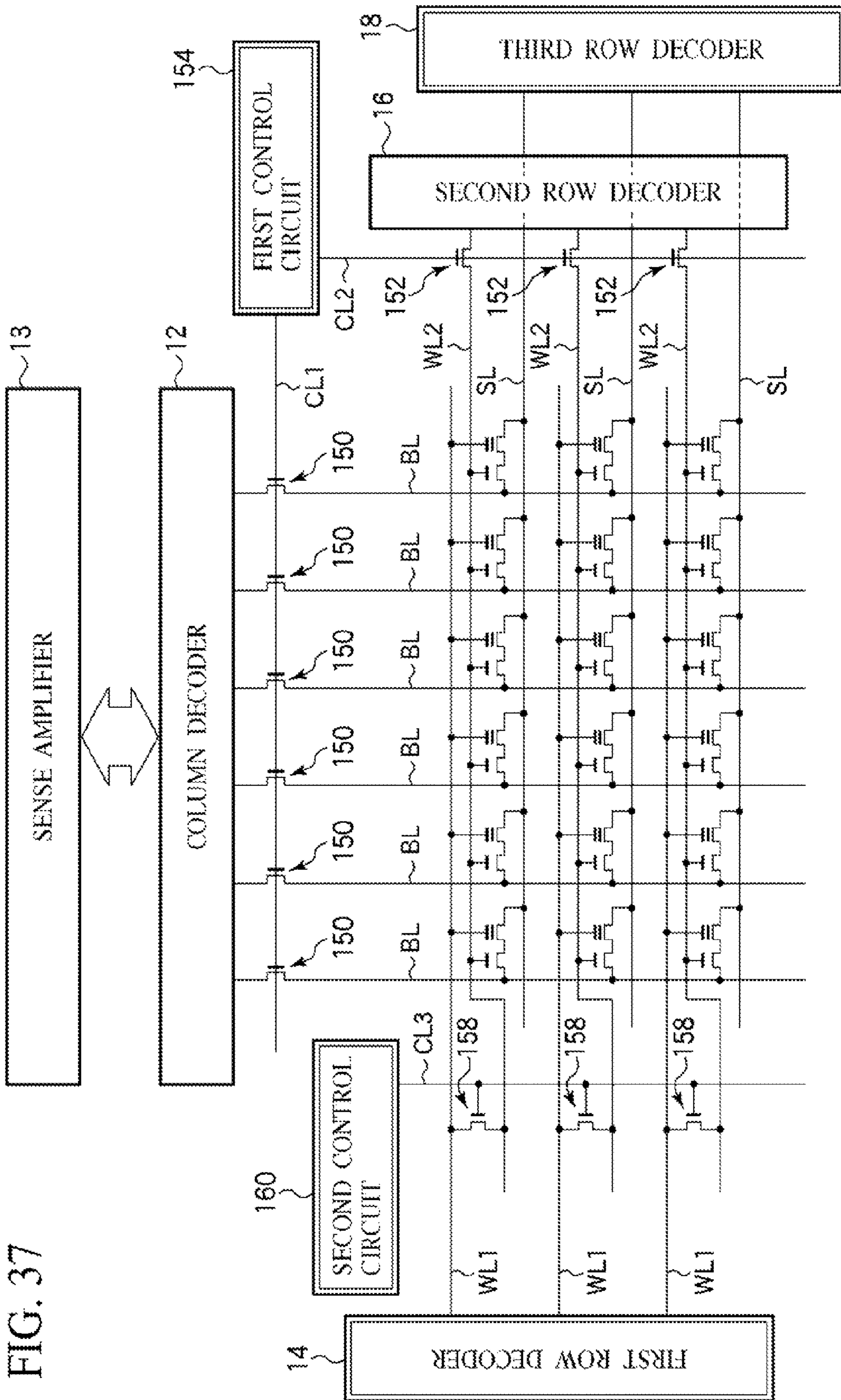


FIG. 37

FIG. 38

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	FIRST CONTROL LINE	SECOND CONTROL LINE	THIRD CONTROL LINE	WELL
READ	V _{cc} (0V)	0V (0V)	V _{cc} (V _{cc})	V _{cc} (0V)	5V	5V	0V	0V
WRITE	0V (F)	5V (0V or F)	9V (0V)	9V (0V)	5V	0V	10V	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	0V	0V	0V	-9V

FIG. 39

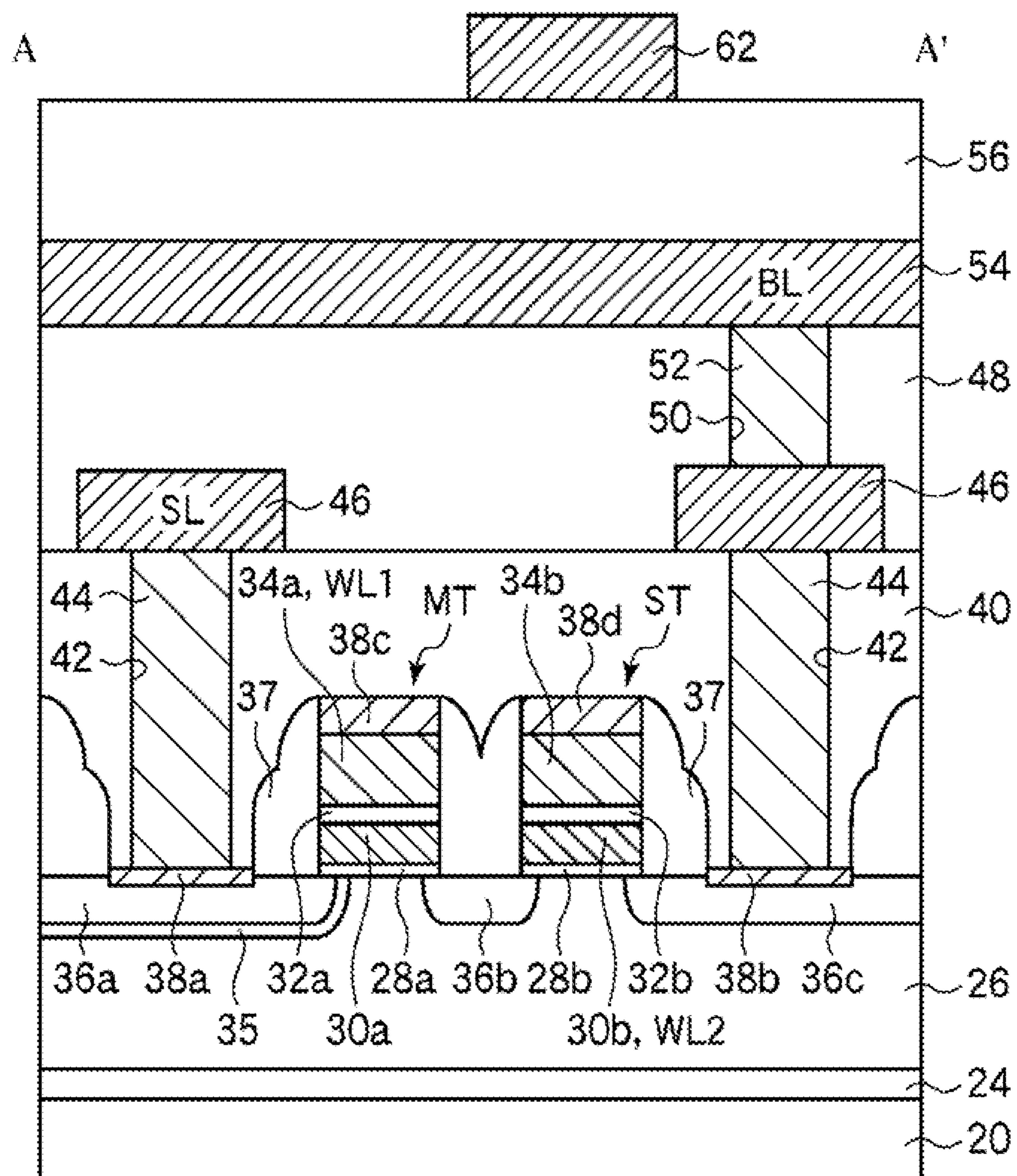


FIG. 40

	BIF LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	FIRST CONTROL LINE	SECOND CONTROL LINE	THIRD CONTROL LINE	WELL
READ	V _{cc} (0V)	0V (0V)	V _f (V _{cc})	V _{cc} (0V)	5V	5V	0V	0V
WRITE	0V (F)	5V (0V or F)	9V (0V or F)	9V (0V or F)	5V	0V	10V	0V
ERASE	FLOATING	FLOATING	-9V	FLOATING	0V	0V	0V	+9V

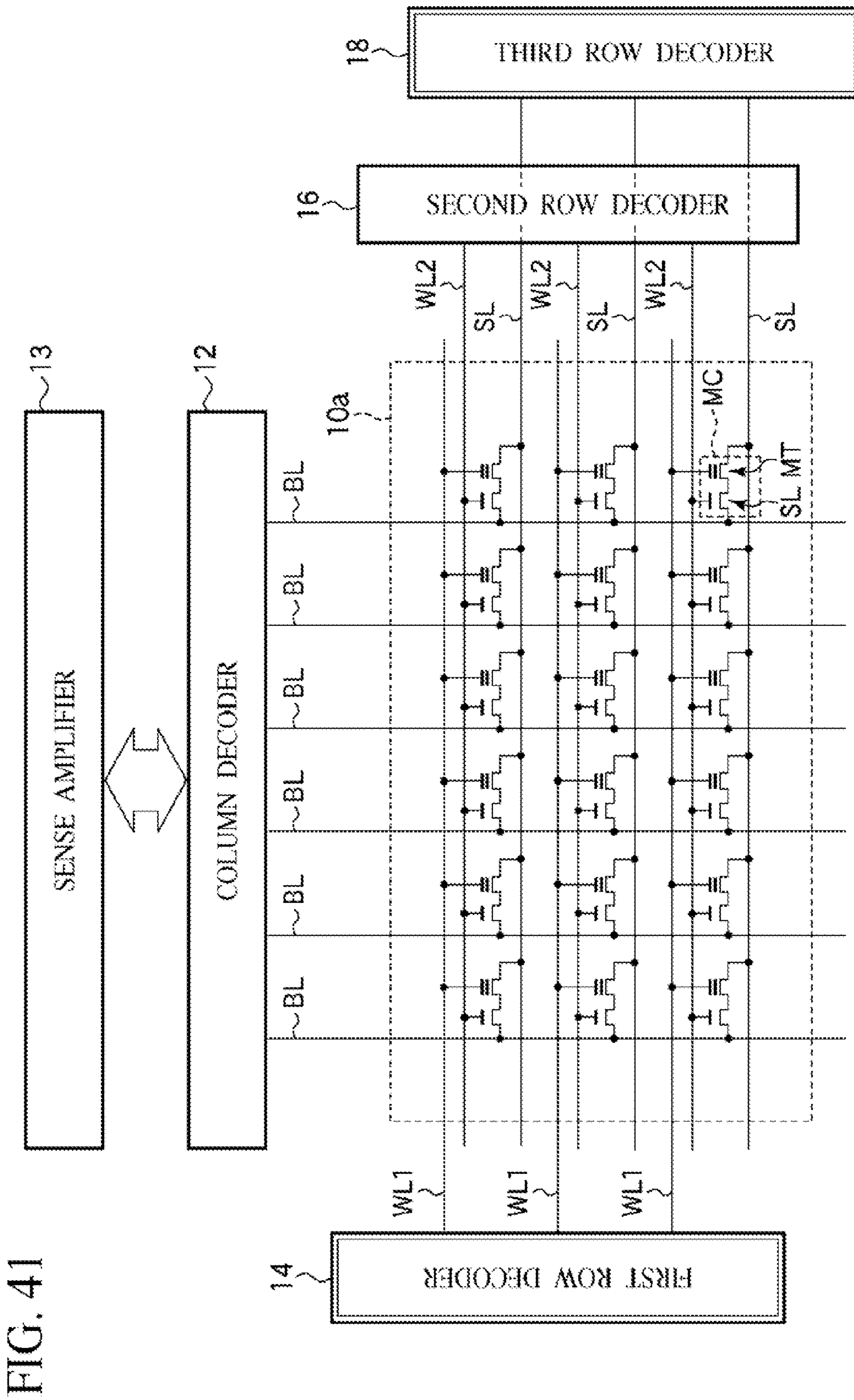


FIG. 41

FIG. 42

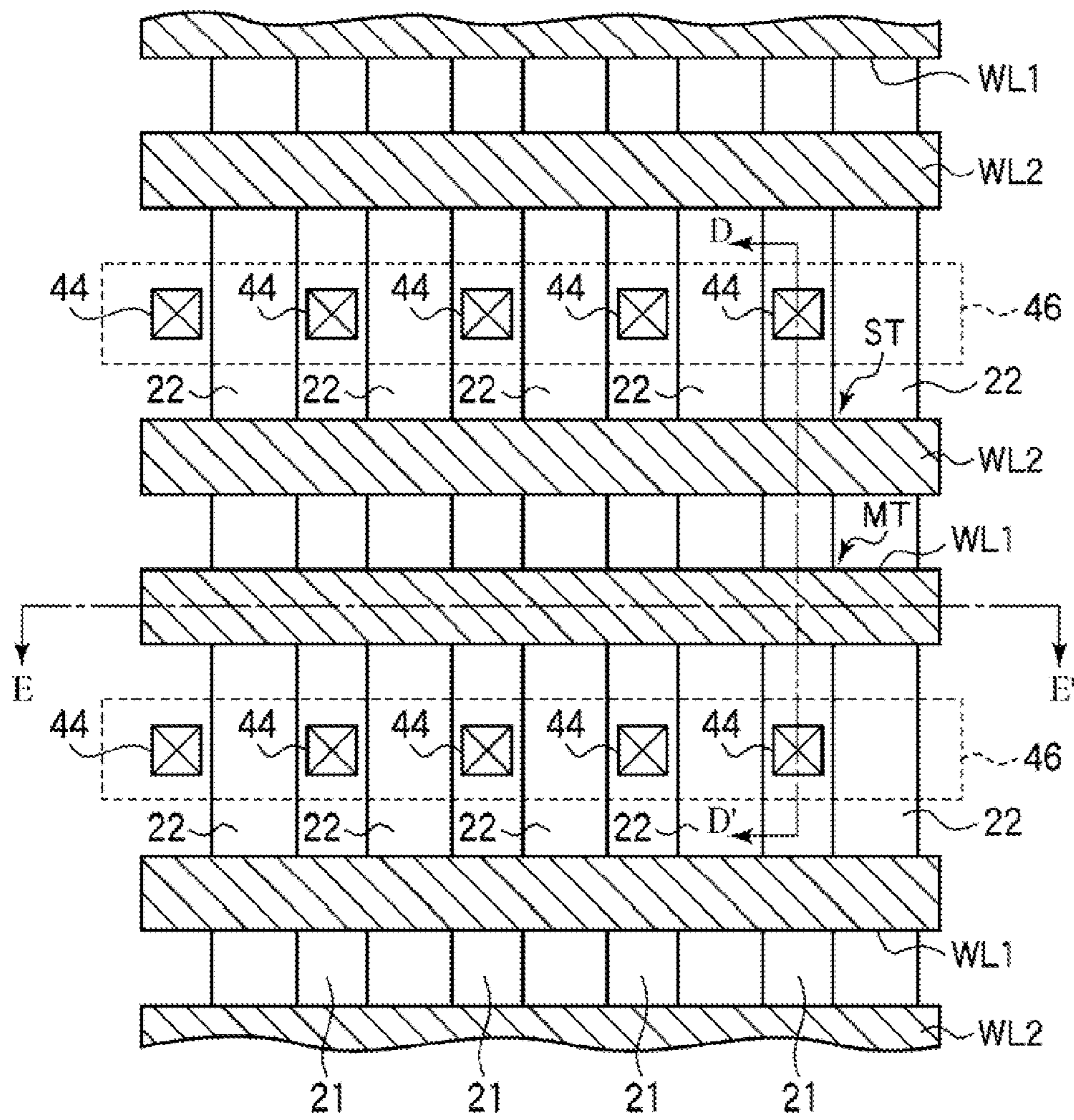


FIG. 43

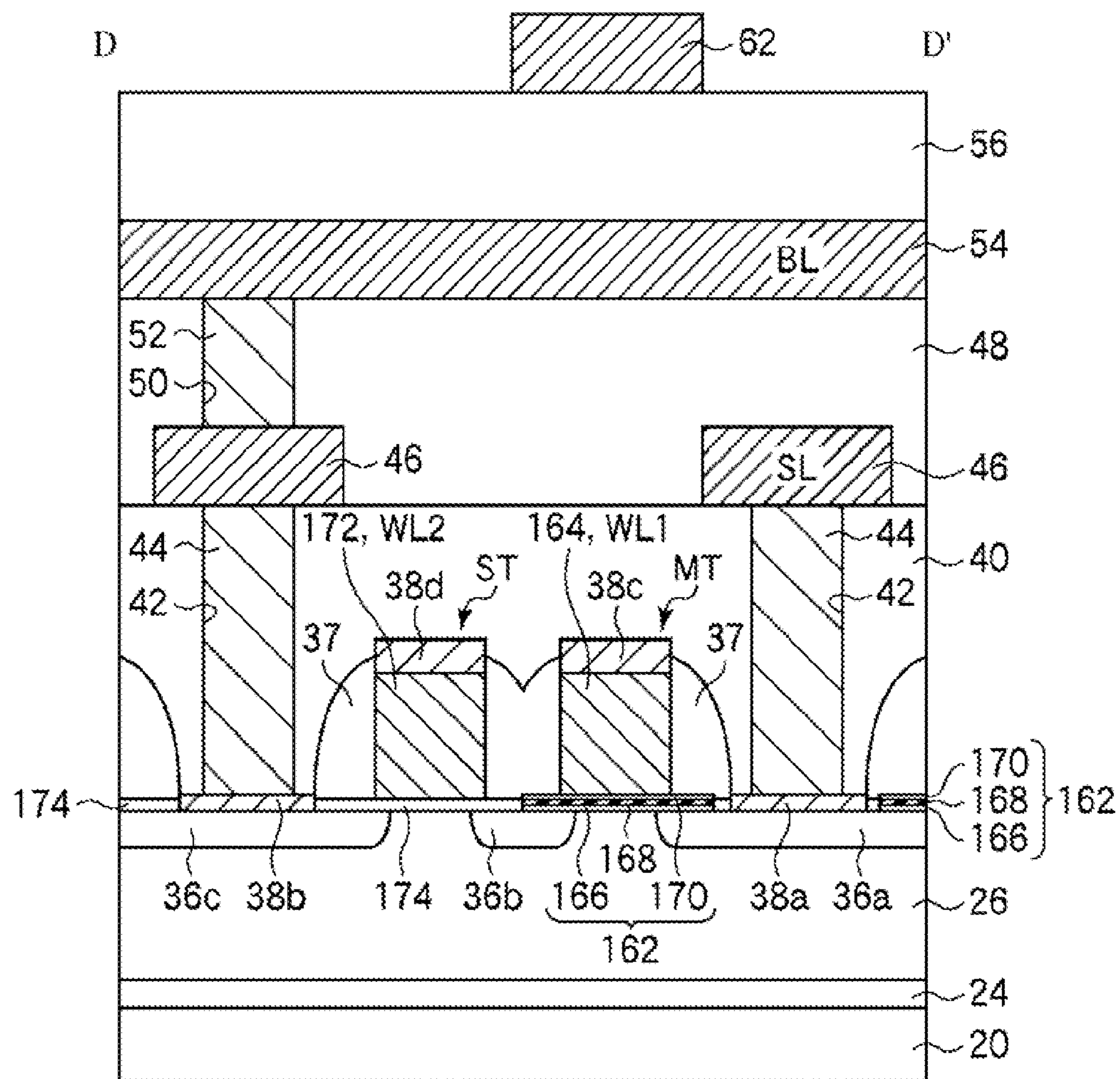


FIG. 44

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	CONSTANTLY V _{cc}	V _{cc} (0V)	0V
WRITE	0V (V _{cc})	5.5V (0V)	V step (0V)	V _{cc} (0V)	0V
ERASE	0V	5V	-5V	0V	0V

FIG. 45

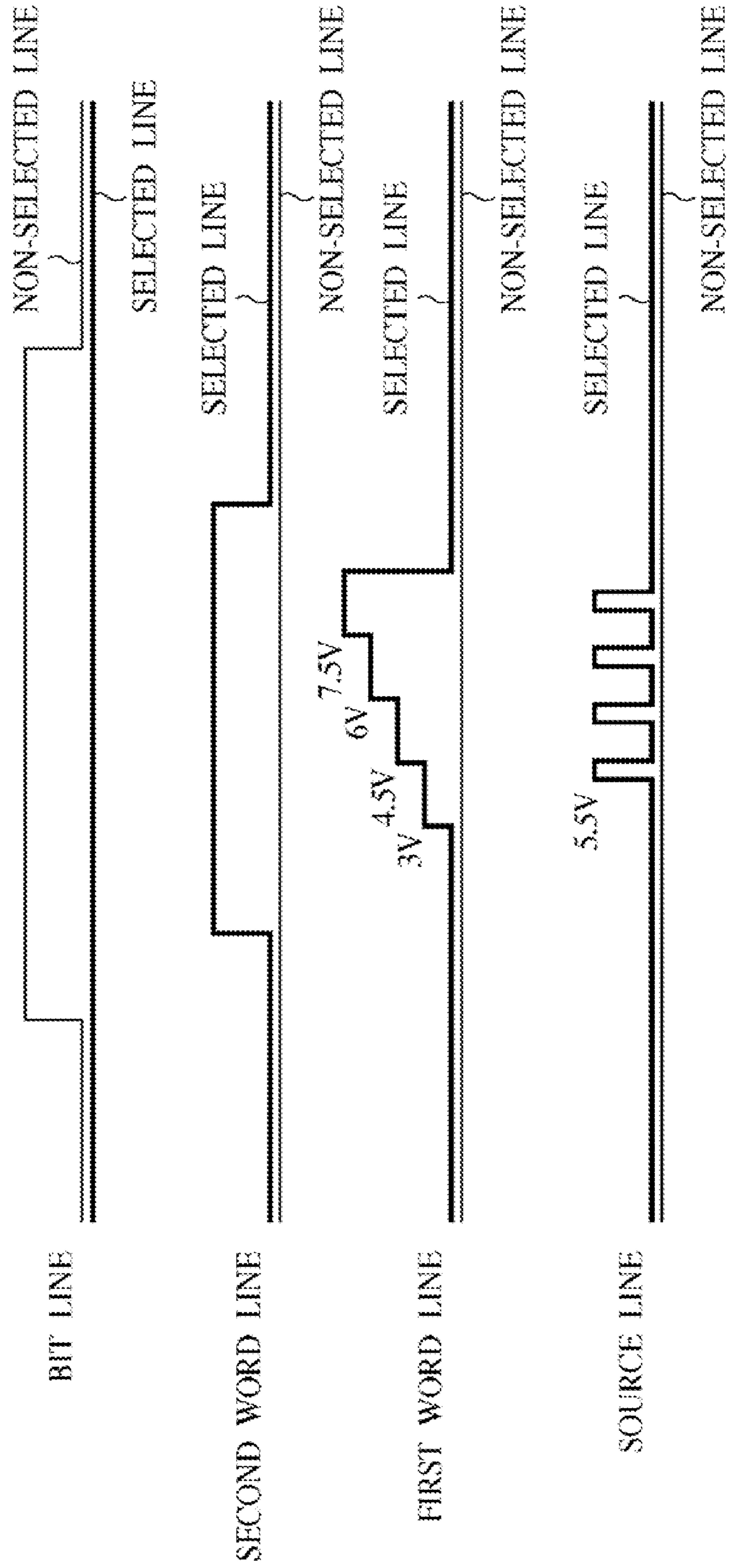


FIG. 46

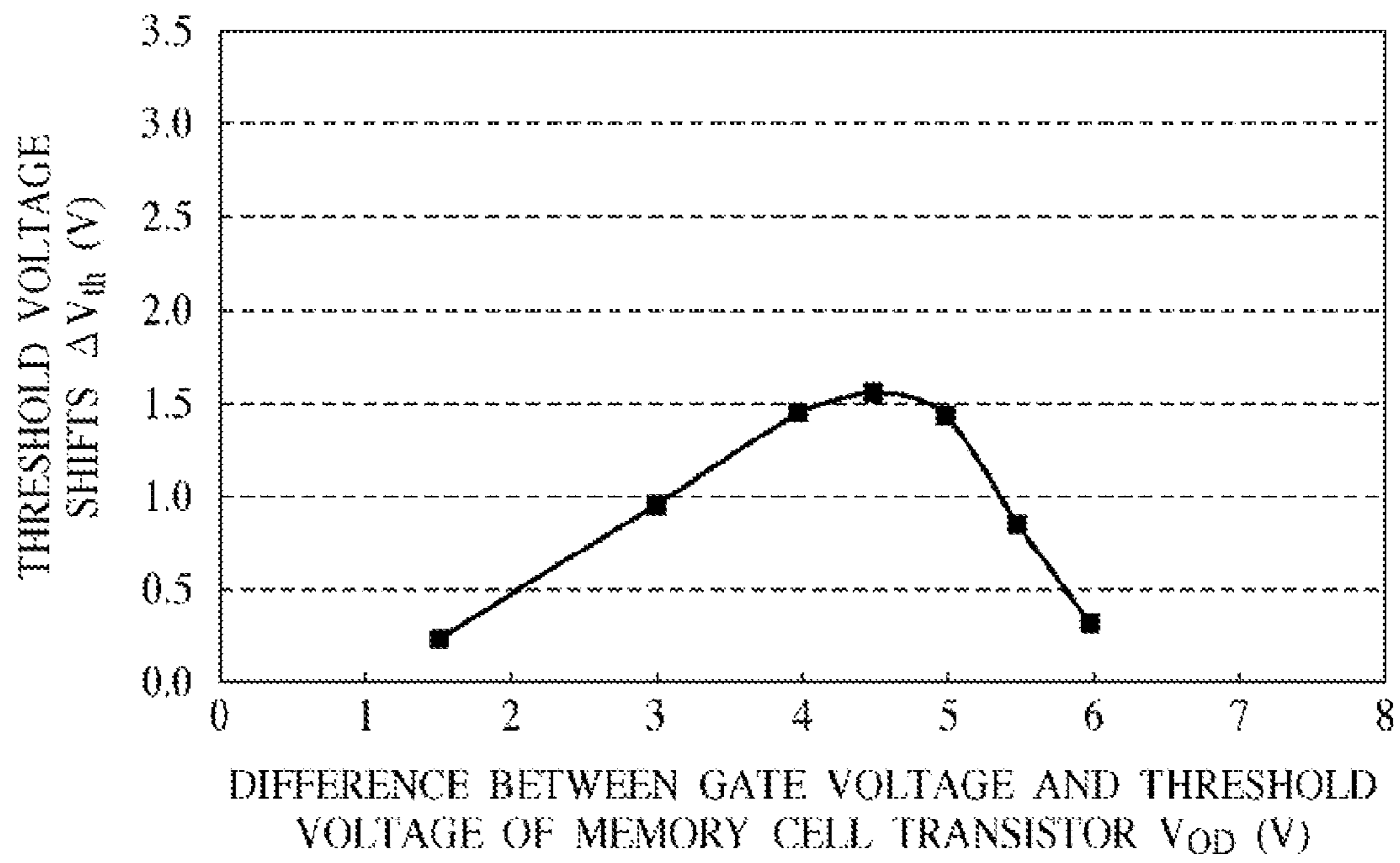


FIG. 47

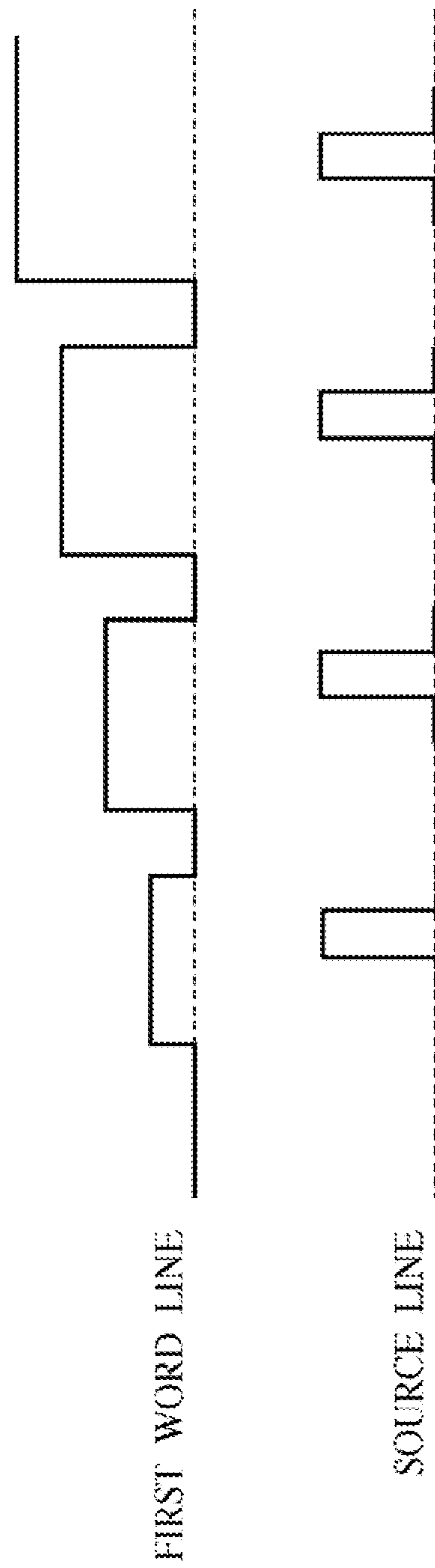
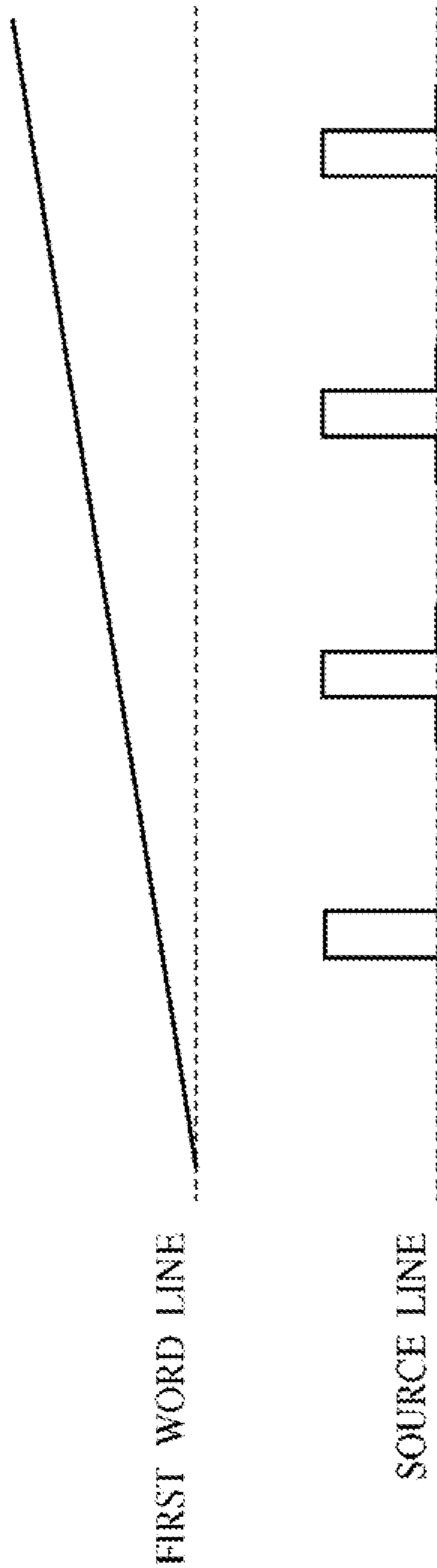
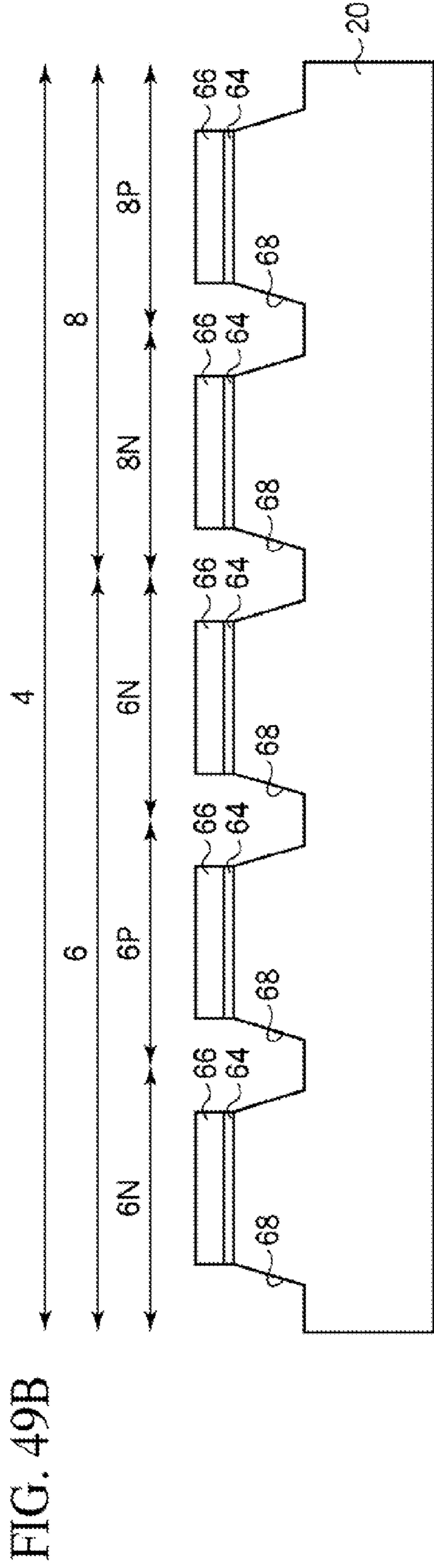
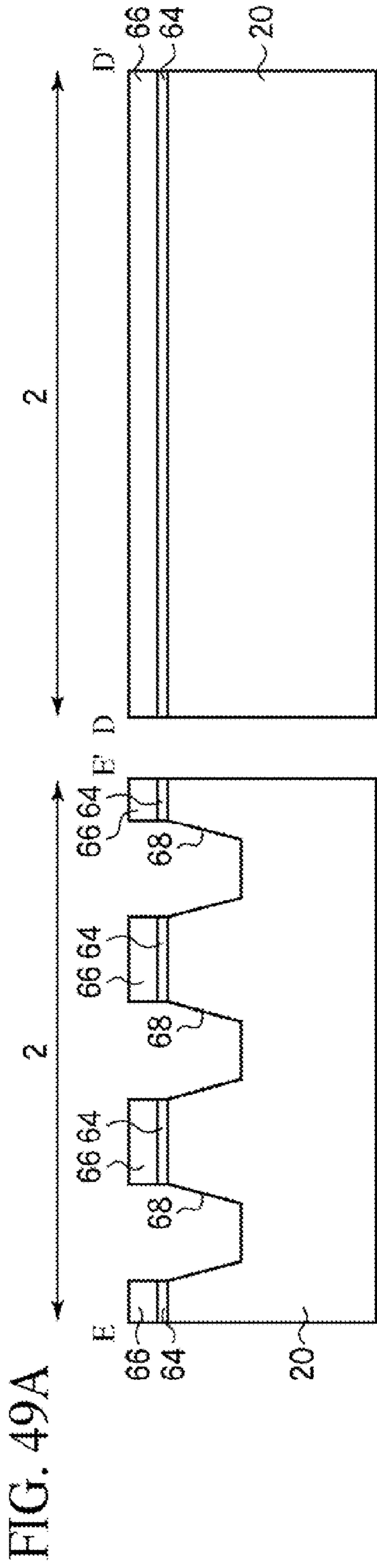


FIG. 48





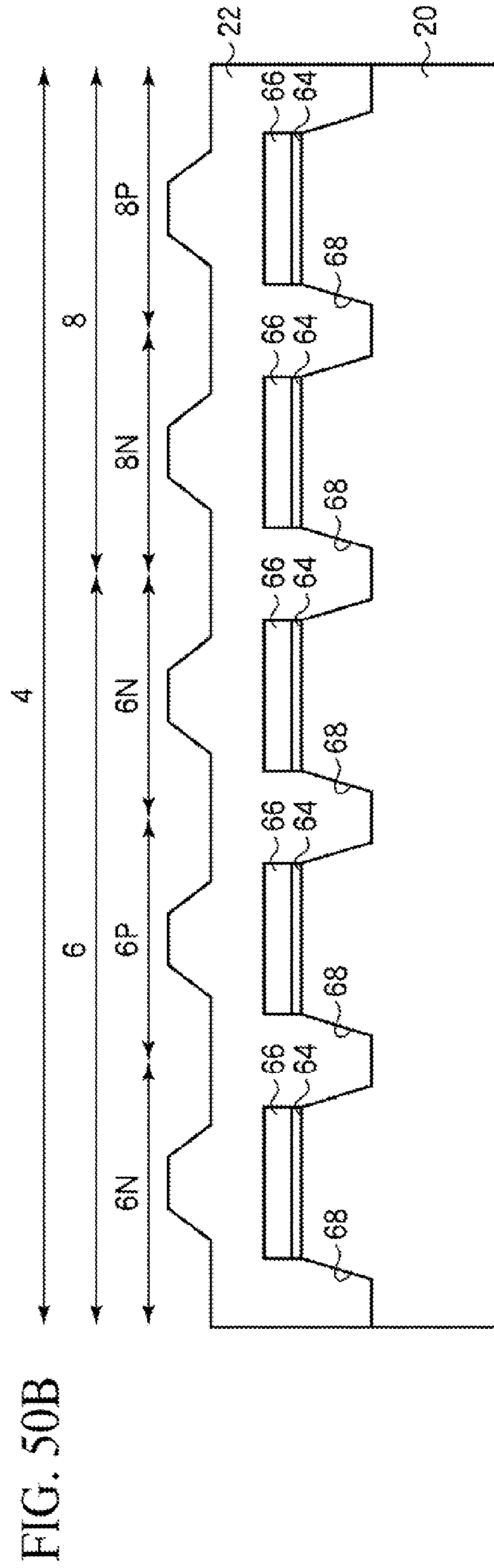
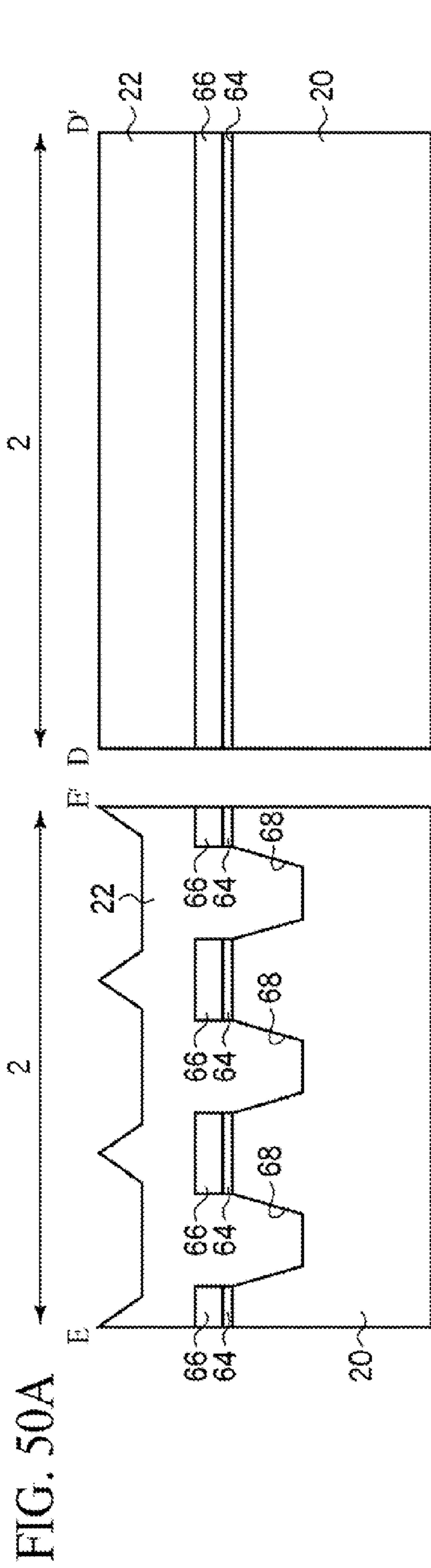


FIG. 51A

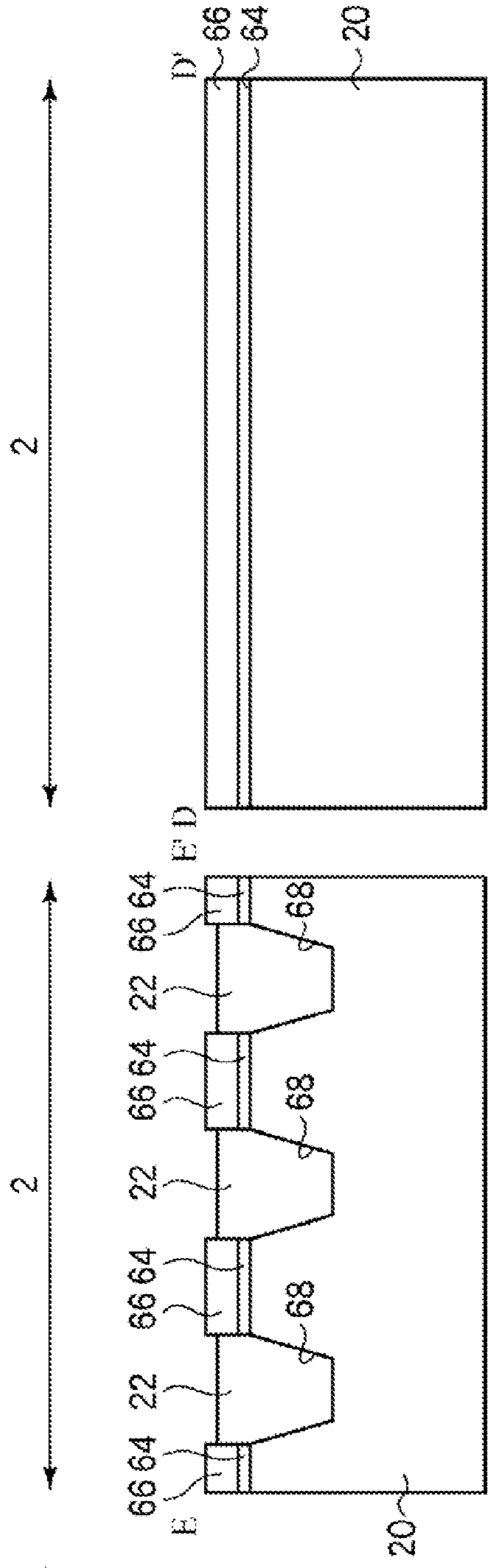
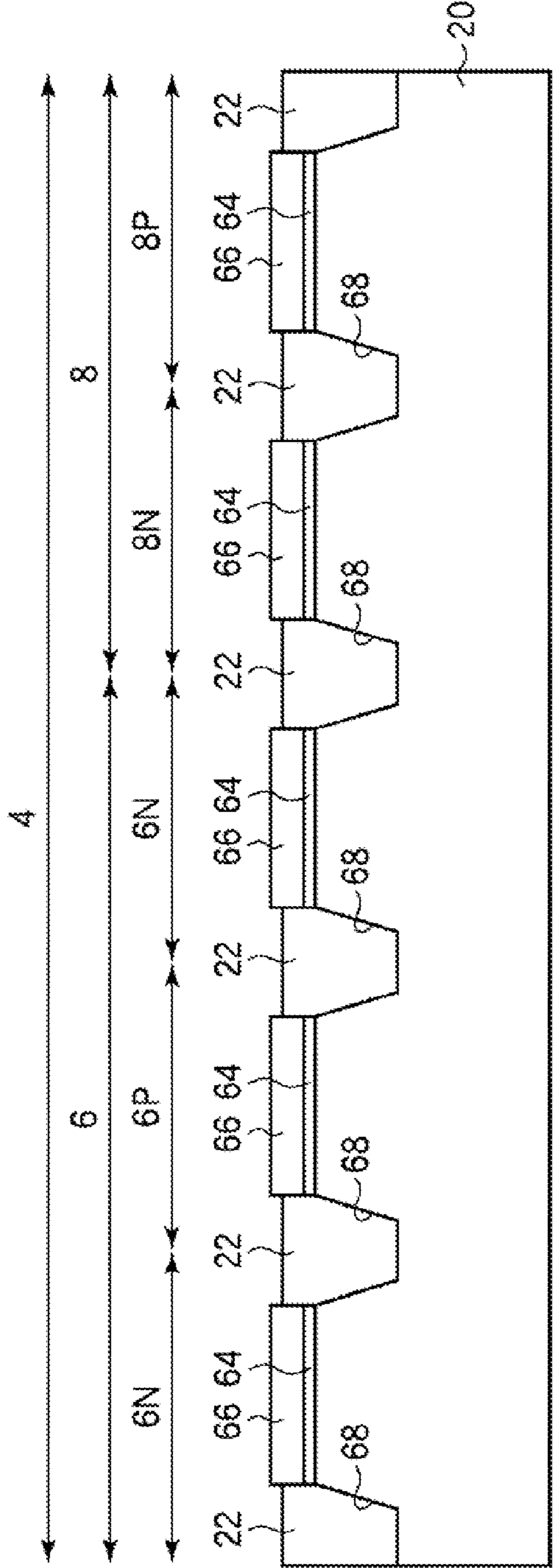
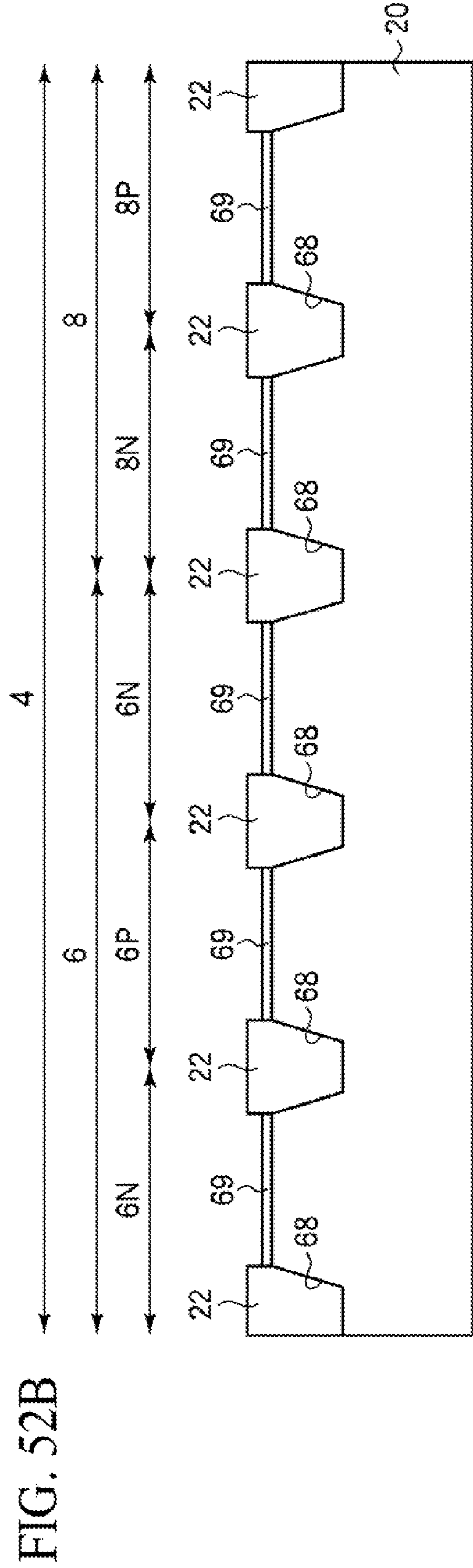
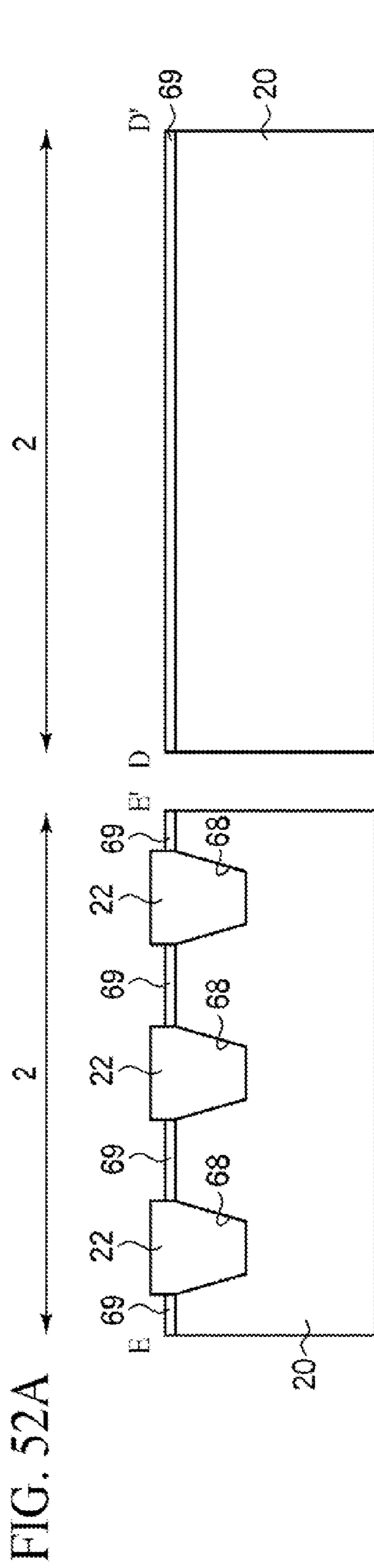


FIG. 51B





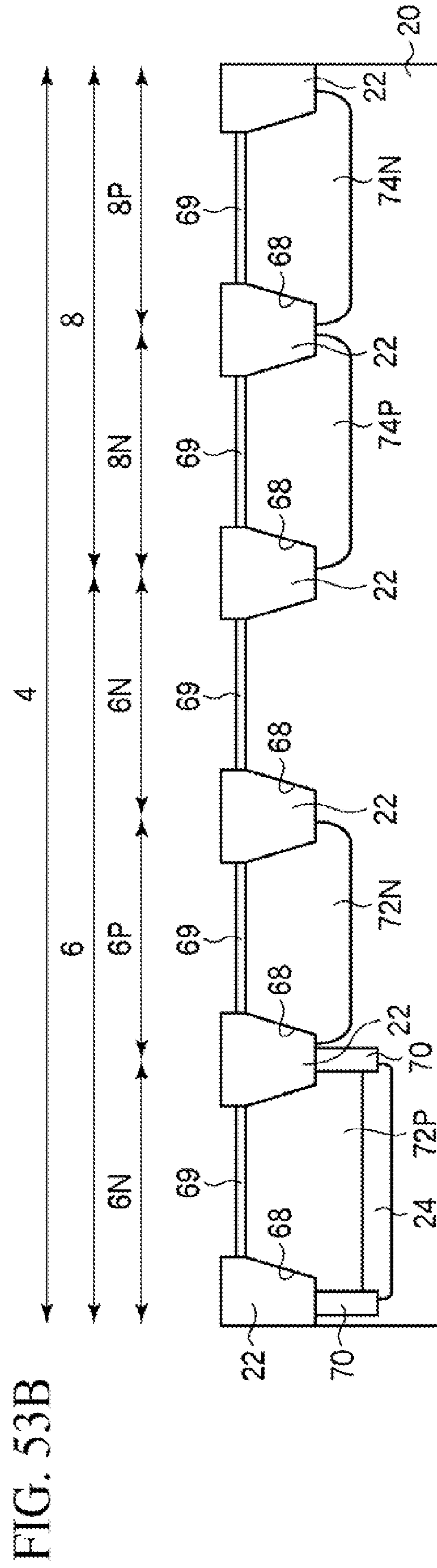
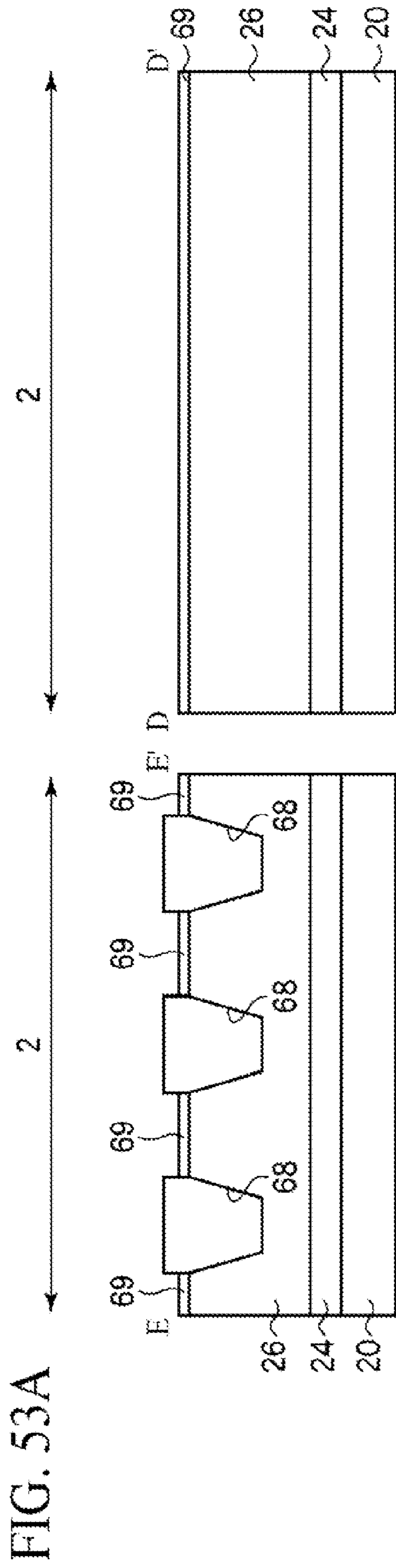


FIG. 54A

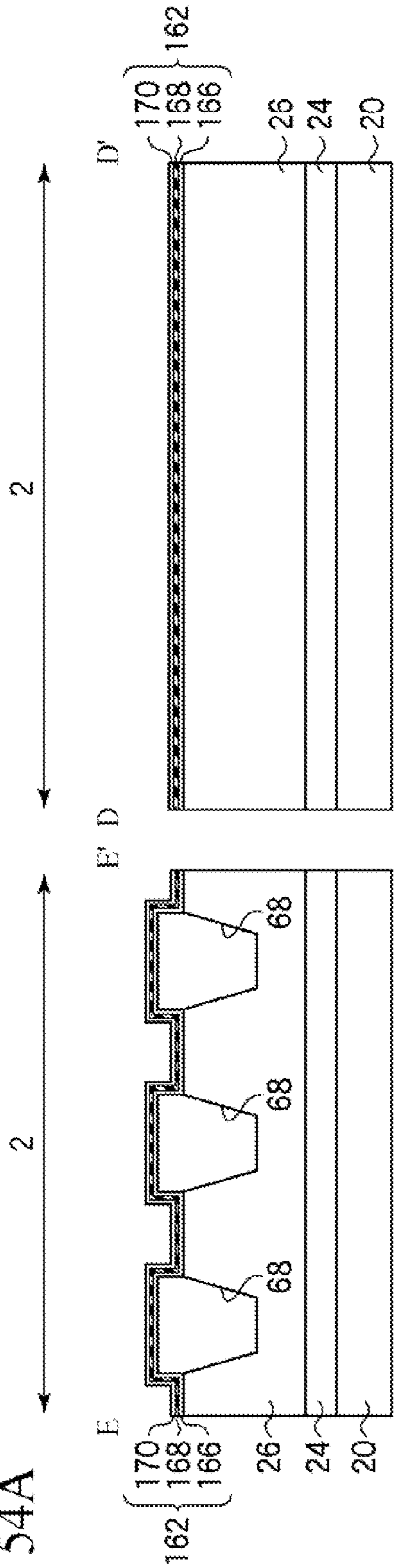


FIG. 54B

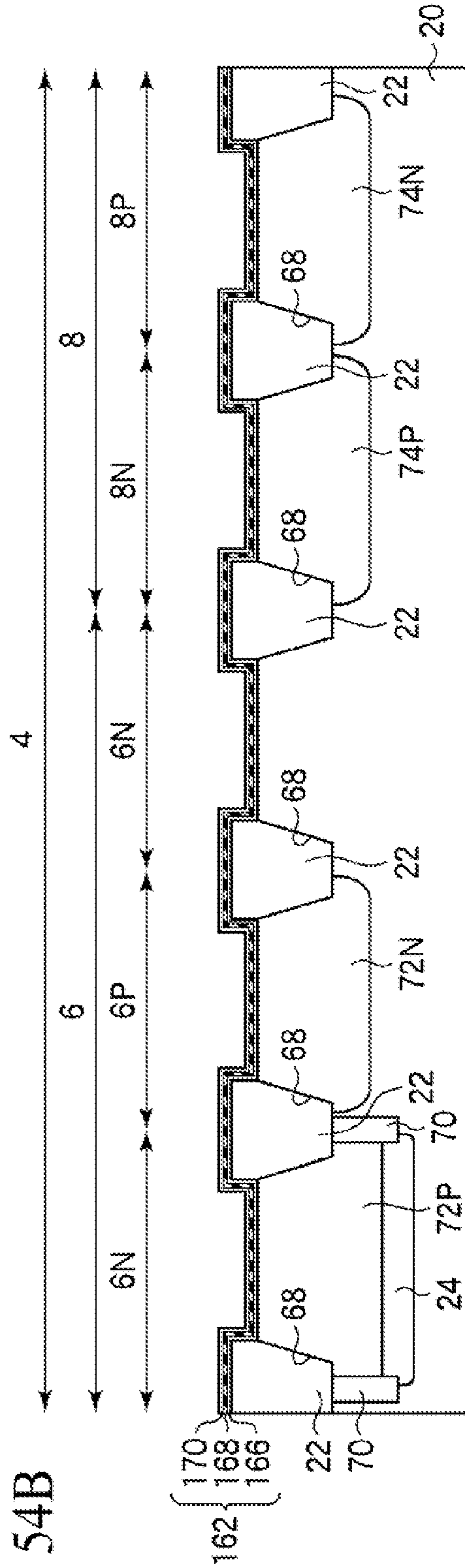


FIG. 55A

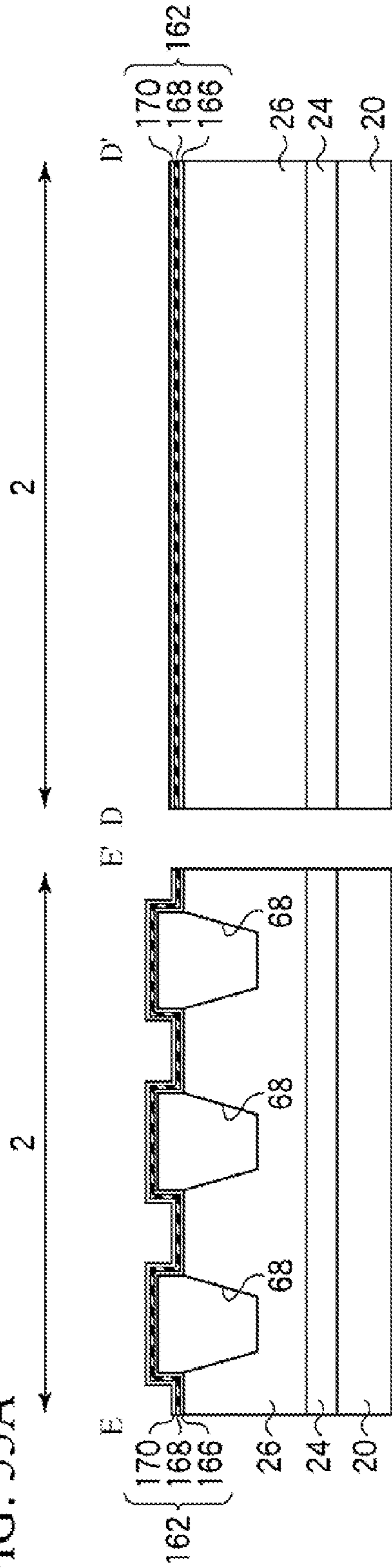
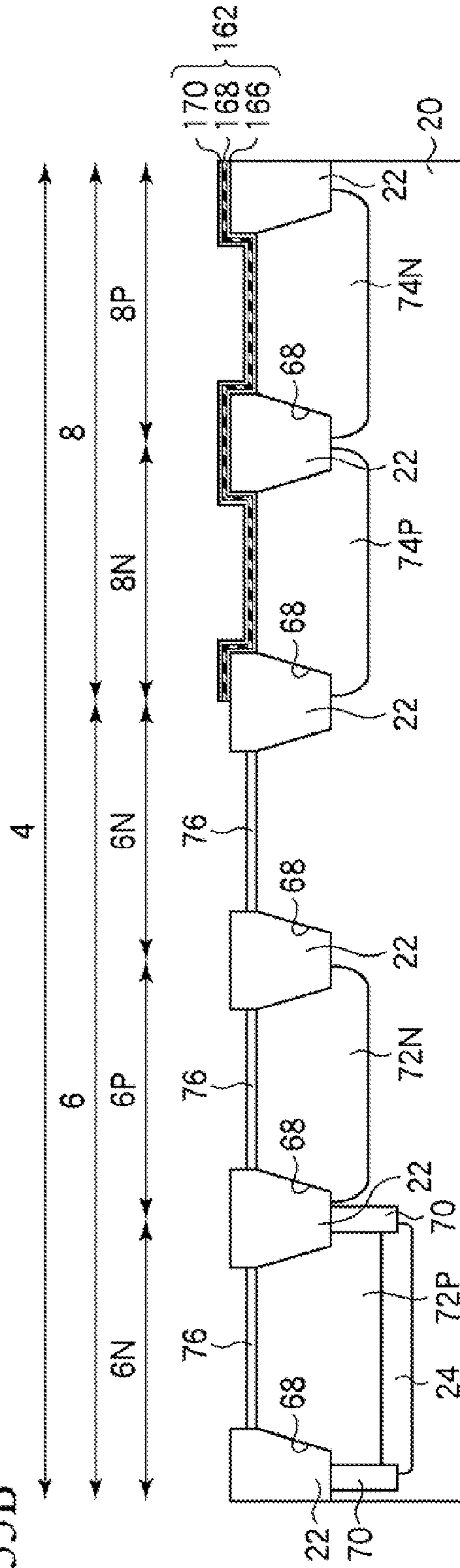
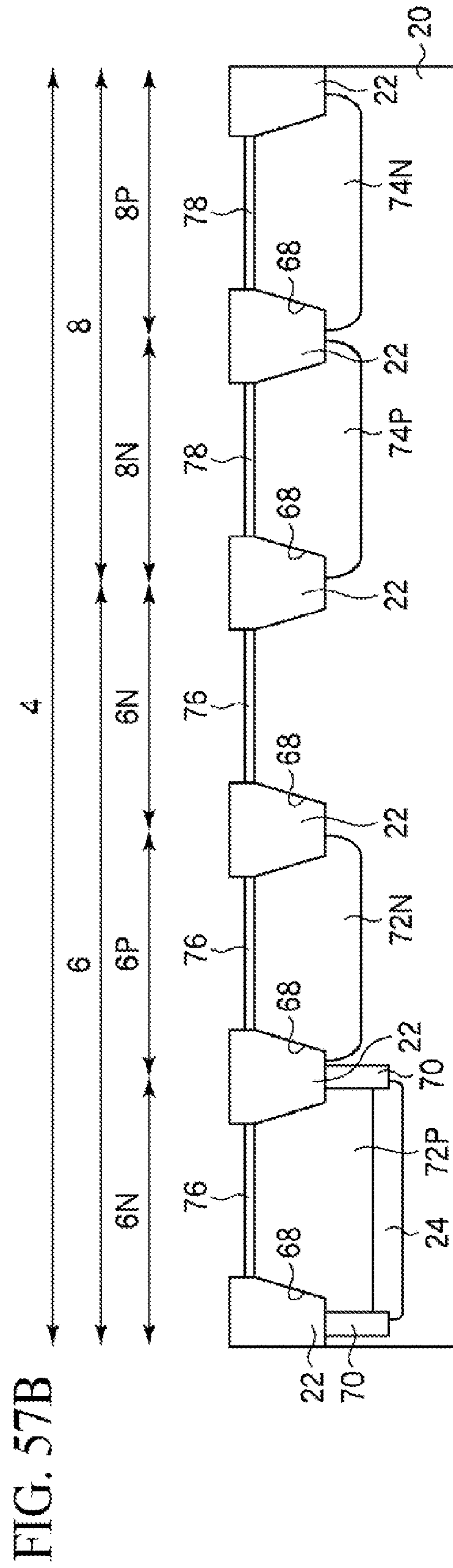
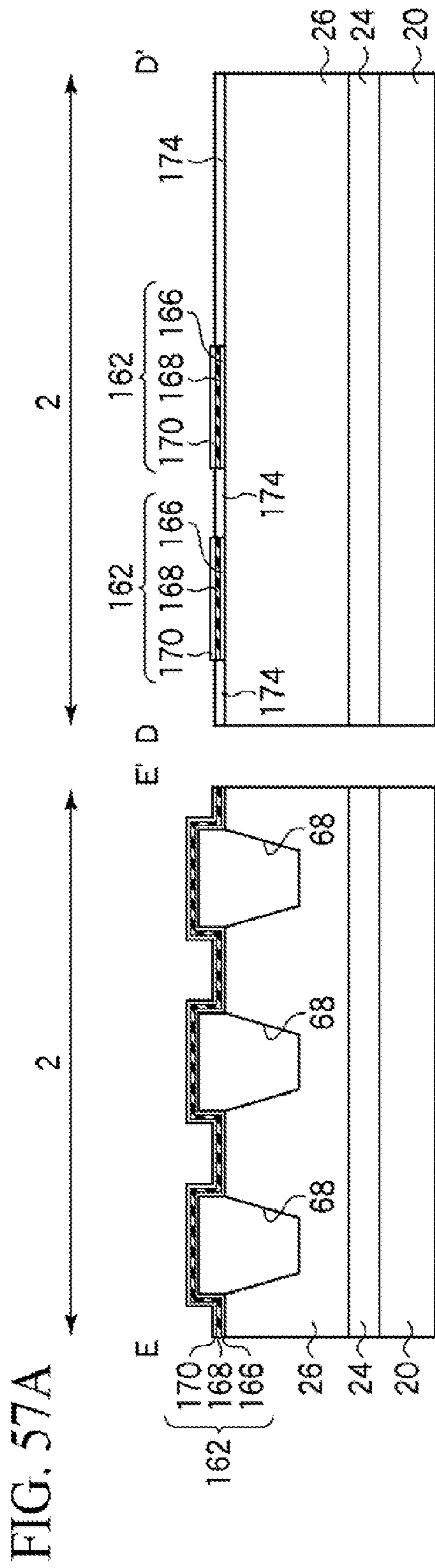


FIG. 55B





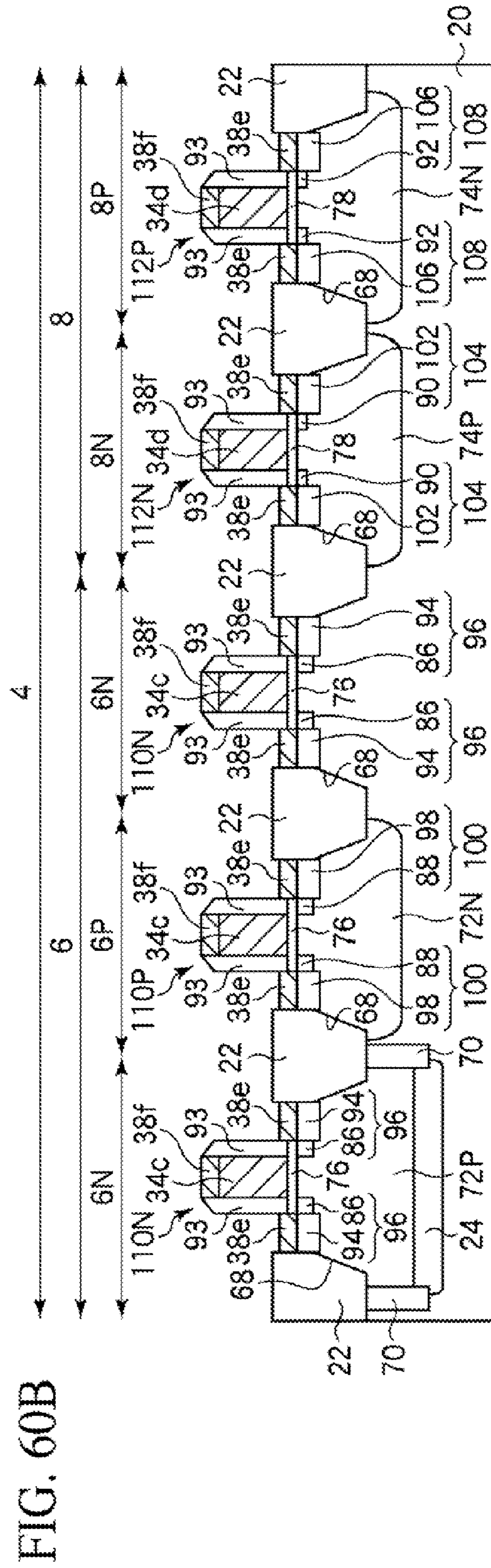
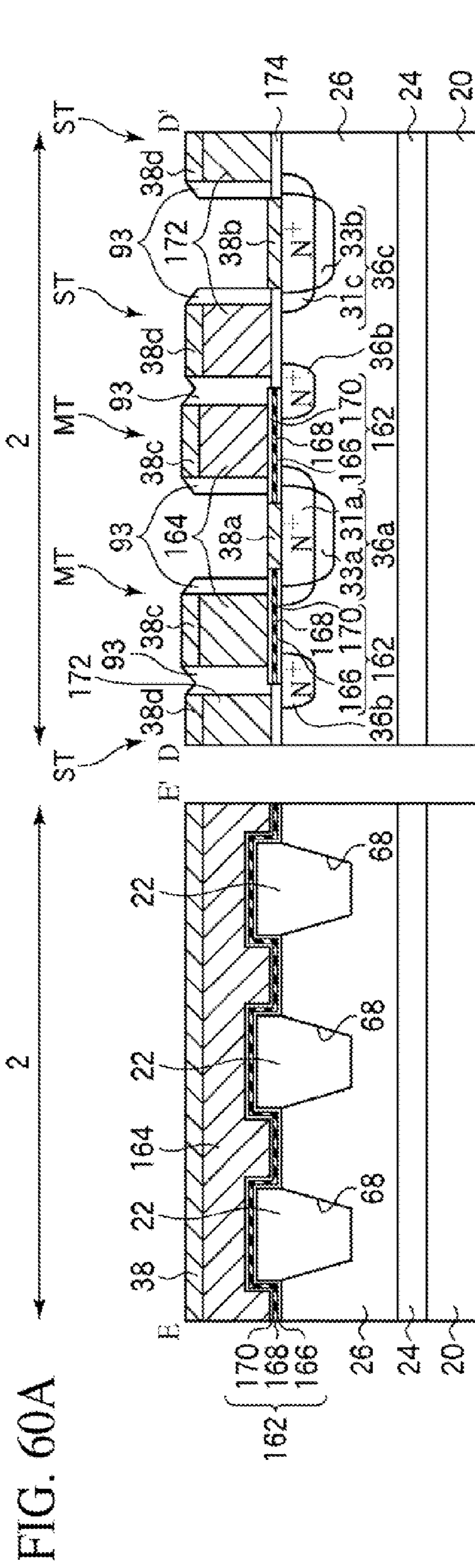
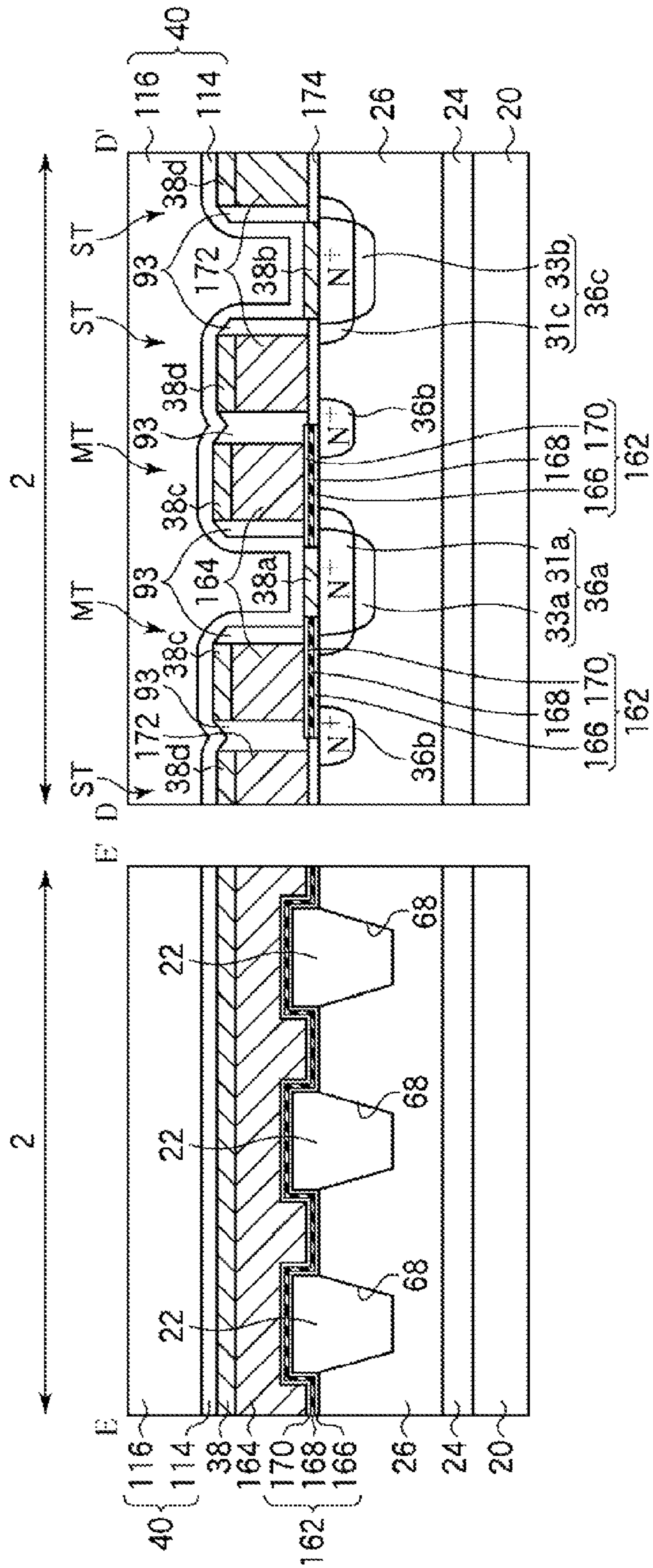


FIG. 61



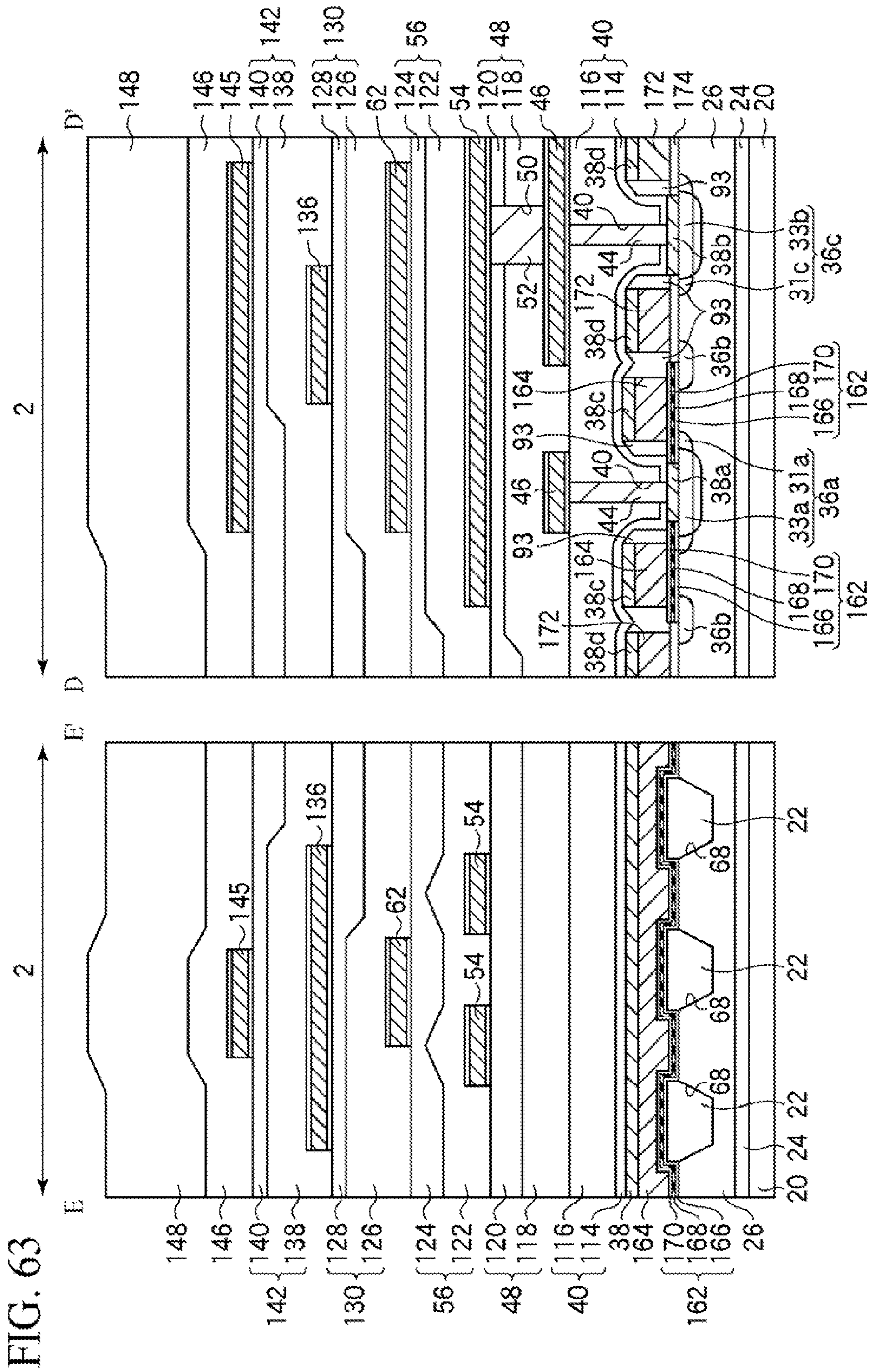


FIG. 66

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	CONSTANTLY V _{cc}	V _{cc} (0V)	0V
WRITE	0V (V _{cc})	5.5V (0V)	V step (0V)	V _{cc} (0V)	0V
ERASE	0V	5V	--5V	0V	0V

FIG. 67

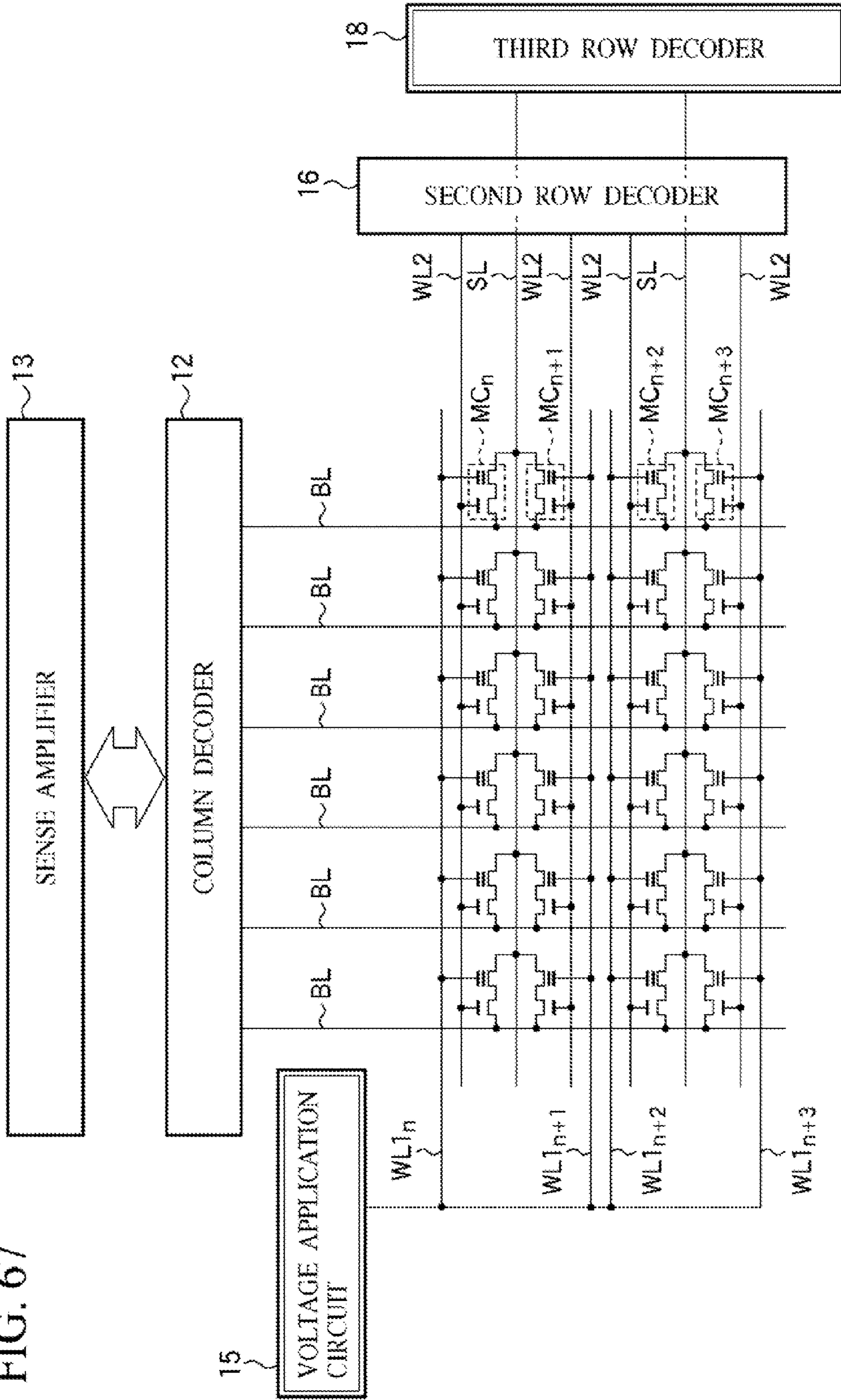


FIG. 68

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V _{cc} (0V)	0V (0V)	CONSTANTLY V _{cc}	V _{cc} (0V)	0V
WRITE	0V (V _{cc})	5.5V (0V)	V step (0V)	V _{cc} (0V)	0V
ERASE	0V	5V	-5V	0V	0V

FIG. 69

	BIT LINE	SOURCE LINE	FIRST WORD LINE	SECOND WORD LINE	WELL
READ	V_{cc} (0V)	0V (0V)	CONSTANTLY V_r	V_{cc} (0V)	0V
WRITE	0V (V_{cc})	5.5V (0V)	V step (0V)	V_{cc} (0V)	0V
ERASE	0V	5V	-5V	0V	0V

1**NONVOLATILE SEMICONDUCTOR
MEMORY DEVICE****CROSS-REFERENCE TO RELATED
APPLICATION**

This application is a Divisional of application Ser. No. 12/411,938 filed Mar. 26, 2009, which is a Continuation of International Application No. PCT/JP2006/319591, with an international filing date of Sep. 29, 2006, designating the United States of America, and International Application No. PCT/JP2007/068849, with an international filing date of Sep. 27, 2007, designating the United States of America, the entire contents of both of which are incorporated herein by reference.

FIELD

The embodiments discussed herein are related to a non-volatile semiconductor memory device.

BACKGROUND

Recently, nonvolatile semiconductor memory devices comprising memory cells each including a selecting transistor and a memory cell transistor are proposed.

In such nonvolatile semiconductor memory devices, bit lines and word lines and source lines, etc. are suitably selected by a column decoder and a row decoder to thereby select memory cells, and make read, write, erase, etc. of information for the selected memory cells.

SUMMARY

According to aspects of the embodiment, a nonvolatile semiconductor memory device including: a memory cell array of a plurality of memory cells arranged in a matrix, which each include a selecting transistor, and a memory cell transistor connected to the selecting transistor; a plurality of bit lines each commonly connecting the drains of a plurality of the selecting transistors present in one and the same column; a plurality of the first word lines each commonly connecting the gate electrodes of a plurality of the memory cell transistors present in one and the same row; a plurality of the second word lines each commonly connecting the select gates of a plurality of the selecting transistors present in one and the same row; a plurality of source lines each commonly connecting the sources of a plurality of the memory cell transistors present in one and the same row; a column decoder connected to the plural bit lines and controlling the potential of the plural bit lines; a voltage application circuit connected to the plural first word lines and controlling the potential of the plural first word lines; a first row decoder connected to the plural second word lines and controlling the potential of the plural second word lines; and a second row decoder connected to the plural source lines and controlling the potential of the plural source lines, the column decoder being formed of a circuit whose withstand voltage is lower than the voltage application circuit and the second row decoder, and the first row decoder being formed of a circuit whose withstand voltage is lower than the voltage application circuit and the second row decoder.

The object and advantages of the embodiments will be realized and attained by means of the elements and combinations particularly pointed out in the claims.

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It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are not restrictive of the embodiments, as claimed.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a circuit diagram of a nonvolatile semiconductor memory device according to a first embodiment;

FIG. 2 is a plan view of the memory cell array of the nonvolatile semiconductor memory device according to the first embodiment;

FIG. 3 is the sectional view along the A-A' line in FIG. 2;

FIG. 4 is the sectional view along the B-B' line in FIG. 2;

FIG. 5 is the sectional view along the C-C' line in FIG. 2;

FIG. 6 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the first embodiment;

FIGS. 7A and 7B are sectional views (Part 1) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 8A and 8B are sectional views (Part 2) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 9A and 9B are sectional views (Part 3) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 10A and 10B are sectional views (Part 4) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 11A and 11B are sectional views (Part 5) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 12A and 12B are sectional views (Part 6) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 13A and 13B are sectional views (Part 7) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 14A and 14B are sectional views (Part 8) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 15A and 15B are sectional views (Part 9) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIGS. 16A and 16B are sectional views (Part 10) of the nonvolatile semiconductor memory device according to the

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first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method;

FIG. 17 is a sectional view (Part 11) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 18 is a sectional view (Part 12) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 19 is a sectional view (Part 13) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 20 is a sectional view (Part 14) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 21 is a sectional view (Part 15) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 22 is a sectional view (Part 16) of the nonvolatile semiconductor memory device according to the first embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 23 is a partial circuit diagram of the nonvolatile semiconductor memory device according to a second embodiment;

FIG. 24 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the second embodiment;

FIG. 25 is the time chart of the writing method of the nonvolatile semiconductor memory device according to the second embodiment;

FIG. 26 is a partial circuit diagram of the nonvolatile semiconductor memory device according to a third embodiment;

FIG. 27 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the third embodiment;

FIG. 28 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to a fourth embodiment;

FIG. 29 is the time chart of the writing method of the nonvolatile semiconductor memory device according to the fourth embodiment;

FIG. 30 is a graph of the relationships between the difference between the control gate voltage and the threshold voltage, and the voltage between the source and the drain of the memory cell transistor;

FIG. 31 is the circuit diagram of the nonvolatile semiconductor memory device according to a fifth embodiment;

FIG. 32 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the fifth embodiment;

FIG. 33 is the circuit diagram of the nonvolatile semiconductor memory device according to a sixth embodiment;

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FIG. 34 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the sixth embodiment;

FIG. 35 is the circuit diagram of the nonvolatile semiconductor memory device according to a seventh embodiment;

FIG. 36 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the seventh embodiment;

FIG. 37 is the circuit diagram of the nonvolatile semiconductor memory device according to an eighth embodiment;

FIG. 38 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the eighth embodiment;

FIG. 39 is a sectional view of the nonvolatile semiconductor memory device according to a ninth embodiment;

FIG. 40 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the ninth embodiment;

FIG. 41 is the circuit diagram of the nonvolatile semiconductor memory device according to a tenth embodiment;

FIG. 42 is a plan view of the nonvolatile semiconductor memory device according to the tenth embodiment, which illustrate the memory cell array;

FIG. 43 is the sectional view along the D-D' line of FIG. 42;

FIG. 44 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the tenth embodiment;

FIG. 45 is the time chart of the writing method of the nonvolatile semiconductor memory device according to the tenth embodiment;

FIG. 46 is a graph of the relationships between the difference between the gate voltage and the threshold voltage of the memory cell transistor, and shifts of the threshold voltage;

FIG. 47 is the time chart (Part 1) of another example of the writing method of the nonvolatile semiconductor memory device according to the tenth embodiment;

FIG. 48 is the time chart (Part 2) of another example of the writing method of the nonvolatile semiconductor memory device according to the tenth embodiment;

FIGS. 49A and 49B are sectional views (Part 1) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 50A and 50B are sectional views (Part 2) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 51A and 51B are sectional views (Part 3) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 52A and 52B are sectional views (Part 4) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 53A and 53B are sectional views (Part 5) of the nonvolatile semiconductor memory device according to the

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tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 54A and 54B are sectional views (Part 6) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 55A and 55B are sectional views (Part 7) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 56A and 56B are sectional views (Part 8) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 57A and 57B are sectional views (Part 9) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 58A and 58B are sectional views (Part 10) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIGS. 59A and 59B are sectional views (Part 11) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 60 is sectional views (Part 12) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 61 is a sectional view (Part 13) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 62 is sectional views (Part 14) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 63 is sectional views (Part 15) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 64 is sectional views (Part 16) of the nonvolatile semiconductor memory device according to the tenth embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrates the method;

FIG. 65 is the circuit diagram of the nonvolatile semiconductor memory device according to an eleventh embodiment;

FIG. 66 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the eleventh embodiment;

FIG. 67 is the circuit diagram of the nonvolatile semiconductor memory device according to a twelfth embodiment;

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FIG. 68 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the twelfth embodiment;

FIG. 69 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to a thirteenth embodiment;

FIG. 70 is a sectional view of the nonvolatile semiconductor memory device according to a fourteenth embodiment.

DESCRIPTION OF EMBODIMENTS

In the proposed nonvolatile semiconductor memory devices, both the column decoder and the row decoder use high withstand voltage circuits (high voltage circuits). The high withstand voltage circuits comprise high withstand voltage transistors having the gate insulation film formed thick, which makes it difficult to read information written in the memory cells at high speed.

Preferred embodiments of the present invention will be explained with reference to accompanying drawings.

[a] First Embodiment

The nonvolatile semiconductor memory device according to a first embodiment, a reading method, a writing method and an erasing method of the nonvolatile semiconductor memory device, and a method for manufacturing the nonvolatile semiconductor memory device will be explained with reference to FIGS. 1 to 22.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIGS. 1 to 6. FIG. 1 is a circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment.

As illustrated in FIG. 1, the nonvolatile semiconductor memory device according to the present embodiment comprises memory cells MC each including a selecting transistor ST and a memory cell transistor MT connected to the selecting transistor ST. The selecting transistor ST has the source connected to the drain of the memory cell transistor MT. More specifically, the source of the selecting transistor ST and the drain of the memory cell transistor MT are integrally formed of one impurity diffused layer.

A plurality of the memory cells MC are laid out in a matrix. The plural memory cells MC laid out in a matrix form a memory cell array 10.

The drains of a plurality of the selecting transistors ST present in one and the same column are commonly connected by a bit line BL.

The control gates of a plurality of the memory cell transistors MT present in one and the same row are commonly connected by the first word line WL1.

The select gates of a plurality of the selecting transistors ST present in one and the same row are commonly connected by the second word line WL2.

The sources of a plurality of the memory cell transistors MT present in one and the same row are commonly connected by a source line SL.

A plurality of bit lines BL commonly connecting the drains of the selecting transistors ST are connected to a column decoder 12. The column decoder 12 is for controlling the potential of plural bit lines BL commonly connecting the drains of the selecting transistors ST. The column decoder 12 is connected to a sense amplifier 13 for detecting current

flowing in the bit lines BL. The column decoder **12** is formed of a low voltage circuit, which is operative at relatively low voltage. The low voltage circuit is a circuit whose withstand voltage is relatively low but is operative at high speed. The gate insulation film (not illustrated) of the transistors of the low voltage circuit is formed relatively thin. Accordingly, the transistors of the low voltage circuit used in the column decoder **12** can operate at relatively high speed. The column decoder **12** is formed of the low voltage circuit in the present embodiment because it is not necessary to apply high voltage to the drains of the selecting transistors ST but the selecting transistors ST is operated at high speed when information written in the memory cell transistors MT is read. In the present embodiment, the column decoder **12** is formed of the low voltage circuit, whereby the selecting transistors ST can be operated at relatively high speed, which resultantly allows the nonvolatile semiconductor memory device to operate at high read speed.

A plurality of the first word lines WL1 commonly connecting the control gates of the memory cell transistors MT are connected to the first row decoder (voltage application circuit) **14**. The first row decoder is for controlling the potential of the respective plural first word lines WL1 commonly connecting the control gates of the memory cell transistors MT. The first row decoder **14** is formed of a high voltage circuit (high withstand voltage circuit). The high voltage circuit is a circuit whose operation speed is relatively low and whose withstand voltage is relatively high. The gate insulation film (not illustrated) of the transistors (not illustrated) of the high voltage circuit is formed relatively thick so as to ensure sufficient withstand voltage. Accordingly, the operation speed of the transistors of the high voltage circuit is lower in comparison with the operation speed of the transistors of the low voltage circuit. The first row decoder **14** is formed of the high voltage circuit in the present embodiment because high voltages is applied to the first word lines WL1 when information is written into the memory cell transistors MT or information written in the memory cell transistors MT is erased. As will be described later, when information written in the memory cell transistors MT is read, a power supply voltage V_{CC} is constantly applied to the first word lines WL1. Accordingly, even with the relatively low operation speed of the high voltage circuit used in the first row decoder **14**, there is no special problem.

A plurality of second word lines WL2 commonly connecting the select gates of the selecting transistors ST are connected to the second row decoder **16**. The second row decoder **16** is for controlling the potential of the plural second word lines WL2 commonly connecting the select gates of the selecting transistors ST. The second row decoder **16** is formed of a low voltage circuit (low withstand voltage circuit). The second row decoder **16** is formed of a low voltage circuit in the present embodiment because it is not necessary to apply high voltage to the select gates of the selecting transistors ST, but it is preferably to operate the selecting transistors ST at high speed. In the present embodiment, because of the second row decoder **16** comprising a low voltage circuit, the selecting transistors ST can operate at relatively high speed, which resultantly permits the nonvolatile semiconductor memory device to have high read speed.

A plurality of source lines SL commonly connecting the memory cell transistors MT are connected to the third row decoder **18**. The third row decoder **18** is for controlling the potential of the plural source lines SL commonly connecting the sources of the memory cell transistors MT. The third row decoder **18** is formed of a high voltage circuit (high withstand voltage circuit). The third row decoder **18** is formed of a high

voltage circuit in the present embodiment because high voltage is applied to the source lines SL when information is written into the memory cell transistors MT. As will be described later, when information written in the memory cell transistors MT is read, the source lines SL are constantly grounded. Accordingly, the operation speed of the third row decoder **18** whose operation speed is relatively low makes no special problem.

Then, the structure of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIGS. **2** to **5**. FIG. **2** is a plan view of the memory cell array of the nonvolatile semiconductor memory device according to the present embodiment. FIG. **3** is the sectional view along the A-A' line in FIG. **2**. FIG. **4** is the sectional view along the B-B' line in FIG. **2**. FIG. **5** is the sectional view along the C-C' line in FIG. **2**.

In a semiconductor substrate **20**, device isolation regions **22** for defining device regions **21** are formed. The semiconductor substrate **20** is, e.g., a P-type silicon substrate. The device regions **22** are formed by, e.g., STI (Shallow Trench Isolation).

In the semiconductor substrate **20** with the device isolation regions **22** formed in, an N-type buried diffused layer **24** is formed. The upper part of the N-type buried diffused layer **24** is a P-type well **26**.

On the semiconductor substrate **20**, floating gates **30a** are formed with a tunnel insulation film **28a** formed therebetween. The floating gates **30a** in the respective device regions **21** are electrically isolated from each other.

On the floating gates **30a**, control gates **34a** are formed via an insulation film **32a** formed therebetween. The control gates **34a** of the memory cell transistors MT present in one and the same row are commonly connected. In other words, on the floating gates **30**, the first word lines WL1 commonly connecting the control gates **34a** are formed with the insulation film **32a** formed therebetween.

On the semiconductor substrate **20**, the select gates **30b** of the selecting transistors ST are formed in parallel with the floating gates **30a**. The select gates **30b** of the selecting transistors ST present in one and the same row are commonly connected. In other words, on the semiconductor substrate **20**, the second word lines WL2 commonly connecting the select gates **30b** are formed with the gate insulation film **28b** formed therebetween. The film thickness of the gate insulation film **28b** of the selecting transistors ST is the same as the film thickness of the tunnel insulation film **28a** of the memory cell transistors MT.

On the select gates **30b**, a polycrystalline silicon layer **34b** is formed with an insulation film **32b** formed therebetween.

In the semiconductor substrate **20** on both sides of each floating gate **30a** and in the semiconductor substrate on both sides of each select gate **30b**, an N-type impurity diffused layers **36a**, **36b**, **36c** are formed.

The impurity diffused layer **36b** forming the drain of the memory cell transistor MT, and the impurity diffused layer **36b** forming the source of the selecting transistor ST are formed of one and the same impurity diffused layer **36b**.

On the side wall of the layer structure of the floating gate **30a** and the control gate **34a**, a sidewall insulation film **37** is formed.

The sidewall insulation film **37** is formed also on the side wall of the layer structure of the select gate **30b** and the polycrystalline silicon layer **34b**.

On the source region **36a** of the memory cell transistor MT, on the drain region of the selecting transistor ST, in the upper part of the control gate **34a** and in the upper part of the polycrystalline silicon layer **34b**, silicide layers **38a-38d** of,

e.g., cobalt silicide are respectively formed. The silicide layer **38a** on the source electrode **36a** functions as the source electrode. The silicide layer **38c** on the drain electrode **36c** functions as the drain electrode.

Thus, the memory cell transistors MT each comprising the floating gate **30a**, the control gate **34a** and the source/drain diffused layers **36a**, **36b** are formed.

The selecting transistors ST each comprising the select gate **30b** and the source/drain diffused layers **36b**, **36c** are formed. The selecting transistors ST are NMOS transistors. In the present embodiments, NMOS transistors whose operation speed is higher than PMOS transistors are used as the selecting transistors ST, which can contribute to the operation speed increase.

On the semiconductor substrate **20** with the memory cell transistors MT and the selecting transistors ST formed on, an inter-layer insulation film **40** of a silicon nitride film (not illustrated) and a silicon oxide film (not illustrated) is formed.

In the inter-layer insulation film **40**, contact holes **42** are formed respectively down to each source electrode **38a** and the drain electrode **38b**.

In the contact holes **42**, conductor plugs **44** of, e.g., tungsten are buried.

On the inter-layer insulation film **40** with the conductor plugs **44** buried in, interconnections (the first metal interconnection layers) **46** are formed.

On the inter-layer insulation film **40** with the interconnections **46** formed on, an inter-layer insulation film **48** is formed.

In the inter-layer insulation film **48**, a contact hole **50** is formed down to the interconnection **46**.

In the contact hole **50**, a conductor plug **52** of, e.g., tungsten is buried.

On the inter-layer insulation film **48** with the conductor plug **52** buried in, interconnections (the second metal interconnection layers) **54** are formed.

On the inter-layer insulation film **48** with the interconnections **54** formed on, an inter-layer insulation film **56** is formed.

In the inter-layer insulation film **56**, a contact hole **58** is formed down to the interconnection **54**.

In the contact hole **58**, a conductor plug **60** of, e.g., tungsten is buried.

On the inter-layer insulation film **56** with the conductor plug **60** buried in, an interconnection (the third metal interconnection layer) **62** is formed.

Thus, the memory cell array **10** (see FIG. 1) of the non-volatile semiconductor memory device according to the present embodiment is constituted.

The explanation has been made here by means of the example as illustrated FIG. 1 that the memory cell transistors MT of each row are connected to the source line SL associated with said each row, but as will be detailed later with reference to FIG. 65, as in the nonvolatile semiconductor memory device according to an eleventh embodiment, the sources of the memory cell transistors MT present in rows adjacent to each other may be connected by a common source line SL. The plan view of FIG. 2 corresponds to the example that the sources of the memory cells MT present in rows adjacent to each other are connected by a common source line SL. The sources of the memory cell transistors MT present in rows adjacent to each other are connected by a common source line SL, whereby the area of the memory cell array region **2** can be small, and the nonvolatile semiconductor memory device can be downsized. The number of the source lines SL to be controlled by the third row decoder **18** can be made smaller, whereby the third row decoder **18** can be simplified.

(Operations of Nonvolatile Semiconductor Memory Device)

Next, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 6. FIG. 6 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 6, the voltages in the parentheses are the potentials of the non-selected lines. In FIG. 6, F indicates floating.

(Reading Method)

First, the reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 6.

When information written the memory cell transistors MT is read, the potentials of the respective parts are set as follows. That is, the bit line BL connected to a memory cell MC to be selected is V_{CC} . The potential of the bit lines other than the selected bit line is 0 V. The potential of all the source lines is 0 V. The potential of the first word lines WL1 is constantly V_{CC} on standby for read. The potential of the second word line WL2 connected to the memory cell MC to be selected is V_{CC} . The potential of the second word lines WL2 other than the selected second word line WL2 is 0 V. The potential of all the wells **26** is 0 V. In the present embodiment, the potential of the source lines SL is set at 0 V on standby for read, and the potential of the first word lines WL1 is constantly set at V_{CC} on standby for read, which allows information written in the memory cell transistors MT to be read by controlling only the potentials of the bit lines BL and the potential of the second word lines WL2. In the present embodiment, the column decoder **12** for controlling the potential of the bit lines BL is formed of a low voltage circuit as described above, whereby the bit lines BL are controlled at high speed. The second row decoder **16** for controlling the potential of the second word lines WL2 is formed of a low voltage circuit as described above, whereby the second word lines WL2 can be controlled at high speed. Thus, according to the present embodiment, information written in the memory cell transistors MT can be read at high speed.

When information is written into the memory cell transistor MT, i.e., the information in the memory cell transistor MT is "0", charges are stored in the floating gate **30a** of the memory cell transistor MT. In this case, no current flows between the source diffused layer **36a** of the memory cell transistor MT and the drain diffused layer **36c** of the selecting transistor ST, and no current flows in one selected bit line BL. In this case, the information in the memory cell transistor MT is judged "0".

On the other hand, when information written in the memory cell transistor MT has been erased, i.e., the information in the memory cells MT is "1", no charges are stored in the floating gate **30a** of the memory cell transistor MT. In this case, current flows between the source diffused layer **36a** of the memory cell transistor MT and the drain diffused layer **36c** of the selecting transistor ST, and current flows in one selected bit line BL. The current flowing in one selected bit line BL is detected by the sense amplifier **13**. In this case, the information in the memory cell transistor MT is judged "1".

(Writing Method)

Then, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 6.

When information is written into the memory cell transistor MT, the potentials of the respective parts are set as follows. That is, the potential of the bit line BL connected to a memory cell MC to be selected is 0 V. The potential of the bit lines BL

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other than the selected bit line BL is floating. The potential of the source line SL connected to the memory cell MC to be selected is set at, e.g., 5 V (the second potential). The potential of the source lines SL other than the selected source line SL is 0 V or floating. The potential of the first word line WL1 connected to the memory cell MC to be selected is, e.g., 9 V (the third potential). On the other hand, the potential of the first word lines WL1 other than the selected first word line WL1 is 0 V or floating. The potential of the second word line WL2 connected to the memory cell MC to be selected is V_{CC} (the first potential). On the other hand, the potential of the second word lines WL2 other than the selected second word line WL2 is floating. The potential of all the wells is 0 V.

When the potentials of the respective parts are set as described above, electron flow between the source diffused layer 36a of the memory cell transistor MT and the drain diffused layer 36c of the selecting transistor ST, and the electrons are injected into the floating gate 30a of the memory cell transistor MT. Thus, charges are stored in the floating gate 30a of the memory cell transistor MT, and information is written into the memory cell transistor MT.

(Erasing Method)

Next, the erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 6.

When information written in the memory cell array 10 is erased, the potentials of the respective parts are set as follows. That is, the potential of the bit lines BL is floating. The potential of all the source lines SL is floating. The potential of all the first word lines WL1 is, e.g., -9 V. The potential of all the second word lines WL2 is floating. The potential of all the wells 26 is, e.g., +9 V.

When the potentials of the respective parts are set as described above, the charge is drawn out of the floating gate 30a of the memory cell transistor MT. Thus, no charge is stored in the floating gate 30a of the memory cell transistor MT, and the information in the memory cell transistor MT is erased.

As described above, according to the present embodiment, the column decoder 12 for controlling the potential of the bit lines BL commonly connecting the drain diffused layers 36c of the selecting transistors ST is formed of a low voltage circuit, which is operative at high speed, the second row decoder for controlling the potential of the second word lines WL2 commonly connecting the select gate 30b of the selecting transistor ST is formed of a low voltage circuit, which is operative at high speed, and the potentials of only the bit lines BL and the second word lines WL2 are controlled, whereby information written the memory cell transistors MT can be read. According to the present embodiment, the nonvolatile semiconductor memory device can read information written in the memory cell transistors MT at high speed.

In the present embodiment, the selecting transistors ST is formed of NMOS transistors, and can contribute more to increasing the operation speed than the selecting transistors being formed of PMOS transistors.

(Method for Manufacturing Nonvolatile Semiconductor Memory Device)

Then, the method for manufacturing the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIGS. 7A to 22. FIGS. 7A to 22 are sectional views of the nonvolatile semiconductor memory device according to the present embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device, which illustrate the method. FIG. 7A, FIG. 8A, FIG. 9A, FIG. 10A, FIG. 11A, FIG. 12A, FIG. 13A, FIG. 14A, FIG. 15A, FIG. 16A, FIG. 17,

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FIG. 19 and FIG. 21 illustrate the memory cell array region (core region) 2. The views of FIG. 7A, FIG. 8A, FIG. 9A, FIG. 10A, FIG. 11A, FIG. 12A, FIG. 13A, FIG. 14A, FIG. 15A, FIG. 16A, FIG. 17, FIG. 19 and FIG. 21 on the left sides correspond to the C-C' section in FIG. 2. The views of FIG. 7A, FIG. 8A, FIG. 9A, FIG. 10A, FIG. 11A, FIG. 12A, FIG. 13A, FIG. 14A, FIG. 15A, FIG. 16A, FIG. 17, FIG. 19 and FIG. 21 on the right sides correspond to the A-A' section in FIG. 2. FIG. 7B, FIG. 8B, FIG. 9B, FIG. 10B, FIG. 11B, FIG. 12B, FIG. 13B, FIG. 14B, FIG. 15B, FIG. 16B, FIG. 18, FIG. 20 and FIG. 22 illustrate the peripheral circuit region 4. The views of FIG. 7B, FIG. 8B, FIG. 9B, FIG. 10B, FIG. 11B, FIG. 12B, FIG. 13B, FIG. 14B, FIG. 15B, FIG. 16B, FIG. 18, FIG. 20 and FIG. 22 on the left sides illustrate the region 6 where high withstand voltage transistors are to be formed. The left side views of the region 6 where the high withstand voltage transistors are to be formed illustrate the region 6N where the high withstand voltage N-channel transistors are to be formed. The right side views of the region 6N where the high withstand voltage N-channel transistors are to be formed illustrate the region 6P where the high withstand voltage P-channel transistor is to be formed. The right side of the region 6P where the high withstand voltage P-channel transistors are to be formed illustrate the region 6N where the high withstand voltage N-channel transistor is to be formed. The views of FIG. 7B, FIG. 8B, FIG. 9B, FIG. 10B, FIG. 11B, FIG. 12B, FIG. 13B, FIG. 14B, FIG. 15B, FIG. 16B, FIG. 18, FIG. 20 and FIG. 22 on the right sides illustrate the region 8 where low voltage transistors are to be formed. The left side views of the region 8 where the low voltage transistors are to be formed illustrate the region 8N where the low voltage N-channel transistor is to be formed, and the right side views of the regions 8 where the low voltage transistors are to be formed illustrate the region 8P where the low voltage P-channel transistor is to be formed.

First, a semiconductor substrate 20 is prepared. The semiconductor substrate 20 is, e.g., a P-type silicon substrate.

Next, on the entire surface, a 15 nm-thickness thermal oxide film 64 is formed by, e.g., thermal oxidation.

Next, on the entire surface, a 150 nm-thickness silicon nitride film 66 is formed by, e.g., CVD (Chemical Vapor Deposition).

Next, on the entire surface, a photoresist film (not illustrated) is formed by, e.g., spin coating.

Next, by photolithography, openings (not illustrated) are formed in the photoresist film. These openings are for patterning the silicon nitride film 66.

Next, with the photoresist film as the mask, the silicon nitride film 66 is patterned. Thus, a hard mask 66 of silicon nitride film is formed.

Next, with the hard mask 66 as the mask, the semiconductor substrate 20 is etched by dry etching. Thus, trenches 68 are formed in the semiconductor substrate 20 (see FIGS. 7A and 7B). The depth of the trenches 68 formed in the semiconductor substrate 20 is, e.g., 400 nm from the surface of the semiconductor substrate 20.

Next, the exposed parts of the semiconductor substrate 20 are oxidized by thermal oxidation. Thus, a silicon oxide film (not illustrated) is formed on the exposed parts of the semiconductor substrate 20.

Next, as illustrated in FIGS. 8A and 8B, a 700 nm-thickness silicon oxide film 22 is formed on the entire surface by high density plasma-enhanced CVD.

Next, as illustrated in FIGS. 9A and 9B, the silicon oxide film 22 is polished by CMP (Chemical Mechanical Polishing)

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until the surface of the silicon nitride film **66** is exposed. Thus, the device isolation regions **22** of silicon oxide film are formed.

Next, thermal processing for curing the device isolation regions **22** is made. The thermal processing conditions are, e.g., 900° C. in a nitrogen atmosphere and 30 minutes.

Next, the silicon nitride film **66** is removed by wet etching.

Next, as illustrated in FIGS. **10A** and **10B**, a sacrifice oxide film **69** is grown on the surface of the semiconductor substrate **20** by thermal oxidation.

Next, as illustrated in FIGS. **11A** and **11B**, an N-type dopant impurity is implanted deep in the memory cell array region **2** to thereby form an N-type buried diffused layer **24**. At this time, also in the region **6N** where the high withstand voltage N-channel transistors are to be formed, the N-type dopant impurity is implanted deep to thereby form the N-type buried diffused layer **24**. In the memory cell array region **2**, a P-type dopant impurity is implanted shallower than the buried diffused layer **24** to thereby form a P-type well **26**. In the region **6N** where the high withstand voltage N-channel transistor are to be formed, a P-type dopant impurity is implanted shallower than the buried diffused layer **24** to thereby form a P-type well **72P**.

Then, in the region **6N** where the high withstand voltage N-channel transistors are to be formed, an N-type diffused layer **70** is formed in a frame-shape. The frame-shaped diffused layer **70** is formed from the surface of the semiconductor substrate **20** to the peripheral edge of the buried diffused layer **24**. The P-type well **72P** is surrounded by the buried diffused layer **24** and the diffused layer **70**. Although not illustrated, the P-type well **26** of the memory cell array region **2** is also surrounded by the buried diffused layer **24** and the frame-shaped diffused layer **70**.

Then, in the region **6P** where the high withstand voltage channel transistor is to be formed, an N-type dopant impurity is implanted to thereby form an N-type well **72N**.

Next, in the memory cell array region **2**, channel doping is made (not illustrated).

Then, channel doping is made in the region **6N** where the high voltage N-channel transistors are to be formed and in the region **6P** where the high withstand voltage P-channel transistor is to be formed (not illustrated).

Next, the sacrifice oxide film **69** present on the surface of the semiconductor substrate **20** is etched off.

Next, a 10 nm-thickness tunnel insulation film **28** is formed on the entire surface by thermal oxidation.

Next, a 90 nm-thickness polycrystalline silicon film **30** is formed on the entire surface by, e.g., CVD. As the polycrystalline silicon film **30**, an impurity-doped polycrystalline silicon film is formed.

Then, the polycrystalline silicon film **30** present in the peripheral circuit region **4** is etched off.

Then, on the entire surface, an insulation film (ONO film) **32** of a silicon oxide film, a silicon nitride film and a silicon oxide film sequentially laid is formed. The insulation film **32** is for insulating the floating gate **30a** and the control gate **34a** from each other.

Then, as illustrated in FIGS. **12A** and **12B**, in the region **8N** where the low voltage N-channel transistor is to be formed, an N-type dopant impurity is implanted to thereby form an N-type well **74P**.

Next, in the region **8P** where the low voltage P-channel transistor is to be formed, an N-type dopant impurity is implanted to thereby form an N-type well **74N**.

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Next, in the region **8N** where the low voltage N-channel transistor is to be formed and in the region **8P** where the low voltage P-channel transistor is to be formed, channel doping is made (not illustrated).

Next, the insulation film (ONO film) **32** present in the peripheral circuit region **4** is etched off.

Then, the gate insulation film **76** of, e.g., a 15 nm-thickness is formed on the entire surface by thermal oxidation.

Next, the gate insulation film **76** present in the region **8** where the low voltage transistors are to be formed is removed by wet etching.

Next, the gate insulation film **78** of, e.g., a 3 nm-thickness is formed on the entire surface by thermal oxidation. Thus, the gate insulation film of, e.g., a 3 nm-thickness is formed in the region **8** where the low voltage transistors are to be formed. On the other hand, in the region **6** where the high withstand voltage transistors are to be formed, the film thickness of the gate insulation film **76** is, e.g., about 16 nm.

Next, a polycrystalline silicon film **34** of, e.g., a 180 nm-thickness is formed on the entire surface by, e.g., CVD.

Then, an anti-reflection film **80** is formed on the entire surface.

Next, as illustrated in FIGS. **13A** and **13B**, the anti-reflection film **80**, the polycrystalline silicon film **34**, the insulation film **32** and the polycrystalline silicon film **30** are dry etched by photolithography. Thus, the layer structure including the floating gate **30a** of polycrystalline silicon and the control gate **34a** of polycrystalline silicon is formed in the memory cell array region **2**. The layer structure of the select gate **30b** of polycrystalline silicon and the polycrystalline silicon film **34b** is formed in the memory cell array region **2**.

Then, in the region where an interconnection (the first metal interconnection) **46** and the select gate **30b** are to be connected to each other, the polycrystalline silicon film **34b** is etched off (not illustrated).

Next, as illustrated in FIGS. **14A** and **14B**, a silicon oxide film (not illustrated) is formed by thermal oxidation on the side wall of the floating gate **30a**, the side wall of the control gate **34a**, the side wall of the select gate **30b** and the side wall of the polycrystalline silicon film **34b**.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, a photoresist film having an opening (not illustrated) for exposing the memory cell array region **2** is formed by photolithography.

Then, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, impurity diffused layers **36a-36c** are formed in the semiconductor substrate **20** on both sides of the floating gate **30a** and in the semiconductor substrate **20** on both sides of the select gate **30b**. Then, the photoresist film is released.

Thus, the memory cell transistor MT including the floating gate **30a**, the control gate **34a** and the source/drain diffused layers **36a, 36b** is formed. The selecting transistor ST including the control gate **30b** and the source/drain diffused layers **36b, 36c** is formed.

Then, a silicon oxide film **82** is formed by thermal oxidation on the side wall of the floating gate **30a**, the side wall of the control gate **34b**, the side wall of the select gate **30b** and the side wall of the polycrystalline silicon film **34b**.

Next, a 50 nm-thickness silicon nitride film **84** is formed by, e.g., CVD.

Then, the silicon nitride film **84** is anisotropically etched by dry etching to thereby form the sidewall insulation film **84** of silicon nitride film. At this time, the anti-reflection film **80** is etched off.

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Then, by photolithography, the polycrystalline silicon film **34** in the region **6** where the high withstand voltage transistors are to be formed and in the region **8** where the withstand voltage transistors are to be formed is patterned. Thus, the gate electrodes **34c** of the high withstand voltage transistors, which are formed of polycrystalline silicon film **34** are formed. The gate electrodes **34d** of the low voltage transistors, which is formed of the polycrystalline silicon film **34** are formed.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, openings (not illustrated) for exposing the region **6N** where the high withstand voltage N-channel transistors are to be formed are formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, N-type lightly doped diffused layers **86** are formed in the semiconductor substrate **20** on both sides of the gate electrodes **34c** of the high withstand voltage N-channel transistors. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening (not illustrated) for exposing the region **6P** where the high withstand voltage P-channel transistors are to be formed is formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, P-type lightly doped diffused layers **88** are formed in the semiconductor substrate **20** on both sides of the gate electrodes **34c** of the high withstand voltage P-channel transistors. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, an opening (not illustrated) for exposing the region **8N** where the low voltage N-channel transistor is to be formed is formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, N-type lightly doped diffused layers **90** are formed in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage N-channel transistor. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening (not illustrated) for exposing the region **8P** where the low voltage P-channel transistor is to be formed is formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, a P-type lightly doped diffused layers **92** are formed in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage P-channel transistor. Then, the photoresist film is released.

Then, a 100 nm-thickness silicon oxide film **93** is formed by, e.g., CVD.

Then, the silicon oxide film **93** is anisotropically etched by dry etching. Thus, the sidewall insulation film **93** of silicon oxide film is formed on the side wall of the layer structure of the floating gate **30a** and the control gate **34a** (see FIGS. **15A** and **15B**). Also on the side wall of the layer structure of the select gate **30b** and the polycrystalline silicon film **34b**, the sidewall insulation film **93** of silicon oxide film is formed. Also on the side walls of the gate electrodes **34c**, the sidewall insulation film **93** of silicon oxide film is formed. Also on the

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side walls of the gate electrodes **34d**, the side wall insulation film **93** of silicon oxide film is formed.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, openings (not illustrated) for exposing the regions **6N** where the high withstand voltage N-channel transistors are to be formed are formed in the photoresist film by photolithography.

Then with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, N-type heavily doped diffused layers **94** are formed in the semiconductor substrate **20** on both sides of the gate electrodes **34c** of the high withstand voltage N-channel transistors. The N-type lightly doped diffused layers **86** and the N-type heavily doped diffused layers **94** form the N-type source/drain diffused layers **96** of the LDD structure. Thus, the high withstand voltage N-channel transistors **110N** each including the gate electrode **34c** and the source/drain diffused layer **96** are formed. The high withstand voltage N-channel transistors **110N** are used in the high voltage circuit (high withstand voltage circuit). Then the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening for exposing the region **6P** where the high withstand voltage P-channel transistor is to be formed is formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, P-type heavily doped diffused layers **98** are formed in the semiconductor substrate **20** on both sides of the gate electrode **34c** of the high withstand voltage P-channel transistor. The P-type lightly doped diffused layer **88** and the P-type heavily doped diffused layer **98** form the P-type source/drain diffused layers **100** of the LDD structure. Thus, the high withstand voltage P-channel transistors **110P** including the gate electrode **34c** and the source/drain diffused layers **100** is formed. The high withstand voltage P-channel transistor **110P** is used in the high voltage circuit (high withstand voltage circuit). Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, an opening (not illustrated) for exposing the region **8N** where the low voltage N-channel transistor is to be formed is formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. N-type heavily doped diffused layers **102** are formed in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage N-channel transistor. The N-type lightly doped diffused layers **90** and the N-type heavily doped diffused layers **102** form the N-type source/drain diffused layers **104** of the LDD structure. Thus, the low voltage N-channel transistor **112N** including the gate electrode **34d** and the source/drain diffused layers **104** is formed. The low voltage N-channel transistor **112N** is used in the low voltage circuit. Then, the photoresist film is released.

Then, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening (not illustrated) for exposing the region **8P** where the low voltage P-channel transistor is to be formed is formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, P-type heavily doped diffused layers **106** are formed in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage P-channel transistor. The

P-type lightly doped diffused layers **92** and the P-type heavily doped diffused layers **106** form the P-type source/drain diffused layers **108** of the LDD structure. Thus, the low voltage P-channel transistor **112P** including the gate electrode **34d** and the source/drain diffused layers **108** is formed. The low voltage P-channel transistor **112P** is used in the low voltage circuit. Then, the photoresist film is released.

Next, a 10 nm-thickness cobalt film is formed on the entire surface by, e.g., sputtering.

Next, thermal processing is made to thereby react the silicon atoms in the surface of the semiconductor substrate **20** and the cobalt atoms in the cobalt film with each other. The silicon atoms in the surface of the control gates **34c** and the cobalt atoms in the cobalt film are also reacted with each other. The silicon atoms in the surface of the polycrystalline silicon film **34d** and the cobalt atoms in the cobalt film are also reacted with each other. The silicon atoms in the surface of the gate electrodes **34c**, **34d** and the cobalt atoms in the cobalt film are also reacted with each other. Thus, a cobalt silicide film **38a**, **38b** is formed on the source/drain diffused layers **36a**, **36c** (see FIGS. **16A** and **16B**). On the control gate **34a**, the cobalt silicide film **38c** is also formed. On the polycrystalline silicon film **34b**, the cobalt silicide film **38d** is formed. On the source/drain diffused layers **96**, **100**, **104**, **108**, cobalt silicide films **38e** are formed. On the gate electrodes **34c**, **34d**, the cobalt silicide film **38f** is formed.

Next, the non-reacted cobalt film is etched off.

The cobalt silicide film **38b** formed on the drain diffused layer **36c** of the selecting transistor ST functions as the drain electrode.

The cobalt silicide film **38a** formed on the source diffused layer **36a** of the memory cell transistor MT functions as the source electrode.

The cobalt silicide film **38e** formed on the source diffused layers **96**, **100** of the high withstand voltage transistors **110N**, **110P** function as the source/drain electrodes.

The cobalt silicide film **38e** formed on the source/drain diffused layers **104**, **108** of the low voltage transistors **112N**, **112P** functions as the source/drain electrodes.

Then, as illustrated in FIGS. **17** and **18**, a 100 nm-thickness silicon nitride film **114** is formed on the entire surface by, e.g., CVD. The silicon nitride film **114** functions as the etching stopper.

Next, a 1.6 μm -thickness silicon oxide film **116** is formed on the entire surface by CVD. Thus, the inter-layer insulation film **40** of the silicon nitride film **114** and the silicon oxide film **116** is formed.

Next, the surface of the inter-layer insulation film **40** is planarized by CMP.

Then, contact holes **42** arriving at the source/drain electrodes **38a**, **38b**, contact holes **42** arriving at the cobalt silicide film **38e** and contact holes **42** arriving at the cobalt silicide film **38** are formed by photolithography (see FIG. **19** and FIG. **20**).

Next, a barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **44** is formed on the entire surface by, e.g., CVD.

Next, the tungsten film **44** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **40** is exposed. Thus, the conductor plugs **44** of, e.g., tungsten are buried in the contact holes **42**.

Next, on the inter-layer insulation film **40** with the conductor plugs **44** buried in, the layer film **46** of a Ti film, a TiN film, an Al film, a Ti film and a TiN film sequentially laid is formed by, e.g., sputtering.

Next, the layer film **46** is patterned by photolithography. Thus, the interconnection (the first metal interconnection layers) **46** of the layer film are formed.

Next, as illustrated in FIGS. **21** and **22**, a 700 nm-thickness silicon oxide film **118** is formed by, e.g., high density plasma-enhanced CVD.

Then, a silicon oxide film **120** is formed by TEOS-CVD (Tetra-Ethoxy-Silane Chemical Vapor Deposition). The silicon oxide film **118** and the silicon oxide film **120** form the inter-layer insulation film **48**.

Next, by photolithography, contact holes **50** arriving at the interconnections **46** are formed in the inter-layer insulation film **48**.

Next, a barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **52** is formed on the entire surface by, e.g., CVD.

Then, the tungsten film **52** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **48** is exposed. Thus, the conductor plugs **52** of, e.g., tungsten are buried in the contact holes **50**.

Next, on the inter-layer insulation film **48** with the conductor plugs **52** buried in, the layer film **54** of a Ti film, a TiN film, an Al film, a Ti film and a TiN film sequentially laid is formed by, e.g., sputtering on the inter-layer insulation film **48** with the conductor plugs **52** buried in.

Then, the layer film **54** is patterned by photolithography. Thus, the interconnections (the second interconnection layers) **54** of the layer film are formed.

Next, a silicon oxide film **122** is formed by, e.g., high density plasma-enhanced CVD.

Next, a silicon oxide film **124** is formed by TEOS-CVD. The silicon oxide film **122** and the silicon oxide film **124** form the inter-layer insulation film **56**.

Then, contact holes **58** arriving at the interconnections **54** are formed in the inter-layer insulation film **56** by photolithography.

Next, a barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Then, a 300 nm-thickness tungsten film **60** is formed on the entire surface by, e.g., CVD.

Then, the tungsten film **60** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **56** is exposed. Thus, conductor plugs **60** (see FIG. **22**) of, e.g., tungsten are formed in the contact holes **58**.

Next, a layer film **62** is formed by, e.g., sputtering on the inter-layer insulation film **56** with the conductor plugs **60** buried in.

Then, the layer film **62** is patterned by photolithography. Thus, the interconnections (the third metal interconnection layers) **62** of the layer film are formed.

Then, a silicon oxide film **126** is formed by, e.g., high density plasma-enhanced CVD.

Next, a silicon oxide film **128** is formed by TEOS-CVD. The silicon oxide film **126** and the silicon oxide film **128** form the inter-layer insulation film **130**.

Then, a contact hole **132** arriving at the interconnection **62** is formed in the inter-layer insulation film **130** by photolithography.

Next, a barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Then, a 300 nm-thickness tungsten film **134** is formed on the entire surface by, e.g., CVD.

Next, the tungsten film **134** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **130** is exposed. Thus, a conductor plug (not illustrated) **134** of, e.g., tungsten is buried in the contact holes **132**.

Then, on the inter-layer insulation film **130** with the conductor plug **134** buried in, a layer film **136** is formed by, e.g., sputtering.

Then, a layer film **136** is patterned by photolithography. Thus, the interconnections (the fourth metal interconnection layers) **136** of the layer film are formed.

Next, a silicon oxide film **138** is formed by, e.g., high density plasma-enhanced CVD.

Then, a silicon oxide film **140** is formed by TEOSCVD. The silicon oxide film **138** and the silicon oxide film **140** form the inter-layer insulation film **142**.

Next, by photolithography, contact holes **143** arriving at the interconnections **136** are formed in the inter-layer insulation film **142**.

Then, a barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **146** is formed on the entire surface by, e.g., CVD.

Next, the tungsten film **146** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **142** is exposed. Thus, the conductor plugs **144** of tungsten are buried in the contact holes **143**.

Next, a layer film **145** is formed by, e.g., sputtering on the inter-layer insulation film **142** with the conductor plugs **144** buried in.

Next, the layer film **145** is patterned by photolithography. Thus, the interconnections (the fifth metal interconnection layers) **145** of the layer film are formed.

Next, a silicon oxide film **146** is formed by, e.g., high density plasma-enhanced CVD.

Next, a 1 μm -thickness silicon nitride film **148** is formed by plasma-enhanced CVD.

Thus, the nonvolatile semiconductor memory device according to the present embodiment is manufactured.

[b] Second Embodiment

The writing method of the nonvolatile semiconductor memory device according to a second embodiment will be explained with reference to FIGS. **23** to **25**. FIG. **23** is a partial circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. FIG. **24** is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. **24**, the voltages in the parentheses are the potentials of the non-selected lines. In FIG. **24**, F indicates floating. FIG. **25** is the time chart of the writing method of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first embodiment illustrated in FIGS. **1** to **22** are represented by the same reference numbers not to repeat or to simplify their explanation.

The constitution of the nonvolatile semiconductor memory device according to the present embodiment is the same as the constitution of the nonvolatile semiconductor memory device according to the first embodiment described above with reference to FIG. **1**.

The writing method of the nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that a power supply voltage V_{CC} (the first voltage) is applied to the non-selected bit lines, and the potential of the non-selected second word lines is set at 0 V (ground voltage).

When information is written into a memory cell transistor MT, in accordance with the time chart of FIG. **25**, the poten-

tials of the respective parts are set as illustrated in FIGS. **23** and **24**. A memory cell transistor MT for information to be written into is surrounded by the solid line circle in FIG. **23**.

First, the potential of the bit line $BL_{(SELECT)}$ connected to the memory cell MC to be selected, i.e., the potential of the bit line $BL_{(SELECT)}$ of the selected column is set at 0 V. The potential of the bit lines BL other than the selected bit line $BL_{(SELECT)}$, i.e., the potential of the bit lines BL of the non-selected columns is set at V_{CC} (the first potential). At this time, the potential of all the second word lines WL2 is 0 V (ground voltage).

Next, the potential of the second word line $WL2_{(SELECT)}$ connected to the memory cell MC to be selected, i.e., the potential of the second word line $WL2_{(SELECT)}$ of the selected row is set at V_{CC} (the first potential). On the other hand, the potential of the second word lines WL2 other than the selected second word line $WL2_{(SELECT)}$ i.e., the potential of the second word lines WL2 of the non-selected rows remains 0 V (ground voltage).

Next, the potential of the first word lines $WL1_{(SELECT)}$ connected to the memory cell MC to be selected, i.e., the potential of the first word line $WL1_{(SELECT)}$ of the selected row is set at, e.g., 9 V (the third potential). On the other hand, the potential of the first word lines WL1 other than the selected first word line $WL1_{(SELECT)}$ i.e., the potential of the first word lines WL1 of the non-selected row is set at 0 V or floating.

Next, the potential of the source line $SL_{(SELECT)}$ connected to the memory cell MC to be selected, i.e., the potential of the source line $SL_{(SELECT)}$ of the selected row is set at, e.g., 5 V (the second potential). On the other hand, the potential of the source lines SL other than the selected source line $SL_{(SELECT)}$, i.e., the potential of the source line SL of the non-selected row is set at 0 V or floating. In FIG. **23** the potential of the source line SL of another row adjacent to the source line $SL_{(SELECT)}$ of the selected row is 5 V (the second potential), because the each source line SL is common between 2 rows, as illustrated with broken line. That is to say, as will be detailed later with reference to FIG. **65**, as in the nonvolatile semiconductor memory device according to an eleventh embodiment, the sources of the memory cell transistors MT present in rows adjacent to each other may be connected by a common source line SL.

The potential of the wells **26** is constantly 0 V (ground voltage).

With the potentials of the respective parts being set as above, electrons flow between the source diffused layer **36a** of the memory cell transistor MT and the drain diffused layer **36c** of the selecting transistor ST, and the electrons are injected into the floating gate **30a** of the memory cell transistors MT. Thus, charges are stored in the floating gate **30a** of the memory cell transistor MT, and information is written into the memory cell transistor MT.

The reading method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment are the same as the reading method and the erasing method of the nonvolatile semiconductor memory device according to the first embodiment and are not explained here.

In the present embodiment, the potential of the non-selected bit lines BL is V_{CC} for the following reason. That is, with the potential of the non-selected bit lines BL being floating as in the first embodiment, there is a risk that information might be erroneously written into the non-selected memory cell transistor MT present in the same selected row. There is a risk that information might be erroneously written into, e.g., the memory cell transistor MT indicated by the

mark B in FIG. 23. In the present embodiment, the potential of the non-selected bit lines BL is V_{CC} , whereby the potential of the select gates 30b of the select transistors and the potential of the drain diffused layers 36c thereof become equal to each other. Thus, in the present embodiment, the selecting transistors ST can be surely turned off-state. According to the present embodiment, erroneous write of information in the non-selected memory cell transistors MT present in the same selected row can be prevented.

In the present embodiment, the potential of the non-selected second word lines WL2 is 0 V (ground voltage) for the following reason. That is, with the potential of the non-selected second word lines WL2 being floating as in the first embodiment, there is a risk that information might be erroneously written into the non-selected memory cell transistors MT present in the rows other than the selected row. There is a risk that information might be written erroneously in, e.g., the memory cell transistors MT indicated by the marks A and C in FIG. 23. In the present embodiment, the potential of the non-selected second word lines WL2 being 0 V (ground voltage), whereby the potential of the select gates 30b of the selecting transistor ST becomes lower than the potential of the drain diffused layer 36c of the selecting transistors ST. Thus, in the present embodiment, the selecting transistors ST can be surely turned off-state. According to the present embodiment the erroneous write of information in the non-selected memory cell transistors MT present in the rows other than the selected row can be prevented.

In the present embodiment the potentials of the respective parts are set in accordance with the time chart of FIG. 25 so as to turn off-state the selecting transistors ST of the non-selected memory cells MC before voltages are applied to the first word lines WL1 and the source line SL.

As described above, according to the present embodiment, the power supply voltage V_{CC} (the first voltage) is applied to the non-selected bit lines, and potential of the non-selected second word lines is set at 0 V (ground voltage), whereby the erroneous write of information in the non-selected memory cells MC can be prevented.

[c] Third Embodiment

The writing method of the nonvolatile semiconductor memory device according to a third embodiment will be explained with reference to FIGS. 26 and 27. FIG. 26 is a partial circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. FIG. 27 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 27, the voltages in the parentheses are the potentials of the non-selected lines. In FIG. 27, F indicates floating. FIG. 27 is the time chart of the writing method of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first or the second embodiment illustrated in FIGS. 1 to 25 are represented by the same reference numbers not to repeat or to simplify their explanation.

The constitution of the nonvolatile semiconductor memory device according to the present embodiment is the same as the constitution of the nonvolatile semiconductor memory device according to the first embodiment described above with reference to FIG. 1.

The writing method of the nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the potential of the second word line

WL2_(SELECT) connected to a memory cell MC to be selected is set at V_{CC}' which is lower than a V_{CC} which is the potential of the non-selected bit lines BL.

When information is written into the memory cell transistor MT, in accordance with the time chart of FIG. 25, the potentials of the respective parts are set as illustrated in FIGS. 26 and 27.

First, the potential of the bit line BL_(SELECT) connected to the memory cell MC to be selected is set at 0 V. On the other hand, the potential of the bit lines BL other than the selected bit line BL_(SELECT) is set at V_{CC} (the fourth potential).

Then, the potential of the second word line WL2_(SELECT) connected to the memory cell MC to be selected is set at the potential V_{CC}' (the first potential) which is lower than the potential V_{CC} (the fourth potential) of the non-selected bit lines BL. In other words, the potential V_{CC} (the fourth potential) of the non-selected bit lines BL is set higher than the potential V_{CC}' (the first potential) of the selected second word line WL2_(SELECT). The potential V_{CC}' (the first potential) of the selected second word line WL2_(SELECT) is set lower by, e.g., about 0.2-0.5 V than the potential V_{CC} (the fourth potential) of the non-selected bit lines BL. On the other hand, the potential of the second word line WL2 other than the selected second word line WL2_(SELECT) is set at 0 V (ground voltage).

Then, the potential of the first word line WL1_(SELECT) connected to the memory cell MC to be selected is set at, e.g., 9 V (the third potential). On the other hand, the potential of the first word lines WL1 other than the selected first word line WL1_(SELECT) is set at 0 V or floating.

Next, the potential of the source line SL_(SELECT) connected to the memory cell MC to be selected is set at, e.g., 5 V (the second potential). On the other hand, the potential of the source lines SL other than the selected source line SL_(SELECT) is set at 0 V or floating. In FIG. 26, the potential of the source line SL of the row adjacent to the selected row is 5 V (the second potential), because each source line SL is common between 2 rows, as illustrated with a broken line. That is to say, as will be detailed later with reference to FIG. 65, as in the nonvolatile semiconductor memory device according to an eleventh embodiment, the sources of the memory cell transistors MT present in rows adjacent to each other may be connected by a common source line SL.

The potential of the wells 26 is constantly 0 V (ground voltage).

In the present embodiment, the potential V_{CC}' (the first potential) of the second word line WL2_(SELECT) connected to the memory cell MC to be selected is set lower than the potential V_{CC} (the fourth potential) of the non-selected bit lines BL for the following reason. That is, with the potential of the non-selected bit lines BL being set floating as in the first embodiment, there is a risk that information is erroneously written into a non-selected memory cell transistor MT present in the same selected row. There is a risk that information might be written into, e.g., the memory cell transistor MT indicated by the mark B in FIG. 26. In the present embodiment, the potential V_{CC}' of the selected second word line WL2_(SELECT) is lower than the potential V_{CC} (the fourth potential) of the non-selected bit lines BL, whereby the potential of the select gates 30b of the selecting transistors ST becomes lower than the potential of the drain diffused layers 36c of the selecting transistors ST. Thus, according to the present embodiment, the selecting transistors ST can be surely turned off-state. According to the present embodiment, the erroneous write of information in the non-selected memory cell transistors MT present in the same selected row can be further surely prevented.

As described above, according to the present embodiment, the potential of the second word line $WL2_{(SELECT)}$ connected to the memory cell MC to be selected is V_{CC} lower than the potential V_{CC} of the non-selected bit lines, whereby the erroneous write of information in the non-selected memory cell transistors MT present in the same selected row can be further surely prevented.

[d] Fourth Embodiment

The writing method of the nonvolatile semiconductor memory device according to a fourth embodiment will be explained with reference to FIG. 26 and FIGS. 28 to 30. FIG. 28 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 28, the voltages in the parentheses are the potentials of the non-selected lines. In FIG. 28, F indicates floating. FIG. 29 is the time chart of the writing method of the nonvolatile semiconductor memory device according to the present embodiment. FIG. 30 is the graph of the relationships between the difference between the control gate voltage and the threshold voltage, and the voltage between the source and the drain of the memory cell transistor. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the third embodiments illustrated in FIGS. 1 to 27 are represented by the same reference numbers not to repeat or to simplify their explanation.

The constitution of the nonvolatile semiconductor memory device according to the present embodiment is the same as the constitution of the nonvolatile semiconductor memory device according to the first embodiment described above with reference to FIG. 1.

The writing method of the nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that voltage is applied in pulses to the source line $SL_{(SELECT)}$ connected to the memory cell MC to be selected while the potential of the first word line $WL1_{(SELECT)}$ connected to the memory cell MC to be selected is gradually being raised, whereby information can be written into the memory cell transistor MT of the selected memory cell MC.

When information is written into the memory cell transistor MT, as illustrated in FIG. 28, the potential of the bit line $BL_{(SELECT)}$ connected to the memory cell MC to be selected is set at 0 V. On the other hand, the potential of the bit lines BL other than the selected bit line $BL_{(SELECT)}$ is set at V_{CC} (the first potential).

The potential of the second word line $WL2_{(SELECT)}$ connected to the memory cell MC to be selected is set at V_{CC} (the first potential). On the other hand, the potential of the second word lines WL2 other than the selected second word line $WL2_{(SELECT)}$ is set at 0 V (ground voltage).

To the first word line $WL1_{(SELECT)}$ connected to the memory cell MC to be selected, as illustrated in FIG. 29, the first voltage V_{step} which gradually rises is applied. On the other hand, the potential of the first word lines WL1 other than the selected first word line $WL1_{(SELECT)}$ is set at 0 V or floating.

To the source line $SL_{(SELECT)}$ connected to the memory cell MC to be selected, as illustrated in FIG. 29, the second voltage is applied in pulses. The pulsed second voltage to be applied to the source line $SL_{(SELECT)}$ is, e.g., 5 V. On the other hand, the potential of the source lines SL other than the selected source line $SL_{(SELECT)}$ is 0 V or floating.

The potential of the wells 26 is constantly 0 V (ground voltage).

In the present embodiment, voltage is applied in pulses to the source line $SL_{(SELECT)}$ of the selected column while the first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row is being raised for the following reason. That is, when high voltage is applied to the control gate 34b of the memory cell transistor MT, the electric resistance between the source and the drain of the memory cell transistor MT becomes smaller in comparison with the electric resistance between the source and the drain of the selecting transistor ST. Then, a large transverse electric field is applied between the source and the drain of the selecting transistor, while a sufficient transverse electric field is not applied between the source and the drain of the memory cell transistor MT. When a sufficient transverse electric field is not applied between the source and the drain of the memory cell transistor MT, the electrons are not accelerated between the source and the drain of the memory cell transistor MT, and the write speed becomes slow. In the present embodiment, in the initial stage of the write relatively low voltage is applied to the first word line $WL1_{(SELECT)}$ of the selected row, whereby the electric resistance between the source and the drain of the memory cell transistor MT does not become excessively small. Then, when voltage is applied in pulses to the source line $SL_{(SELECT)}$ of the selected column, charges are injected into the floating gate 30a of the memory cell transistor MT. Hereafter, when voltage is applied in pulses to the source line $SL_{(SELECT)}$ of the selected column while the voltage of the first word line $WL1_{(SELECT)}$ of the selected row is gradually raised, charges are gradually injected into the floating gate 30a of the memory cell transistor MT. The first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row gradually rises, but charges are gradually increasingly stored in the floating gate 30a, whereby the electric resistance between the source and the drain of the memory cell transistor MT never becomes excessively small. Thus, according to the present embodiment, the write speed of writing information in the memory cell transistor MT can be increased.

In the nonvolatile semiconductor memory device according to the present embodiment, hot carriers are generated, and the generated hot carriers are injected into the floating gate 30a of the memory cell transistor MT, whereby information is written into the memory cell transistor MT. To write by using hot carriers, energy which exceeds the height of the barrier of the tunnel insulation film 28a, i.e., 3.2 V is necessary, and the hot carriers is accelerated to this energy or more by the potential difference between the source and the drain of the memory cell transistor MT. FIG. 30 is the graph of the relationships between the difference between the control gate voltage and the threshold voltage, and the voltage between the source and the drain of the memory cell transistor. FIG. 30 was given by simulation. As the conditions for the simulation, the voltage to be applied to the select gate 30b of the selecting transistor is 1.5 V, and the voltage to be applied to the source line is 5 V. As seen in FIG. 30, when the difference between the voltage of the control gate 34a of the memory cell transistor MT and the threshold voltage of the memory cell transistor MT is 2.5 V or below, the voltage between the source and the drain of the memory cell transistor MT is 3.2 V or above. On the other hand, to flow large current to the channel of the memory cell transistor MT to increase the write speed, it is preferable to set the voltage of the control gate 34a of the memory cell transistor MT as high as possible with respect to the threshold voltage of the memory cell transistor MT. Preferably, the first voltage V_{step} to be applied to the control gate 34a of the memory cell transistor MT is gradually increased

so that the voltage of the control gate **34a** of the memory cell transistor MT becomes higher constantly by 2.5 V than the threshold voltage of the memory cell transistor MT. In other words, preferably, the first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row is gradually increased so that the voltage of the control gate **34a** of the memory cell transistor MT is higher constantly by 2.5 V than the threshold voltage of the memory cell transistor MT.

The present embodiment is explained here by means of an example that the first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row is gradually increased so that the voltage to be applied to the first word line $WL1_{(SELECT)}$ of the selected row is higher constantly by 2.5 V than the threshold voltage of the memory cell transistor MT. However, the difference between the first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row and the threshold voltage of the memory cell transistor MT is not limited to this. The first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row may be gradually increased so that the first voltage V_{step} to be applied to the first word line $WL1_{(SELECT)}$ of the selected row is higher by 2-3 V than the threshold voltage of the memory cell transistor MT.

[e] Fifth Embodiment

The nonvolatile semiconductor memory device according to a fifth embodiment, and the reading method, the writing method and the erasing method thereof will be explained with reference to FIGS. **31** and **32**. FIG. **31** is the circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the fourth embodiments are represented by the same reference numbers not to repeat or to simplify their explanation.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **31**.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the bit lines BL are connected to the column decoder **12** via the first protection transistors **150**, the second word lines WL2 are connected to the second row decoder **16** via the second protection transistors **152**, and when information written in the memory cell array **10** is erased, the column decoder **12** is electrically disconnected from the bit lines BL, and the second row decoder **16** is electrically disconnected from the second word lines WL2.

As illustrated in FIG. **31**, the respective bit lines BL are connected to the column decoder **12** via the first protection transistors **150**. In other words, one of the source/drain of each of the first protection transistor **150** is connected to a bit line BL, and the other of the source/drain of each of the first protection transistor **150** is connected to the column decoder **12**.

The gates of the respective first protection transistor **150** are connected to a control circuit **154** via the first control line CL1. The respective first protection transistors **150** are controlled by the control circuit **154**.

The film thickness of the gate insulation film (not illustrated) of the first protection transistors **150** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. The film thickness of the gate insulation film of the first protection transistors **150** is set relatively thick as is the film thickness of the gate insulation film **28b** of the select-

ing transistors ST so as to sufficiently ensure the withstand voltage of the first protection transistors **150**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained by means of the example that the film thickness of the gate insulation film (not illustrated) of the first protection transistors **150** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. However, the film thickness of the gate insulation film of the first protection transistors **150** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the first protection transistors **150** can be suitably set corresponding to a working voltage.

The respective second word lines WL2 are connected to the second row decoder **16** via the second protection transistors **152**. In other words, one of the source/drain of each of the second protection transistors **152** is connected to the second word line WL2, and the other of the source/drain of each of the second protection transistors **152** is connected to the second row decoder **16**.

The gates of the respective second protection transistors **152** are connected to the control circuit **154** via the second control line CL2. The respective second protection transistors **152** are controlled by the control circuit **154**.

The film thickness of the gate insulation film (not illustrated) of the second protection transistors **152** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. The film thickness of the gate insulation film of the second protection transistors **152** is set relatively thick as is the film thickness of the gate insulation film **28b** of the selecting transistors ST so as to sufficiently ensure the withstand voltage of the second protection transistors **152**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained by means of the example that the film thickness of the gate insulation film (not illustrated) of the second protection transistors **152** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. However, the film thickness of the gate insulation film of the second protection transistors **152** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the second protection transistors **152** can be suitably set corresponding to a working voltage.

Thus, the nonvolatile semiconductor memory device according to the present embodiment is constituted.

The memory cell transistors MT of the respective rows are connected by the source lines SL respectively associated with the respective rows here as illustrated in FIG. **31**. However, as in the nonvolatile semiconductor memory device according to an eleventh embodiment which will be detailed later with reference to FIG. **65**, the sources of the memory cell transistors MT present in rows adjacent to each other may be connected by a common source line SL. The sources of the memory cell transistors MT present in rows adjacent to each other are connected by a common source line SL, whereby the area of the memory cell array region **2** can be reduced, and the nonvolatile semiconductor memory device can be downsized. The number of the source lines SL to be controlled by the third row decoder **18** can be decreased, whereby the third row decoder **18** can be simplified.

(Operations of the Nonvolatile Semiconductor Memory Device)

Next, the operation of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **32**. FIG. **32** is a view illustrating the reading method, the writing method and the eras-

ing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 32, the voltages in the parentheses are the potentials of the non-selected lines. In FIG. 32, F indicates floating.

(Reading Method)

First, the reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 32.

In the present embodiment, when information written in the memory cell transistors MT is read, the voltage of the first control line CL1 is set at 5 V, and the potential of the second control line CL2 is set at 5 V. That is, in the present embodiment, when information written in a memory cell transistor MT is read, the first protection transistors 150 and the second protection transistors 152 are turned on-state. The potential of the bit lines BL, the potential of the source lines SL, the potential of the first word lines WL1, the potential of the second word lines WL2, the potential of the wells 26 are the same as the potentials of the respective parts in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

Because of the first protection transistor 150 and the second protection transistor 152 being on-state, the bit line BL is electrically connected to the column decoder 12 as in the nonvolatile semiconductor memory device according to the first embodiment, and the second word line WL2 is electrically connected to the second row decoder 16 as in the nonvolatile semiconductor memory device according to the first embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information written in the memory cell transistor MT can be read in the same way as in the nonvolatile semiconductor memory device according to the first embodiment.

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 32.

In the present embodiment, when information is written into the memory cell transistors MT, the potential of the first control line CL1 is set at 5 V, and the potential of the second control line CL2 is set at 5 V. That is, in the present embodiment, when information is written into the memory cell transistors MT, the first protection transistors 150 and the second protection transistors 152 are turned on-state. The potential of the bit lines BL, the potential of the source lines SL, the potential of the first word lines WL1 and the potential of the second word lines WL2 and the potential of the wells 26 are the same as the potentials of the respective parts in the writing method of the nonvolatile semiconductor memory device according to the second embodiment.

Because of the first protection transistor 150 and the second protection transistor 152 being on-state, the bit line BL is electrically connected to the column decoder 12 as in the nonvolatile semiconductor memory device according to the second embodiment, and the second word line WL2 is connected to the second row decoder 16 as in the nonvolatile semiconductor memory device according to the second embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information can be written in the memory cell transistor MT in the same way as in the writing method of the nonvolatile semiconductor memory device according to the second embodiment.

(Erasing Method)

Next, the erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 32.

When information written in the memory cell array 10 is erased, the potential of the first control line CL1 is set at 0 V, and the potential of the second control line CL2 is set at 0 V. That is, in the present embodiment, when information written in the memory cell transistors MT is erased, the first protection transistors 150 and the second protection transistors 152 are turned off-state. The potential of the bit lines BL, the potential of the source lines SL, the potential of the first word lines WL1, the potential of the second word lines WL2 and the potential of the wells 26 are the same as the potential of the respective parts in the erasing method of the nonvolatile semiconductor memory device according to the first embodiment.

When information written in the memory cell array 10 is erased, high voltage is applied to the first word line WL1 and the wells 26. When information in the memory cell array 10 is erased with the column decoder 12 and the second row decoder 16, which are formed of low voltage circuits, electrically connected to the memory cell array 10, there is a risk that the column decoder 12 and the second row decoder 16 might be broken. In the present embodiment, when information written in the memory cell array 10 is erased, the first protection transistor 150 and the second protection transistor 152 are turned off-state, whereby the bit lines BL are electrically disconnected from the second row decoder 12, and the second word lines WL2 are electrically disconnected from the second row decoder 16. That is, in the present embodiment, when information written in the memory cell array 10 is erased, the column decoder 12 and the second row decoder 16 of low voltage circuits are electrically disconnected from the memory cell array 10. Thus, according to the present embodiment, when information written in the memory cell array 10 is erased, the column decoder 12 and the second row decoder 16 of low withstand voltage can be prevented from being broken.

As described above, according to the present embodiment, in which the bit lines BL are connected to the column decoder 12 via the first protection transistors 150, and the second word lines WL2 are connected to the second row decoder 16 via the second protection transistors 152, when information written in the memory cell array 10 is erased, the column decoder 12 is electrically disconnected from the bit lines BL, and the second row decoder 16 is electrically disconnected from the second word lines WL2. Thus, according to the present embodiment, when information written in the memory cell array 10 is erased, the column decoder 12 and the second row decoder of low withstand voltage can be prevented from being broken.

[f] Sixth Embodiment

The nonvolatile semiconductor memory device according to a sixth embodiment, and the reading method, the writing method and the erasing method thereof will be explained with reference to FIG. 33 and FIG. 34. FIG. 33 is a circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the fifth embodiments illustrated in FIGS. 1 to 32 are represented by the same reference numbers not to repeat or to simplify their explanation.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 33.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the

second word lines WL2 are connected not only to the second row decoder 16 but also to the fourth row decoder of a high voltage circuit, and when information is written into the memory cell transistors MT, the second row decoder 16 is electrically disconnected from the second word lines WL2, and voltage is applied to the second word lines WL2 by the fourth row decoder 156.

As illustrated in FIG. 33, the respective bit lines BL are connected to the row decoder 12 via the first protection transistors 150. In other words, one of the source/drain of the first protection transistor 150 is connected to the bit line BL, and the other of the source/drain of the first protection transistor 150 is connected to column decoder 12.

The gate of each of the first protection transistor 150 is connected to the control circuit 154 via the first control line CL1. Each of the first protection transistors 150 is controlled by the control circuit 154.

The film thickness of the gate insulation film (not illustrated) of the first protection transistors 150 is set equal to the film thickness of the gate insulation film 28b of the selecting transistors ST. The film thickness of the gate insulation film of the first protection transistors 150 is set relatively thick as is the film thickness of the gate insulation film 28b of the selecting transistors ST so as to sufficiently ensure the withstand voltage of the first protection transistors 150.

The explanation of the nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the film thickness of the gate insulation film (not illustrated) of the first protection transistors 150 is set equal to the film thickness of the gate insulation film 28b of the selecting transistors ST. However, the film thickness of the gate insulation film of the first protection transistors 150 may be set equal to the film thickness of the gate insulation film of the high voltage transistors. The film thickness of the gate insulation film of the first protection transistors 150 can be set suitably corresponding to a working voltage.

The respective second word lines WL2 are connected to the second row decoder 16 via the second protection transistors 152. In other words, one of the source/drain of the second protection transistors 152 is connected to the second word line WL2, and the other of the source/drain of the second protection transistors 152 is connected to the second row decoder 16.

The gates of the respective second protection transistors 152 are connected to the control circuit 154 via the second control line CL2. The respective second protection transistors 152 are controlled by the control circuit 154.

The film thickness of the gate insulation film (not illustrated) of the second protection transistors 152 is set equal to the film thickness of the gate insulation film 28b of the selecting transistors ST. The film thickness of the gate insulation film of the first protection transistors 152 are set relatively thick, as is the film thickness of the gate insulation film 28b of the selecting transistors ST so as to sufficiently ensure the withstand voltage of the first protection transistors 152.

The nonvolatile semiconductor memory device according to the present embodiment has been explained by means of the example that the film thickness of the gate insulation film (not illustrated) of the second protection transistors 152 is set equal to the film thickness of the gate insulation film 28b of the selecting transistors ST. However, the film thickness of the gate insulation film of the second protection transistors 152 may be set equal to the film thickness of the gate insulation film of the high voltage transistors. The film thickness of the gate insulation film of the second protection transistors 152 can be suitably set corresponding to a working voltage.

The respective second word lines WL2 are connected further to the fourth row decoder 156. The fourth row decoder 156 is for controlling the potential of the plural second word lines WL2. The fourth row decoder 156 is formed of a high voltage circuit (high withstand voltage circuit). The fourth row decoder 156 is formed of a high voltage circuit in the present embodiment so as to apply high voltage to the second word lines WL2 when information is written into the memory cell transistors MT.

Thus, the nonvolatile semiconductor memory device according to the present embodiment is constituted.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that, as illustrated in FIG. 33, the memory cell transistors MT of each row are connected respectively to the source line SL associated with the row. However, as in the nonvolatile semiconductor memory device according to an eleventh embodiment which will be detailed with reference FIG. 65, the sources of the memory cell transistors MT present in rows adjacent to each other may be connected to the common source line SL. The sources of the memory cell transistors MT present in rows adjacent to each other are connected to the common source line SL, whereby the area of the memory cell array region 2 can be reduced, and the nonvolatile semiconductor memory device can be downsized. The number of the source lines SL to be controlled by the third row decoder 18 can be decreased, which can simplify the third row decoder 18.

(Operations of Nonvolatile Semiconductor Memory Device)

Next, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 34. FIG. 34 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 34, the voltages in the parentheses are potentials of the non-selected lines. In FIG. 34, F indicates floating.

(Reading Method)

First, the reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 34.

In the present embodiment, when information written in the memory cell transistors MT is read, the potential of the first control line CL1 is set at 5 V, and the potential of the second control lines CL2 is set at 5 V. That is, in the present embodiment, when information written in the memory cell transistors MT is read, the first protection transistors 150 and the second protection transistors 152 are turned on-state. The potential of the bit lines BL, the potential of the source lines SL, the potential of the first word lines WL1, the potential of the second word lines WL2 and the potential of the wells 26 are the same as the potentials of the respective parts in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

Because of the first protection transistors 150 and the second protection transistors 152 being on-state, the bit lines BL are electrically connected to the column decoder 12 as in the nonvolatile semiconductor memory device according to the first embodiment, and the second word lines WL2 are electrically connected to the second row decoder 16 as in the nonvolatile semiconductor memory device according to the first embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information written in the memory cell transistors MT can be read

in the same way as in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 34.

When information is written into the memory cell transistors MT, the potentials of the respective parts are set as follows. That is, the potential of the bit line BL connected to a memory cell MC to be selected is set at 0 V. The potential of the bit lines BL other than the selected bit line BL is set at floating. The potential of the source line SL connected to the memory cell MC to be selected is set at, e.g., 5 V (the second potential). The potential of the source lines SL other than the selected source line SL is set at 0 V or floating. The potential of the first word line WL1 connected to the memory cell MC to be selected is set at, e.g., 9 V (the third potential). The potential of the first word lines WL1 other than the selected first word line WL1 is set at 0 V or floating. The potential of the second word line WL2 connected to the memory cell MC to be selected is set at, e.g., 4 V (the first potential). The potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V (ground voltage). The potential of the first control line CL1 is set at, e.g., 5 V. The potential of the second control line CL2 is set at, e.g., 5 V. That is, in the present embodiment, when information is written into the memory cell transistors MT, the first protection transistors 150 are turned on-state, and the second protection transistors 152 are turned off-state. The potential of all the wells 26 is set at 0 V.

In the present embodiment, in which voltage is applied to the second word lines WL2 by the fourth row decoder 156 of a high voltage circuit, relative high voltage can be applied to the select gates 30b of the selecting transistors ST. Accordingly, in the present embodiment, the current flowing in the channels of the selecting transistors ST can be increased, and the write speed can be increased. On the other hand, when information is written into the memory cell transistors MT, the second protection transistors 152 are turned off-state, and accordingly, the second row decoder 16 of a low voltage circuit is electrically disconnected from the second word lines WL2. Thus, according to the present embodiment, when information is written into the memory cell transistors MT, the second row decoder 16 of a low voltage circuit can be prevented from being broken.

(Erasing Method)

The erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 34.

In the present embodiment, when information written in the memory cell array 10 is erased, the potentials of the respective parts are the same as the potentials of the respective parts in the erasing method of the nonvolatile semiconductor memory device according to the fifth embodiment.

Accordingly, in the nonvolatile semiconductor memory device according to the present embodiment, information written in the memory cell transistors MT can be erased in the same way as in the erasing method of the nonvolatile semiconductor memory device according to the fifth embodiment.

As described above, in the present embodiment, the second word lines WL2 are connected not only to the second row decoder 16 and also to the fourth row decoder 156 of a high voltage circuit, and when information is written into the memory cell transistors MT, the second row decoder 16 is electrically disconnected from the second word lines WL2, and voltage is applied to the second word lines WL2 by the

fourth row decoder 156. Thus, according to the present embodiment, when information is written into the memory cell transistors MT, high voltage can be applied to the channels of the selecting transistors ST, and the current flowing in the selecting transistors ST can be increased, and the write speed can be increased. The second row decoder 16 is electrically disconnected from the second word lines WL2 when information is written into the memory cell transistors MT, whereby the breakage of the second row decoder 16 of a low voltage circuit can be prevented.

[g] Seventh Embodiment

The nonvolatile Semiconductor Memory Device according to a seventh embodiment, and the reading method, the writing method and the erasing method thereof will be explained with reference to FIG. 35 and FIG. 36. FIG. 35 is the circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the sixth embodiments illustrated in FIGS. 1 to 34 are represented by the same reference numbers not to repeat or to simplify their explanation.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 35.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that bypass transistors 158 are provided respectively between the respective second word lines WL2 and the respective source lines SL, and when information is written into the memory cell transistors MT, the second row decoder 16 is electrically disconnected from the second word lines WL2, the source lines SL and the second word lines WL2 are electrically connected by the bypass transistor 158, and voltage is applied to the word lines WL2 by the third row decoder 18.

As illustrated in FIG. 35, the respective bit lines BL are connected to the column decoder 12 via the first protection transistors 150. In other words, one of the source and drain of the first protection transistors 150 is connected to the bit line BL, and the other of the source and the drain of the first protection transistors 150 is connected to the column decoder 12.

The gates of the respective first protection transistors 150 are connected to the first control circuit 154 via the first control line CL1. The respective first protection transistors 150 are controlled by the first control circuit 154.

The film thickness of the gate insulation film (not illustrated) of the first protection transistors 150 is set equal to the film thickness of the gate insulation film 28b of the selecting transistors ST. The film thickness of the gate insulation film of the first protection transistors 150 is set relatively thick as is the film thickness of the gate insulation film 28b of the selecting transistor ST so as to sufficiently ensure the withstand voltage of the first protection transistors 150.

The nonvolatile semiconductor memory device according to the present embodiment has been explained by means of the example that the film thickness of the gate insulation film (not illustrated) of the first protection transistors 150 is set equal to the film thickness of the gate insulation film 28b of the selecting transistors ST. However, the film thickness of the gate insulation film of the first protection transistors 150 may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of

the gate insulation film of the first protection transistors **150** can be set suitably corresponding to a working voltage.

The respective second word lines **WL2** are connected to the second row decoder **16** via the second protection transistors **152**. In other words, one of the source and the drain of the second protection transistors **152** is connected to the second word line **WL2**, and the other of the source and the drain of the second protection transistors **152** is connected to the second row decoder **16**.

The gates of the respective second protection transistors **152** are connected to the second control circuit **154** via the second control line **CL2**. The respective second protection transistors **152** are controlled by the second control circuit **154**.

The film thickness of the gate insulation film (not illustrated) of the second protection transistors **152** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors **ST**. The film thickness of the gate insulation film of the first protection transistors **152** is set relatively thick as is the film thickness of the gate insulation film **28b** of the selecting transistors **ST** so as sufficiently ensure the withstand voltage of the first protection transistors **152**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the film thickness of the gate insulation film (not illustrated) of the second protection transistors **152** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors **ST**. However, the film thickness of the gate insulation film of the second protection transistors **152** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the second protection transistors **152** can be set suitably corresponding to a working voltage.

The bypass transistors **158** is provided each between the second word line **WL2** and the source line **SL**. In other words, one of the source and the drain of the bypass transistor **158** is connected to the second word line **WL2**, and the other of the source and the drain of the bypass transistor **158** is connected to the source line **SL**.

The gate of the respective bypass transistors **158** are connected to the second control circuit **160** via the third control line **CL3**. The respective bypass transistors **158** are controlled by the third control circuit **160**.

The film thickness of the gate insulation film (not illustrated) of the bypass transistor **158** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors **ST**. The film thickness of the gate insulation film of the bypass transistors **158** is set relatively thick as is the film thickness of the gate insulation film **28b** of the selecting transistors **ST** so as to sufficiently ensure the withstand voltage of the bypass transistors **158**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the film thickness of the gate insulation film (not illustrated) of the bypass transistors **158** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors **ST**. However, the film thickness of the gate insulation film of the bypass transistors **158** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the bypass transistors **158** can be set suitably corresponding to a working voltage.

The second word lines **WL2** are connected to the third row decoder **18** via the bypass transistors **158** in the present

embodiment so as to apply high voltage to the second word lines **WL2** when information is written into the memory cell transistors **MT**.

Thus, the nonvolatile semiconductor memory device according to the present embodiment is constituted.

The nonvolatile semiconductor memory device according to the present embodiment has been explained by means of the example that, as illustrated in FIG. **35**, the memory cell transistors **MT** of the respective rows are respectively connected to the source lines **SL** associated with the respective rows. However, as will be detailed later with reference to FIG. **65**, as in the nonvolatile semiconductor memory device according to an eleventh embodiment, the sources of the memory cell transistors **MT** present in rows adjacent to each other may be connected to a common source line **SL**. The sources of the memory cell transistors **MT** present in rows adjacent to each other are connected to a common source line **SL**, whereby the area of the memory cell array region **2** can be reduced, and the nonvolatile semiconductor memory device can be down sized. The number of the source lines **SL** to be controlled by the third row decoder **18** can be decreased, whereby the third row decoder **18** can be simplified.

(Operations of Nonvolatile Semiconductor Memory Device)

Then, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **36**. FIG. **36** is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. **36**, the voltages in the parentheses are potentials of the non-selected lines. In FIG. **36**, **F** indicates floating.

(Reading Method)

The reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **36**.

In the present embodiment, when information in the memory cell transistors **MT** is read, the potential of the first control line **CL1** is set at 5 V, and the potential of the second control line **CL2** is set at 5 V. That is, in the present embodiment, when information written in the memory cell transistors **MT** is read, the first protection transistors **150** and the second protection transistors **152** are turned on-state. When information written in the memory cell transistors **MT** is read, the potential of the third control line **CL3** is set at 0 V. That is, in the present embodiment, when information written in the memory cell transistors **MT** is read, the bypass transistors **158** are turned off-state. The potential of the bit lines **BL**, the potential of the source lines **SL**, the potential of the first word lines **WL1**, the potential of the second word lines **WL2** and the potential of the wells **26** are the same as the potentials of the respective parts in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

Because of the first protection transistors **150** and the second protection transistors **152** being on-state, the bit lines **BL** are electrically connected to the column decoder **12** as in the nonvolatile semiconductor memory device according to the first embodiment, and the second word lines **WL2** are electrically connected to the second row decoder **16** as in the nonvolatile semiconductor memory device according to the first embodiment. Because of the bypass transistors **158** being off-state, the second word lines **WL2** are electrically disconnected from the source line **SL** as in the nonvolatile semiconductor memory device according to the first embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information written in

the memory cell transistors MT can be read in the same way as in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 36.

When information is written into the memory cell transistors MT, the potentials of the respective parts are set as follows.

That is, the potential of the bit line BL connected to a memory cell MC to be selected is set at 0 V. On the other hand, the potential of the bit lines BL other than the selected bit line BL is set floating.

The potential of the source line SL connected to the memory cell MC to be selected is set at, e.g., 5 V (the first potential). On the other hand, the potential of the source lines SL other than the selected source line SL is set at 0 V or floating.

The potential of the first word line WL1 connected to the memory cell MC to be selected is set at, e.g., 9 V (the second potential). On the other hand, the potential of the word lines WL1 other than the selected first word line WL1 is set at 0 V or floating.

The bypass transistors 158 are turned on-state, whereby the source line SL and the second word line WL2 are electrically connected. Thus, the potential of the second word line WL2 connected to the memory cell MC to be selected becomes equal to the potential of the source line. The potential of the selected source line SL is set here at, e.g., 5 V (the first potential), and the potential of the selected second word line WL2 becomes, e.g., 5 V (the first potential). On the other hand, the potential of the second word line WL2 other than the selected second word line WL2 becomes 0 V (ground voltage).

The potential of the first control line CL1 is set at, e.g., 5 V. The potential of the second control line CL2 is set at, e.g., 0 V. That is, in the present embodiment, when information is written into the memory cell transistors MT, the first protection transistors 150 are turned on-state, and the second protection transistors 152 are turned off-state.

The potential of the third control line CL3 is set at, e.g., 6 V (the third potential). The potential (the third potential) of the third control line CL3 is set higher than the first potential, which is the potential of the selected source line SL. The potential (the third potential) of the third control line CL3 is set higher than the potential (the first potential) of the selected source line SL so as to surely make equal the potential of the second word lines WL2 and the potential of the source lines SL to each other.

The potential of all the wells 26 is set at 0 V.

In the present embodiment, in which when information is written into the memory cell transistors MT, voltage is applied to the second word lines WL2 by the third row decoder 18 of a high voltage circuit, relatively high voltage can be applied to the select gates 30b of the selecting transistors ST. Thus, according to the present embodiment, the current flowing in the channels of the selecting transistors ST can be increased, and the write speed can be increased. When information is written into the memory cell transistors MT, the second protection transistors 152 are turned off-state, and the second row decoder 16 of a low voltage circuit can be electrically disconnected from the second word lines WL2. Thus, according to the present embodiment, when information is written into the memory cell transistors MT, the breakage of the second row decoder 16 of a low voltage circuit can be prevented.

(Erasing Method)

First, the erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 36.

In the present embodiment, when information written in the memory cell array 10 is erased, the potential of the first control line CL1 is set at 0 V, and the potential of the second control line CL2 is set at 0 V. That is, in the present embodiment, when information written in the memory cell array 10 is erased, the first protection transistors 150 and the second protection transistors 152 are turned off-state. When the information written in the memory cell array 10 is erased, the third control line CL3 is set at 0 V. That is, when the information written in the memory cell array 10 is erased, the bypass transistors 158 are turned off-state. The potential of the bit lines BL, the potential of the source line SL, the potential of the first word lines WL1, the potential of the second word lines WL2 and the potential of the wells 26 are the same as the potentials of the respective parts in the erasing method of the nonvolatile semiconductor memory device according to the first embodiment.

Because of the first protection transistors 150 and the second protection transistors 152 being off-state, the bit lines BL are electrically disconnected from the column decoder 12, as in the fifth embodiment, and the second word lines WL2 are electrically disconnected from the second row decoder 16, as in the nonvolatile semiconductor memory device according to the fifth embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information written in the memory cell array 10 can be erased in the same way as in the erasing method of the nonvolatile semiconductor memory device according to the fifth embodiment.

[h] Eighth Embodiment

The nonvolatile semiconductor memory device according to an eighth embodiment, the reading method, the writing method and the erasing method thereof will be explained with reference to FIG. 37 and FIG. 38. FIG. 37 is the circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the seventh embodiments are represented by the same reference numbers not to repeat or to simplify their explanation.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 37.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the bypass transistors 158 are provided respectively between the respective first word lines WL1 and the respective second word lines WL2, and when information is written into the memory cell transistors MT, the second row decoder 16 is electrically disconnected from the second word lines WL2, the first word lines WL1 and the second word lines WL2 are electrically connected by the bypass transistors 158, and voltage is applied to the first word lines WL1 and the second word lines WL2 by the first row decoder (voltage application circuit) 14.

As illustrated in FIG. 37, the respective bit lines BL are connected to the column decoder 12 via the first protection transistors 150. In other words, one of the source and the drain of the first protection transistors 150 is connected to the bit

line BL, and the other of the source and the drain of the first protection transistors **150** is connected to the column decoder **12**.

The gates of the respective first protection transistors **150** are connected to the first control circuit **154** via the first control line CL1. The respective first protection transistors **150** are controlled by the first control circuit **154**.

The film thickness of the gate insulation film (not illustrated) of the first protection transistors **150** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. The film thickness of the gate insulation film of the first protection transistors **150** is set relatively thick, as is the film thickness of the gate insulation film **28b** of the selecting transistors ST so as to sufficiently ensure the withstand voltage of the first protection transistors **150**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the film thickness of the gate insulation film (not illustrated) of the first protection transistors **150** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. However, the film thickness of the gate insulation film of the first protection transistor **150** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the first protection transistors **150** can be set suitably corresponding to a working voltage.

The respective second word lines WL2 are connected to the second row decoder **16** via the second protection transistors **152**. In other words, one of the source and the drain of the second protection transistors **152** is connected to the second word line WL2, and the other of the source and the drain of the second protection transistors **152** is connected to the second row decoder **16**.

The respective second protection transistors **152** are connected to the second control circuit **154** via the second control line CL2. The respective second protection transistors **152** are controlled by the second control circuit **154**.

The film thickness of the gate insulation film (not illustrated) of the second protection transistors **152** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. The film thickness of the gate insulation film of the first protection transistors **152** is set relatively thick as is the film thickness of the gate insulation film **28b** of the selecting transistors ST so as to sufficiently ensure the withstand voltage of the first protection transistors **152**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the film thickness of the gate insulation film (not illustrated) of the second protection transistors **152** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. However, the film thickness of the gate insulation film of the second protection transistors **152** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the second protection transistors **152** can be set suitably corresponding to a working voltage.

The bypass transistors **158** are provided respectively between the first word lines WL1 and the second word line WL2. In other words, the source and the drain of the bypass transistor **158** is connected to the first word line WL1, and the other of the source and the drain of the bypass transistor **158** is connected to the second word line WL2.

The gates of the respective bypass transistors **158** are connected to the second control circuit **160** via the third control

line CL3. The respective bypass transistors **158** are controlled by the second control circuit **160**.

The film thickness of the gate insulation film (not illustrated) of the bypass transistors **158** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. The film thickness of the gate insulation film of the bypass transistors **158** is set relatively thick, as is the film thickness of the gate insulation film **28b** of the selecting transistors ST so as to sufficiently ensure the withstand voltage of the bypass transistors **158**.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the film thickness of the gate insulation film (not illustrated) of the bypass transistors **158** is set equal to the film thickness of the gate insulation film **28b** of the selecting transistors ST. However, the film thickness of the gate insulation film of the bypass transistors **158** may be set equal to the film thickness of the gate insulation film of the high withstand voltage transistors. The film thickness of the gate insulation film of the bypass transistors **158** can be set suitably corresponding to a working voltage.

In the present embodiment, the first word lines WL1 are connected to the second word lines WL2 via the bypass transistors **158** so that when information is written into the memory cell transistors MT, high voltage is applied to the second word lines WL2.

Thus the nonvolatile semiconductor memory device according to the present embodiment is constituted.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that, as illustrated in FIG. **37**, the memory cell transistors MT of the respective rows are connected to the source lines SL associated with the respective rows. The sources of the memory cell transistors MT present in the rows adjacent to each other may be connected to the common source line SL, as in the nonvolatile semiconductor memory device according to an eleventh embodiment which will be detailed later with reference to FIG. **65**. The sources of the memory cell transistors MT present in rows adjacent to each other are connected by the common source line SL, whereby the area of the memory cell array region **2** can be reduced, and the nonvolatile semiconductor memory device can be downsized. The number of the source lines SL to be controlled by the third row decoder **18** can be decreased, which can simplify the third row decoder **18**.

(Operations of the Nonvolatile Semiconductor Memory Device)

Then, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **38**. FIG. **38** is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. **38**, the voltages in the parentheses are the potential of the non-selected lines. In FIG. **38**, F indicates floating.

(Reading Method)

The reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **38**.

In the present embodiment, when information written in the memory cell transistors MT is read, the potential of the first control line CL1 is set at 5 V, and the potential of the second control line CL2 is set at 5 V. That is, in the present embodiment, when information written in the memory cell transistors MT is read, the first protection transistors **150** and the second protection transistors **152** are turned on-state.

When information written in the memory cell transistors MT is read, the potential of the third control line CL3 is set at 0 V. That is, in the present embodiment, when information written in the memory cell transistors MT is read, the bypass transistors 158 are turned off-state.

The potential of the bit lines BL, the potential of the source lines SL, the potential of the first word lines WL1, the potential of the second word lines WL2 and the potential of the wells 26 are the same as the potentials of the respective parts in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

Because of the first protection transistors 150 and the second protection transistors 152 being on-state, the bit lines BL are electrically connected to the column decoder 12, as in the nonvolatile semiconductor memory device according to the first embodiment, and the second word lines WL2 are electrically connected to the second row decoder 16, as in the nonvolatile semiconductor memory device according to the first embodiment. Because of the bypass transistors 158 being off-state, the second word lines WL2 are electrically disconnected from the source lines SL, as in the nonvolatile semiconductor memory device according to the first embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information written in the memory cell transistors MT can be read in the same way as in the reading method of the nonvolatile semiconductor memory device according to the first embodiment.

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 38.

When information is written into the memory cell transistors MT, the potentials of the respective parts are set as follows.

That is, the potential of the bit line BL connected to a memory cell MC to be selected is set at 0 V. On the other hand, the potential of the bit lines BL other than the selected bit line BL is floating.

The potential of the source line SL connected to the memory cell MC to be selected is set at, e.g., 5 V (the first potential). On the other hand, the potential of the source lines SL other than the source line SL to be selected is set at 0 V or floating.

The potential of the word line WL1 connected to the memory cell MC to be selected is set at, e.g., 9 V (the second potential). On the other hand, the potential of the first word lines WL1 other than the selected first word line WL1 is set at 0 V.

The bypass transistors 158 are turned on-state, whereby the first word lines WL1 and the second word lines WL2 are electrically connected. Thus, the potential of the second word line WL2 connected to the memory cell MC to be selected becomes equal to the potential of the first word line WL1. The potential of the selected word line WL1 is, e.g., 9 V (the second potential) here, and the potential of the selected second word line WL2 also becomes, e.g., 9 V (the second potential). The potential of the second word lines WL2 other than the selected second word line WL2 becomes 0 V (ground voltage).

The potential of the first control line CL1 is set at, e.g., 5 V. The potential of the second control line CL2 is set at, e.g., 0 V. That is, in the present embodiment, when information is written into the memory cell transistors MT, the first protection transistors 150 are turned on-state, and the second protection transistors 152 are turned off-state.

The potential of the third control line CL3 is set at, e.g., 10 V (the third potential). The potential (the third potential) of

the third control line CL3 is set higher than the second potential which is the potential of the selected first word line WL1 and the selected second word line WL2. The potential (the third potential) of the third control line CL3 is set higher than the potential (the second potential) of the selected first word line WL1 and the selected second word line WL2 so as to set on-state the bypass transistors 158.

The potential of the wells 26 is 0 V.

In the present embodiment, when information is written into the memory cell transistors MT, voltage is applied to the first word lines WL1 and the second word lines WL2 by the first row decoder 14 of a high voltage circuit, whereby relatively high voltage can be applied to the select gates 30b of the selecting transistors ST. Thus, according to the present embodiment, the current flowing in the channels of the selecting transistors ST can be increased, and the write speed can be increased. When information is written into the memory cell transistors MT, the second protection transistors 152 are turned off-state, whereby the second row decoder 16 of a low voltage circuit is electrically disconnected from the second word lines WL2. Thus, according to the present embodiment, when information is written into the memory cell transistors MT, the second row decoder 16 of a low voltage circuit is prevented from being broken.

(Erasing Method)

The erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 38.

In the present embodiment, when information written in the memory cell array 10 is erased, the potential of the first control line CL1 is set at 0 V, and the potential of the second control line CL2 is set at 0 V. That is, in the present embodiment, when information written in the memory cell array 10 is erased, the first protection transistors 150 and the second protection transistors 152 are turned off-state. When information written in the memory cell array 10 is erased, the potential of the third control line CL3 is set at 0 V. That is, in the present embodiment, when information written in the memory cell array 10 is erased, the bypass transistors 158 are turned off-state. The potential of the bit lines BL, the potential of the source lines SL, the potential of the first word lines WL1, the potential of the second word lines WL2 and the potential of the wells 26 are the same as the potential of the respective parts in the erasing method of the nonvolatile semiconductor memory device according to the first embodiment.

Because of the first protection transistors 150 and the second protection transistors 152 being off-state, the bit lines are electrically disconnected from the column decoder 12, as in the fifth embodiment, and the second word lines WL2 are electrically disconnected from the second row decoder 16, as in the nonvolatile semiconductor memory device according to the fifth embodiment. Thus, in the nonvolatile semiconductor memory device according to the present embodiment, information written in the memory cell array 10 can be erased in the same way as in the erasing method of the nonvolatile semiconductor memory device according to the fifth embodiment.

[i] Ninth Embodiment

The nonvolatile semiconductor memory device according to a ninth embodiment and its writing method will be explained with reference to FIG. 39 and FIG. 40. FIG. 39 is a sectional view of the nonvolatile semiconductor memory device according to the present embodiment. FIG. 40 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory

device according to the present embodiment. In FIG. 40, the voltages in the parentheses are the potential of the non-selected lines. In FIG. 40, F indicates floating. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the eighth embodiments are represented by the same reference numbers not to repeat or to simplify their explanation.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 39.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that a P-type dopant impurity is implanted in a region where an N-type source diffused layer 36a is formed, whereby a P-type impurity diffused layer 35 is formed.

As illustrated in FIG. 39, in the region containing the region where the N-type source diffused layer 36a is formed, the P-type dopant impurity is implanted. Thus, the P-type impurity diffused layer 35 is formed in the region containing the region where the N-type source diffused layer 36a is formed.

In the present embodiment, the P-type impurity diffused layer 35 is formed in the region containing the region where the N-type source diffused layer 36a is formed for the following reason.

That is, the P-type impurity diffused layer 35 formed in the region containing the region where the N-type source diffused layer 36a is formed suppresses the expansion of the depletion layer from the N-type source diffused layer 36a. The expansion of the depletion layer from the N-type source diffused layer 36a is suppressed, whereby the electric field intensity near the N-type source diffused layer 36a is intensified, and the carriers can be abruptly accelerated near the N-type source diffused layer 36a. In the present embodiment, the carriers can be abruptly accelerated, whereby the write speed of information into the memory cell transistors MT can be increased.

The P-type dopant impurity is not implanted in the regions where the source/drain diffused layer 36b, 36c of the selecting transistor ST are formed, whereby the selecting transistor ST is never influenced by the P-type dopant impurity. Thus, the threshold voltage of the selecting transistor ST never rises, and the selecting transistor ST is operative at high speed.

(Reading Method)

The reading method of the nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that a voltage V_r , which is higher than a power supply voltage V_{cc} of the logic circuit is applied to the first word lines WL1.

In the present embodiment, because of the P-type impurity diffused layer 35 is formed in the region which contains the N-type source diffused layer 36a of the memory cell transistor MT, the threshold voltage of the memory cell transistor MT is relatively high. Accordingly, when the voltage V_{cc} which is relatively low is applied to the first word line WL1, there is a risk that sufficient current might not flow between the source and the drain of the memory cell transistor MT.

Thus, in the present embodiment, when information written in the memory cell transistors MT is read, the voltage V_r , which is higher than the power supply voltage V_{cc} of the logic circuit is applied to the first word lines WL1. The voltage V_r , which is relative high is applied to the first word lines WL1, whereby sufficient current can be flowed between the sources and the drains of the memory cell transistors MT, and information written in the memory cell transistors MT can be stably read.

The nonvolatile semiconductor memory device according to a tenth embodiment, the reading method, the writing method and the erasing method thereof, and the method for manufacturing the nonvolatile semiconductor memory device will be explained with reference to FIGS. 41 to 64. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the ninth embodiments are represented by the same reference numbers not to repeat or to simplify their explanation.

(Nonvolatile Semiconductor Memory Device)

First, the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIGS. 41 to 43. FIG. 41 is the circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment.

The circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment is the same as the circuit diagram of the nonvolatile semiconductor memory device described above with reference to FIG. 1.

That is, as illustrated in FIG. 41, the nonvolatile semiconductor memory device according to the present embodiment comprises memory cells MC each including a selecting transistor ST and a memory cell transistor MT connected to a selecting transistor ST. The sources of the selecting transistors ST are connected to the drains of the memory cell transistors MT. More specifically, the source of the selecting transistor ST and the drain of the memory cell transistor MT are integrally formed of one impurity diffused layer.

A plurality of the memory cells MC are arranged in a matrix. The memory cell array 10 is formed of the plural memory cells MC arranged in the matrix.

The drains of a plurality of the selecting transistors ST present in one and the same column are commonly connected to a bit line BL.

The control gates of a plurality of the memory cell transistors MT present in one and the same row are commonly connected by the first word line WL1.

The select gates of a plurality of the selecting transistors ST present in one and the same row are commonly connected by the second word line WL2.

The sources of a plurality of the memory cell transistors MT present in one and the same row are commonly connected by a source line SL.

The bit lines BL commonly connecting the selecting transistors ST are connected to the column decoder 12. The column decoder 12 is for controlling the potential of the plural bit lines BL commonly connecting the drains of the selecting transistors ST. The sense amplifier 13 for detecting current flowing in the bit lines BL is connected to the column decoder 12. The column decoder 12 is formed of a low voltage circuit, which is operative at relatively low voltage. The low voltage circuit is a circuit whose withstand voltage is relatively low but is operative at high speed. The gate insulation film (not illustrated) of the transistors (not illustrated) of the low voltage circuit is formed relatively thin. Accordingly, the transistors of the low voltage circuit used in the column decoder 12 are operative at relative high speed. The column decoder 12 is formed of a low voltage circuit in the present embodiment, because it is not necessary to apply high voltage to the drains of the selecting transistors ST, but it is preferably to operate the selecting transistors ST at high speed when information written in the memory cell transistors MT is read. In the present embodiment, in which the column decoder 12 is formed of a low voltage circuit, the selecting transistors ST

can operate at relatively high speed, and resultantly the non-volatile semiconductor memory device can operate at high read speed.

The plural first word lines WL1 commonly connecting the control gates of the memory cell transistors MT are connected to the first row decoder (voltage application circuit) 14. The first row decoder 14 is for controlling the potentials of the respective plural first word lines WL1 commonly connecting the control gates of the memory cell transistors MT. The first row decoder 14 is formed of a high voltage circuit (high withstand voltage circuit). The high voltage circuit is a circuit whose operation speed is relatively slow but whose withstand voltage is relatively high. The gate insulation film (not illustrated) of the transistors of the high voltage circuit is formed relatively thick so as to ensure sufficient withstand voltage. Accordingly, the transistors of the high voltage circuit have operation speed which is slow in comparison with the operation speed of the transistors of the low voltage circuit. The first row decoder 14 comprises a high voltage circuit in the present embodiment so that when information is written into the memory cell transistors MT or when information written in the memory cell transistors MT is erased, high voltage is applied to the first word lines WL1. When information written in the memory cell transistors MT is read, the power supply voltage V_{cc} is constantly applied to the first word lines WL1. Thus, the relative slow operation speed of the high voltage circuit used in the first row decoder 14 causes no special problem.

The second word lines WL2 commonly connecting the select gates of the selecting transistors ST are connected to the second row decoder 16. The second row decoder 16 is for controlling the potential of the plural second word lines WL2 commonly connecting the select gates of the selecting transistors ST. The second row decoder 16 is formed of a low voltage circuit (low withstand voltage circuit). The second row decoder 16 is formed of a low voltage circuit in the present embodiment because it is not necessary to apply high voltage to the select gates of the selecting transistors ST, but it is important to operate the selecting transistors ST at high speed. In the present embodiment, in which the second row decoder 16 is formed of a low voltage circuit, the selecting transistors ST are operative at relatively high speed, and resultantly, the nonvolatile semiconductor memory device can operate at high read speed.

The plural source lines SL commonly connecting the sources of the memory cell transistors MT are connected to the third row decoder 18. The third row decoder 18 is for controlling the potential of the plural source lines SL commonly connecting the sources of the memory cell transistors MT. The third row decoder 18 is formed of a high voltage circuit (high withstand voltage circuit). The third row decoder 18 is formed of a high voltage circuit in the present embodiment because the high voltage is applied to the source lines SL when information is written into the memory cell transistors MT. When information written in the memory cell transistors MT is read, as will be described, the source lines SL are constantly grounded. Thus, the relatively slow operation speed of the third row decoder 18 makes no special problem.

Then, the structure of the memory cell array of the non-volatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 42 and FIG. 43. FIG. 42 is a plan view of the memory cell array of the nonvolatile semiconductor memory device according to the present embodiment. FIG. 43 is the sectional view along the D-D' line in FIG. 42.

On a semiconductor substrate 20, device isolation regions 22 for defining device regions 21 are formed.

In the semiconductor substrate 20 with the device isolation regions 22 formed on, an N-type buried diffused layer 24 is formed. The upper part of the N-type buried diffused layer 24 is P-type wells 26.

On the semiconductor substrate 20, gate electrodes 164 are formed with charge storage layers 162 of, e.g., ONO film formed therebetween. The ONO film forming the charge storage layers 162 is formed of the first silicon oxide film 166, a silicon nitride film 168 formed on the first silicon oxide film 166, and the second silicon oxide film 170 formed on the silicon nitride film 168.

The gate electrodes 164 of the memory cell transistors MT present in one and the same row are commonly connected. In other words, the first word lines WL1 commonly connecting the gate electrodes 164 are formed on the semiconductor substrate 20 with the charge storage layer 162 formed therebetween.

On the semiconductor substrate 20, the gate electrodes 172 of the selecting transistors ST are formed in parallel with the gate electrodes 164 of the memory cell transistors MT. The gate electrodes 172 of the selecting transistors ST present in one and the same row are commonly connected. In other words, the second word lines WL2 commonly connecting the gate electrodes 172 are formed with a gate insulation film 174 formed therebetween on the semiconductor substrate 20. The gate insulation film 174 of the selecting transistors ST is, e.g., about 5-7 nm. That is, the film thickness of the gate insulation film 174 of the selecting transistors ST is set relatively thin.

In the nonvolatile semiconductor memory device according to the first to the ninth embodiment, the gate insulation film 28b of the selecting transistors ST and the tunnel insulation film 28a of the memory cell transistors MT are formed one and the same insulation film, and the film thickness of the gate insulation film 28b of the selecting transistors ST and the film thickness of the tunnel insulation film 28a of the memory cell transistors MT are equal to each other. Accordingly, in the first to the ninth embodiments, the current flowing in the selecting transistors ST is not necessarily large enough, and the operation speed of the selecting transistors ST is not necessarily high enough.

In the present embodiment, however, the film thickness of the gate insulation film 174 of the selecting transistors ST is set relatively thin, whereby the current flowing in the channels of the selecting transistors ST can be increased, and the operation speed of the selecting transistors ST can be increased.

In the semiconductor substrate 20 on both sides of the gate electrode 164 of memory cell transistor MT and in the semiconductor substrate 20 on both sides of the gate electrode 164 of selecting transistor ST, N-type impurity diffused layers 36a, 36b, 36c are formed.

The impurity diffused layer 36b forming the drain of the memory cell transistor MT, and the impurity diffused layer 36b forming the source of the selecting transistor ST are one and the same impurity diffused layer 36b.

On the side wall of the gate electrode 164 of the memory cell transistor MT, a sidewall insulation film 37 is formed.

On the side wall of the gate electrode 172 of the selecting transistor ST, the sidewall insulation film 37 is formed.

On the source region 36a of the memory cell transistor MT, on the drain region 38c of the selecting transistor ST, in the upper part of the gate electrode 164 of the memory cell transistor MT and in the upper part of the gate electrode 172 of the selecting transistor ST, silicide layers 38a-38d of, e.g., cobalt silicide are respectively formed. The silicide layer 38a

on the source electrode **36a** functions as the source electrode. The silicide layer **38c** on the drain electrode **36c** functions as the drain electrode.

Thus, the memory cell transistors MT each including the charge storage layer **162**, the gate electrode **164** and the source/drain diffused layers **36a**, **36b** are constituted.

Thus, the selecting transistors ST each including the gate electrode **172** and the source/drain diffused layers **36b**, **36c** are constituted. The selecting transistors ST are NMOS transistors. In the present embodiment, NMOS transistors, whose operation speed is higher than PMOS transistors, are used as the selecting transistors ST, which can contribute to the operation speed increase.

On the semiconductor substrate **20** with the memory cell transistors MT and the selecting transistors ST formed on, an inter-layer insulation film **40** of a silicon nitride film (not illustrated) and a silicon oxide film (not illustrated) is formed.

In the inter-layer insulation film **40**, contact holes **42** are formed respectively down to the source electrode **38a** and the drain electrode **38b**.

In the contact holes **42**, conductor plugs **44** of, e.g., tungsten are buried.

On the inter-layer insulation film **40** with the conductor plugs **44** buried in, interconnections (the first metal interconnection layer) **46** is formed.

On the inter-layer insulation film **40** with the interconnections **46** formed on, an inter-layer insulation film **48** is formed.

In the inter-layer insulation film **48**, a contact hole **50** is formed down to the interconnection **46**.

In the contact hole **50**, a conductor plug **52** of, e.g., tungsten is buried.

On the inter-layer insulation film **48** with the conductor plug **52** buried in, an interconnection (the second metal interconnection layer) **54** is formed.

On the inter-layer insulation film **48** with the interconnection **54** formed on, an inter-layer insulation film **56** is formed.

In the inter-layer insulation film **56**, a contact hole (not illustrated) is formed down to the interconnection **54**.

In the contact hole (not illustrated), a conductor plug (not illustrated) of, e.g., tungsten is formed.

On the inter-layer insulation film **56** with the conductor plug (not illustrated) buried in, an interconnection (the third metal interconnection layer) **62** is formed.

Thus, the memory cell array **10a** (see FIG. **41**) of the nonvolatile semiconductor memory device according to the present embodiment is constituted.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that, as illustrated in FIG. **41**, the memory cell transistors of the respective rows are connected to the source lines SL associated with the respective rows. However, the sources of the memory cell transistors MT present in rows adjacent to each other may be connected by the common source line SL, as in the nonvolatile semiconductor memory device according to an eleventh embodiment which will be detailed later with reference to FIG. **65**. The plan view of FIG. **42** correspond to the case that the sources of the memory cells MT present in rows adjacent to each other are connected by the common source line SL. The sources of the memory cell transistors MT present in rows adjacent to each other are connected by the common source line SL, whereby the area of the memory cell array region **2** can be reduced, and the nonvolatile semiconductor memory device can be downsized. The number of the source lines SL to be controlled by the third row decoder **18** can be decreased, which simplifies the third row decoder **18**.

(Operations of Nonvolatile Semiconductor Memory Device)

Next, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **44**. FIG. **44** is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. **44**, the voltages in the parentheses are the potentials of the non-selected lines.

(Reading Method)

First, the reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. **44**.

When information written in the memory cell transistors MT is read, the potentials of the respective parts are set as follows. That is, the potential of the bit line BL connected to a memory cell MC to be selected is set at V_{cc} (the first potential). The potential of the bit lines BL other than the selected bit line BL is set at 0 V. The potential of all the source lines SL is set at 0 V. The potential of the first word lines WL1 on standby for read is set constantly V_{cc} . The potential of the second word line WL2 connected to the memory cell MC to be selected is set at V_{cc} . The potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V. The potentials of the wells **26** is set at 0 V. In the present embodiment, the potential of the source lines SL on standby for read is set at 0 V, and the potential of the first word lines WL1 on standby for read is constantly set at V_{cc} , whereby information written in the memory cell transistors MT can be read only by controlling the potential of the bit lines BL and the potential of the second word lines WL2. In the present embodiment, in which the column decoder **12** for controlling the potential of the bit lines BL comprises a low voltage circuit as described above, whereby the bit lines BL can be controlled at high speed. The second row decoder **16** for controlling the potential of the second word lines WL2 is formed of a low voltage circuit as described above, whereby the second word lines WL2 can be controlled at high speed. Furthermore, the gate insulation film **174** of the selecting transistors ST is set relatively thin, whereby the selecting transistors ST are operative at high speed. Thus, according to the present embodiment, information written in the memory cell transistors MT can be read at high speed.

When information is written into the memory cell transistor MT, i.e., information in the memory cell transistor MT is "0", charges are stored in the charge storage layer **162** of the memory cell transistor MT. In this case, no current flows between the source diffused layer **36a** of the memory cell transistor MT and the drain diffused layer **36c** of the selecting transistor ST, and no current flows in the selected bit line BL. In this case, the information in the memory cell transistors MT is judged to be "0".

On the other hand, when information written in the memory cell transistor has been erased, i.e., the information of the memory cell is "1", charges are not stored in the charge storage layer **162** of the memory cell transistor MT. In this case, current flows between the source diffused layer **36a** of the memory cell transistor MT and the drain diffused layer **36c** of the selecting transistor ST, and current flows in the selected bit line BL. The current flows in the selected bit line BL is detected by the sense amplifier **13**. In this case, the information in the memory cell transistor MT is judged to be "1".

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be

explained with reference to FIGS. 44 to 48. FIG. 45 is the time chart of the writing method of the nonvolatile semiconductor memory device according to the present embodiment.

When information is written into the memory cell transistor MT, the potentials of the respective parts are set as follows.

That is, the potential of the bit line BL connected to the memory cell MC to be selected is set at 0 V (ground voltage). On the other hand, the potential of the bit lines BL other than the selected bit line BL is set at V_{cc} .

To the source line SL connected to the memory cell MC to be selected, as illustrated in FIG. 45, the second voltage is applied in pulses. The pulsated second voltage to be applied to the source line SL is, e.g., 5.5 V. On the other hand, the potential of the source lines SL other than the selected source line SL is set at 0 V (ground voltage).

To the first word line WL1 connected to the memory cell MC to be selected, as illustrated in FIG. 45, the first voltage V_{step} which gradually rises is applied. On the other hand, the potential of the first word lines WL1 other than the selected first word line WL1 is set at 0 V (ground voltage).

The potential of the second word lines WL2 connected to the memory cell MC to be selected is set at V_{cc} (the first potential). On the other hand, the potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V (ground voltage).

The potential of all the wells is 0 V (ground voltage).

In the present embodiment, the voltage is applied in pulses to the source line SL of the selected column while the first voltage V_{step} to be applied to the first word line WL1 of the selected row is being gradually increased for the following reason.

That is, when high voltage is applied to the gate electrodes 164 of a memory cell transistor, the electric resistance between the source and the drain of the memory cell transistor MT becomes small. Then, the electric resistance between the source and the drain of the memory cell transistor MT becomes smaller in comparison with the electric resistance between the source and the drain of the selecting transistor ST. Then, a large transverse electric field is applied between the source and the drain of the selecting transistor ST while a sufficient transverse electric field is not applied between the source and the drain of the memory cell transistor MT. Without a sufficient transverse electric field being applied between the source and the drain of the memory cell transistor MT, electrons are not accelerated between the source and the drain of the memory cell transistor MT, and the write speed becomes slow.

In the present embodiment, in the initial stage of the write, relatively low voltage is applied to the first word line WL1 of a selected row, whereby the electric resistance between the source and the drain of the memory cell transistor MT never excessively lowers. Then, when voltage is applied in pulses to the source line SL of the selected column, charges are injected into the charge storage layer 162 of the memory cell transistor MT. Then, when voltage is applied in pulses to the source line SL of the selected column while the voltage of the first word line WL1 of the selected row is being gradually raised, charges are injected into the charge storage layer 162 of the memory cell transistor MT. The first voltage V_{step} to be applied to the first word line WL1 of the selected row gradually rises, but charges to be stored in the charge storage layer 162 are gradually increase, whereby the electric resistance between the source and the drain of the memory cell transistor MT never becomes excessively low. Thus, according to the present embodiment, the write speed of writing information in the memory cell transistor MT can be high.

In the nonvolatile semiconductor memory device according to the present embodiment, hot carriers are generated, and the generated hot carriers are injected into the charge storage layer 162 of a memory cell transistor MT, whereby information is written into the memory cell transistor MT. To make the write by using hot carriers, energy which exceeds a height of the barrier of the silicon oxide film 166 (see FIG. 43) is necessary, and hot carriers is accelerated to above the energy by the potential difference between the source and the drain of the memory cell transistor MT.

FIG. 46 is a graph of the relationships between the difference between the gate voltage of the memory cell transistor and threshold voltage, and shifts of the threshold voltage. The relationships of FIG. 46 were experimentally given. As the conditions for the simulation, the threshold voltage of the selecting transistor ST was 0.8 V, and the voltage to be applied to the gate electrode 172 of the selecting transistor ST was 1.8 V. That is, the voltage to be applied to the gate electrode 172 of the selecting transistor ST was set higher by 1.0 V than the threshold voltage of the selecting transistor ST.

As seen in FIG. 46, with the gate voltage of the memory cell transistor MT set higher by about 4-5 V than the threshold voltage, a shift of the threshold voltage of the memory cell transistor MT becomes maximum, and charges can be most stored in the charge storage layer 162.

The relationships between the difference between the gate voltage of the memory cell transistor MT and the threshold voltage, and shifts of the threshold voltage were given by the experiment made under the above-described conditions. The relationships between the difference between the gate voltage of the memory cell transistor MT and the threshold voltage, and shifts of the threshold voltage have different values depending on the channel length of the selecting transistor ST, the channel length of the memory cell transistor MT, dose of a dopant impurity in the source/drain diffused layers 36a, 36c, etc.

The write operation has been explained by means of the example that, as illustrated in FIG. 45, the voltage to be applied to the selected first word line WL1 is increased in steps, but the voltage to be applied to the selected first word line WL1 is not essentially the voltage illustrated in FIG. 45.

FIG. 47 is the time chart (Part 1) of another example of the writing method of the nonvolatile semiconductor memory device according to the present embodiment.

As illustrated in FIG. 47, it is possible that after voltage has been raised, the voltage is temporarily decreased, and further higher voltage is applied.

FIG. 48 is the time chart (Part 2) of further another example of the writing method of the nonvolatile semiconductor memory device according to the present embodiment.

As illustrated in FIG. 48, the voltage to be applied to the selected first word line WL1 may be continuously raised.

(Erasing Method)

Then, the erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 45.

When information written in the memory cell array 10, the potentials of the respective parts are set as follows.

That is, the potential of all the bit lines BL is set at 0 V (ground voltage). The potential of all the source lines SL is set at 5 V. The potential of all the first word lines WL1 is set at, e.g., -5 V. The potential of the second word lines WL2 is set at 0 V (ground voltage). The potential of all the wells 26 is set at 0 V (ground voltage).

With the potentials of the respective parts being set as above, charges are drawn out of the charge storage layer 162 of the memory cell transistors MT. Thus, no charges are

stored in the charge storage layer **162** of the memory cell transistors MT, and the information in the memory cell transistors MT is erased.

As described above, in the present embodiment, the column decoder **12** for controlling the potential of the bit lines BL commonly connecting the drain diffused layers **36c** of the selecting transistors ST is formed of a low voltage circuit, which is operative at high speed, and the second row decoder for controlling the potential of the second word lines WL2 commonly connecting the select gates **30b** of the selecting transistors ST is formed of a low voltage circuit, which is operative at high speed. Besides, in the present embodiment, in which the film thickness of the gate insulation film **174** of the selecting transistors ST is formed relatively thin, the selecting transistors ST can operate at high speed. Only by controlling the potentials of the bit line BL and the second word lines WL2, information written in the memory cell transistors MT can be read. The bit lines BL and the second word lines WL2 are controlled at high speed, and besides, the selecting transistors ST are operative at high speed, whereby the nonvolatile semiconductor memory device according to the present embodiment can read at high speed information written in the memory cell transistors MT.

(Method for Manufacturing Nonvolatile Semiconductor Memory Device)

Next, the method for manufacturing the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIGS. **49A** to **64**. FIG. **49A** to **64** are sectional views of the nonvolatile semiconductor memory device according to the present embodiment in the steps of the method for manufacturing the nonvolatile semiconductor memory device. FIG. **49A**, FIG. **50A**, FIG. **51A**, FIG. **52A**, FIG. **53A**, FIG. **54A**, FIG. **55A**, FIG. **56A**, FIG. **57A**, FIG. **58A**, FIG. **59A**, FIG. **60A**, FIG. **61** and FIG. **63** illustrate memory cell array region (core region) **2**. The views on the left sides of the drawings of FIG. **49A**, FIG. **50A**, FIG. **51A**, FIG. **52A**, FIG. **53A**, FIG. **54A**, FIG. **55A**, FIG. **56A**, FIG. **57A**, FIG. **58A**, FIG. **59A**, FIG. **60A**, FIG. **61** and FIG. **63** correspond to the section along the E-E' line in FIG. **42**. The views on the right sides of the drawings of FIG. **49A**, FIG. **50A**, FIG. **51A**, FIG. **52A**, FIG. **53A**, FIG. **54A**, FIG. **55A**, FIG. **56A**, FIG. **57A**, FIG. **58A**, FIG. **59A**, FIG. **60A**, FIG. **61** and FIG. **63** correspond to the sections along the D-D' line in FIG. **42**. FIG. **49B**, FIG. **50B**, FIG. **51B**, FIG. **52B**, FIG. **53B**, FIG. **54B**, FIG. **55B**, FIG. **56B**, FIG. **57B**, FIG. **58B**, FIG. **59B**, FIG. **60B**, FIG. **62** and FIG. **64** illustrate the peripheral circuit region **4**. The views on the left sides of the drawings of FIG. **49B**, FIG. **50B**, FIG. **51B**, FIG. **52B**, FIG. **53B**, FIG. **54B**, FIG. **55B**, FIG. **56B**, FIG. **57B**, FIG. **58B**, FIG. **59B**, FIG. **60B**, FIG. **62** and FIG. **64** illustrate the region **6** where the high withstand voltage transistors are to be formed. The view on the left side of the region **6** for the high withstand voltage transistors to be formed in illustrates the region **6N** where the high withstand voltage N-channel transistors are to be formed in. The views on the right side of the region **6N** for the high withstand voltage N-channel transistors to be formed in illustrate the region **6P** where the high withstand voltage P-channel transistors are to be formed. The views on the right side of the region **6P** for the high withstand voltage P-channel transistors to be formed in illustrate the region **6N** where the high withstand voltage N-channel transistors are to be formed. The views on the right sides of the drawings of FIG. **49B**, FIG. **50B**, FIG. **51B**, FIG. **52B**, FIG. **53B**, FIG. **54B**, FIG. **55B**, FIG. **56B**, FIG. **57B**, FIG. **58B**, FIG. **59B**, FIG. **60B**, FIG. **62** and FIG. **64** illustrate the region **8** where the low voltage transistors are to be formed. The views on the left side of the drawings of the region **8** for the

low voltage transistors to be formed in illustrate the region **8N** where the low voltage N-channel transistors are to be formed, and the view of the right side of the drawing of the region **8** for the low voltage transistors to be formed in illustrate the region **8P** where the low voltage P-channel transistors are to be formed.

First, a conductor substrate **20** of, e.g., a P-type silicon substrate is prepared.

Next, a 15 nm-thickness thermal oxide film **64** is formed on the entire surface by, e.g., thermal oxidation.

Then, a 150 nm-thickness silicon nitride film **66** is formed on the entire surface by, e.g., CVD.

Then, a photoresist film (not illustrated) is formed on the entire surface by, e.g., spin coating.

Then, openings (not illustrated) are formed in the photoresist film by photolithography. These openings are for patterning the silicon nitride film **66**.

Then, with the photoresist film as the mask, the silicon nitride film **66** is patterned. Thus, a hard mask **66** of silicon nitride film is formed.

Then, the semiconductor substrate **20** is etched by dry etching with the hard mask **66** as the mask. Thus, trenches **68** are formed in the semiconductor substrate **20** (see FIGS. **49A** and **49B**). The depth of the trenches **68** formed in the semiconductor substrate **20** is, e.g., 300 nm from the surface of the semiconductor substrate **20**.

Next, the exposed parts of the semiconductor substrate **20** are oxidized by thermal oxidation. Thus, silicon oxide film (not illustrated) is formed on the exposed parts of the semiconductor substrate **20**.

Next, as illustrated in FIGS. **50A** and **50B**, a 700 nm-thickness silicon oxide film **22** is formed on the entire surface by high density plasma-enhanced CVD.

Next, as illustrated in FIGS. **51A** and **51B**, the silicon oxide film **22** is polished by CMP until the surface of the silicon nitride film **66** is exposed. Thus, the device isolation regions **22** of silicon oxide film are formed.

Next, thermal process for curing the device isolation regions **22** is made. The thermal processing conditions are, e.g., 900° C. and 30 minutes in a nitrogen atmosphere.

Next, the silicon nitride film **66** is removed by wet etching.

Next, as illustrated in FIGS. **52A** and **52B**, a sacrifice oxide film **69** is grown on the surface of the semiconductor substrate **20** by thermal oxidation.

Then, as illustrated in FIGS. **53A** and **53B**, an N-type dopant impurity is implanted deep in the memory cell array region **2** to form the N-type buried diffused layer **24**. At this time, the N-type dopant impurity is deeply implanted also into the region **6N** where the high withstand voltage N-channel transistors are to be formed to thereby form the N-type buried diffused layer **24**. In the memory cell array region **2**, a P-type dopant impurity is implanted shallower than the buried diffused layer **24** to thereby form a P-type well **26**. In the region **6N** for the high withstand voltage N-channel transistors to be formed in, a P-type dopant impurity is implanted shallower than the buried diffused layer **24** to thereby form a P-type well **72P**.

Then, in the region **6N** for the high withstand voltage N-channel transistors to be formed in, an N-type diffused layer **70** is formed in a frame-shape. The frame-shaped diffused layer **70** is formed from the surface of the semiconductor substrate **20** to the peripheral edge of the buried diffused layer **24**. The P-type well **72P** is surrounded by the buried diffused layer **24** and the diffused layer **70**. Although not illustrated, the P-type well **26** in the memory cell array region **2** as well is surrounded by the buried diffused layer **24** and the frame-shaped diffused layer **70**.

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Next, in the region **6P** for the high withstand voltage P-channel transistors to be formed in, an N-type dopant impurity is implanted to thereby form an N-type well **72N**.

Next, in the region **8N** for the low voltage N-channel transistors to be formed in, a P-type dopant impurity is implanted to thereby form a P-type well **74P**.

Next, in the region **8P** for the low voltage P-channel transistors to be formed in, an N-type dopant impurity is implanted to thereby form an N-type well **74N**.

Next, in the memory cell array region **2**, channel doping is made (not illustrated).

Next, in the region **6N** for the high withstand voltage N-channel transistors to be formed in and in the region **6P** for the high voltage P-channel transistors to be formed in, channel doping is made (not illustrated).

Then, in the region **8N** for the low voltage N-channel transistors to be formed in and the region **8P** for the low voltage P-channel transistors to be formed in, channel doping is made (not illustrated).

Then, the sacrifice oxide film **69** present on the surface of the semiconductor substrate **20** is etched off.

Then, the first silicon oxide film **166** is formed on the entire surface by thermal oxidation.

Next a silicon nitride film **168** is formed on the entire surface by CVD.

Next, the surface of the silicon nitride film **168** is oxidized by thermal oxidation to form the second silicon oxide film **170** on the entire surface.

Thus, an ONO film **162** of the first silicon oxide film **166** of, e.g., a 4 nm-thickness, the silicon nitride film **168** of, e.g., a 5 nm-thickness formed on the first silicon oxide film **166**, the second silicon oxide film **170** of, e.g., a 7 nm-thickness formed on the silicon nitride film **168** is formed (see FIGS. **54A** and **54B**). The ONO film **162** is to be the charge storage layer of the memory cell transistor MT.

Next, the ONO film **162** present in the region **6** for the high withstand voltage transistors to be formed in is etched off.

Then, in the region **6** for the high voltage transistors to be formed in, the gate insulation film **76** of, e.g., a 15 nm-thickness is formed by thermal oxidation (see FIGS. **55A** and **55B**).

Then, the ONO film **162** present in the region for the selecting transistor ST to be formed in is etched off.

Next, on the semiconductor substrate **20** in the region for the selecting transistor ST to be formed in, the gate insulation film **174** of, e.g., a 5-7 nm-thickness is formed by thermal oxidation (see FIGS. **56A** and **56B**).

Then, the ONO film **162** present in the region for the low voltage transistors to be formed in is etched off.

Next, in the region **8** for the low voltage transistors to be formed in, the gate insulation film **78** of, e.g., a 3 nm-thickness is formed by thermal oxidation (see FIGS. **57A** and **57B**).

Next, a polycrystalline silicon film **34** of, e.g., a 180 nm-thickness is formed on the entire surface by, e.g., CVD.

Next, the polycrystalline silicon film **34** is patterned by photolithography. Thus, the gate electrode **164** of the memory cell transistor MT, which is formed of polycrystalline silicon is formed in the memory cell array region **2**. The gate electrode **172** of the selecting transistor ST, which is formed of polycrystalline silicon is formed in the memory cell array region **2**. The gate electrodes **34c** of the high withstand voltage transistors **110N**, **110P**, which are formed of polycrystalline silicon are formed in the region **6** for the high withstand voltage transistors to be formed in. The gate electrodes **34d** of the low voltage transistors **112N**, **112P**, which are formed of

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the polycrystalline silicon are formed in the region **8** for the low withstand voltage transistors to be formed in.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening (not illustrated) for exposing the region **6N** for the high withstand voltage N-channel transistors to be formed in is formed in the photoresist film by photolithography.

Next, with the photoresist film as the mask, a N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, in the semiconductor substrate **20** on both sides of the gate electrode **34c** of the high withstand voltage N-channel transistor, N-type lightly doped diffused layer **86** is formed. Then the photoresist film released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening (not illustrated) for exposing the region **6P** for the high withstand voltage P-channel transistors to be formed in is formed in the photoresist film by photolithography.

Next, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, in the semiconductor substrate **20** on both sides of the gate electrode **34c** of the high withstand voltage P-channel transistor, P-type lightly doped diffused layer **88** is formed. Then the photoresist film released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, by photolithography, an opening (not illustrated) for exposing the region **8N** for the low voltage N-channel transistors to be formed in is formed in the photoresist film.

Then, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage N-channel transistor, an N-type lightly doped diffused layer **90** is formed. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, by photolithography, an opening (not illustrated) for exposing the region **8P** for the low voltage P-channel transistors to be formed in is formed in the photoresist film.

Then, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage P-channel transistor, a P-type lightly doped diffused layer **92** is formed. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, an opening (not illustrated) for exposing the memory cell array region **2** is formed in the photoresist film by photolithography.

Then, by ion implantation with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. The conditions for the ion implantation are as follows. The dopant impurity is, e.g., arsenic. The acceleration energy is, e.g., 20 keV. The dose is, e.g., 1×10^{14} - 1×10^{15} . Thus, in the semiconductor substrate **20** on both sides of the gate electrode **164** and in the semiconductor substrate **20** on both sides of the gate electrode **172**, impurity diffused layers **31a-31c** are formed. Then, the photoresist film is released (see FIGS. **58A** and **58B**).

Next, a 100 nm-thickness silicon oxide film **93** is formed by, e.g., CVD.

Then, the silicon oxide film **93** is anisotropically etched by dry etching. Thus, the sidewall insulation film **93** of silicon

oxide film is formed on the side walls of the gate electrodes **164** of the memory cell transistors MT. On the side walls of the gate electrodes **172** of the selecting transistors ST, the sidewall insulation film **93** of silicon oxide film is formed. On the side walls of the gate electrodes **34c**, the sidewall insulation film **93** of silicon oxide film is formed. On the side walls of the gate electrodes **34d**, the sidewall insulation film **93** of silicon oxide film is formed.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, openings (not illustrated) for exposing the regions **6N** for the high withstand voltage N-channel transistors to be formed in are formed in the photoresist film by photolithography.

Then, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, in the semiconductor substrate **20** on both sides of the gate electrodes **34c** of the high withstand voltage N-channel transistors, an N-type heavily doped diffused layer **94** is formed. The N-type lightly-doped diffused layer **86** and the N-type heavily doped diffused layer **94** form the N-type source/drain diffused layers **96** of the LDD structure. Thus, the high withstand voltage N-channel transistors **110N** each including the gate electrode **34c** and the source/drain diffused layer **96** are formed. The high withstand voltage N-channel transistors **110N** are used in the high voltage circuit (high withstand voltage circuit). Then, the photoresist film is released.

Then, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, an opening (not illustrated) for exposing the region **6P** for the high withstand voltage P-channel transistors to be formed in is formed in the photoresist film by photolithography.

Next, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, a P-type heavily doped diffused layer **98** is formed in the semiconductor substrate **20** on both sides of the gate electrode **34c** of the high withstand voltage P-channel transistor. The P-type lightly doped diffused layer **88** and the P-type heavily doped diffused layer **98** form P-type source/drain diffused layers **100** of the LDD structure. Thus, the high withstand voltage P-channel transistor **110P** including the gate electrode **34c** and the source/drain diffused layer **100** is formed. The high withstand voltage P-channel transistor **110P** is used in the high voltage circuit (high withstand voltage circuit). Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Then, an opening (not illustrated) for exposing the region **8N** for the low voltage N-channel transistors to be formed in is formed in the photoresist film by photolithography.

Next, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, an N-type heavily doped diffused layer **102** is formed in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage N-channel transistor. The N-type lightly doped diffused layer **90** and the N-type heavily diffused layer **102** form the N-type source/drain diffused layers **104** of the LDD structure. Thus, the low voltage N-channel transistor **112N** including the gate electrode **34d** and the source/drain diffused layers **104** is formed. The low voltage N-channel transistor **112N** is used in the low voltage circuit. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, by photolithography, an opening (not illustrated) for exposing the region **8P** for the low voltage P-channel transistors to be formed in is formed in the photoresist film.

Then, with the photoresist film as the mask, a P-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, a P-type heavily doped diffused layer **106** is formed in the semiconductor substrate **20** on both sides of the gate electrode **34d** of the low voltage P-channel transistor. The P-type lightly doped diffused layer **92** and the P-type heavily doped diffused layer **106** form P-type source/drain diffused layers **108** of the LDD structure. Thus, the low voltage P-channel transistor **112P** including the gate electrode **34d** and the source/drain diffused layers **108** is formed. The low voltage P-channel transistor **112P** is used in the low voltage circuit. Then, the photoresist film is released.

Next, a photoresist film (not illustrated) is formed on the entire surface by spin coating.

Next, by photolithography, an opening (not illustrated) for exposing the memory cell array region **2** is formed in the photoresist film.

Next, with the photoresist film as the mask, an N-type dopant impurity is implanted into the semiconductor substrate **20**. Thus, an N-type heavily doped diffused layer **33a** is formed in the semiconductor substrate **20** on one side of the gate electrode **164** of the memory cell transistor MT, and in the semiconductor substrate **20** on one side of the gate electrode **172** of the selecting transistor ST, an N-type heavily doped diffused layer **33b** is formed. The N-type lightly doped diffused layer **31a** and the N-type heavily doped diffused layer **33a** form an N-type source diffused layer **36a** of the LDD structure. The N-type lightly doped diffused layer **31c** and the N-type heavily doped diffused layer **33b** form an N-type drain diffused layer **36c** of the LDD structure. The N-type source/drain diffused layer **36b** of the N-type lightly doped diffused layer **31b** is formed. Then, the photoresist film is released.

Thus, the memory cell transistors MT each including the charge storage layer **162**, the gate electrode **164** and the source/drain diffused layers **36a**, **36b** are formed. The selecting transistors ST each including the gate electrode **172** and the source/drain diffused layers **36b**, **36c** are formed (see FIGS. **59A** and **59B**).

Next, a 10 nm-thickness cobalt film is formed on the entire surface by, e.g., sputtering.

Then, by thermal processing is made to react the silicon atoms in the surface of the semiconductor substrate **20** and the cobalt atoms in the cobalt film with each other. The silicon atoms in the surfaces of the gate electrodes **164** and the cobalt atoms in the cobalt film are reacted with each other. The silicon atoms in the gate electrodes **172** and the cobalt atoms in the cobalt film are reacted with each other. The silicon atoms in the surfaces of the gate electrodes **34c**, **34d** and cobalt atoms in the cobalt film are reacted with each other. Thus, the cobalt silicide films **38a**, **38b** are formed on the source/drain diffused layers **36a**, **36c**. The cobalt silicide film **38c** is formed on the gate electrodes **164**. The cobalt silicide film **38d** is formed on the gate electrode **172**. The cobalt silicide film **38e** is formed on the source/drain diffused layers **96**, **100**, **104**, **108**. The cobalt silicide film **38f** is formed on the gate electrodes **34c**, **34d**.

Next, the non-reacted cobalt film is etched off (see FIGS. **60A** and **60B**).

The cobalt silicide film **38b** formed on the drain diffused layers **36c** of the selecting transistors ST function as the drain electrodes.

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The cobalt silicide film **38a** formed on the source diffused layers **36a** of the memory cell transistors MT function as the source electrodes.

The cobalt silicide film **38e** formed on the source/drain diffused layers **96**, **100** of the high withstand voltage transistors **110N**, **110P** functions as the source/drain electrodes.

The cobalt silicide film **38e** formed on the source/drain diffused layers **104**, **108** of the low voltage transistors **112N**, **112P** function as the source/drain electrodes.

Next, as illustrated in FIGS. **61** and **62**, a 20 nm-thickness silicon nitride film **114** is formed on the entire surface by, e.g., CVD. The silicon nitride film **114** functions as an etching stopper.

Then, a 1.6 μm -thickness silicon oxide film **116** is formed on the entire surface by CVD. Thus, the inter-layer insulation film **40** of the silicon nitride film **114** and the silicon oxide film **116** is formed.

Next, the surface of the inter-layer insulation film **40** is planarized by CMP.

Next, by photolithography, the contact holes **42** arriving at the source/drain electrodes **38a**, **38b**, the contact holes **42** arriving at the source/drain electrodes **38e** and the contact holes arriving at the cobalt silicide films **38f** are formed (see FIG. **63** and FIG. **64**).

Next, the barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **44** is formed on the entire surface by, e.g., CVD.

Next, the tungsten film **44** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **40** is exposed. Thus, the conductor plugs **44** of, e.g., tungsten are buried in the contact holes **42**.

Next, by, e.g., sputtering, the layer film **46** of a Ti film, a TiN film, an Al film, a Ti film and a TiN film sequentially laid is formed on the inter-layer insulation film **40** with the conductor plugs **44** buried in.

Next, the layer film **46** is patterned by photolithography. Thus, the interconnections (the first metal interconnection layer) **46** of the layer film are formed.

Next, a silicon oxide film **118** of, e.g., a 720 nm-thickness is formed by, e.g., high density plasma-enhanced CVD.

Next, a silicon oxide film **120** of, e.g., a 1.1 μm -thickness is formed by TEOSCVD. The silicon oxide film **118** and the silicon oxide film **120** form the inter-layer insulation film **48**.

Next, the surface of the inter-layer insulation film **48** is planarized by, e.g., CMP.

Next, the contact holes **50** are formed in the inter-layer insulation film **48** down to the interconnections **46** by photolithography.

Next, the barrier film (not illustrated) of a Ti film of, e.g., a 10 nm-thickness and a TiN film of, e.g., a 7 nm-thickness is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **52** is formed on the entire surface by, e.g., CVD.

Next, the tungsten film **52** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **48** is exposed. Thus, the conductor plugs **52** of, e.g., tungsten are buried in the contact holes **50**.

Next, on the inter-layer insulation film **48** with the conductor plugs **52** buried in, the layer film **52** of a Ti film, a TiN film, an Al film, a Ti film and a TiN film sequentially laid is formed by, e.g., sputtering.

Next, the layer film **54** is patterned by photolithography. Thus, the interconnections (the second metal interconnection layer) **54** of the layer film are formed.

Next, a silicon oxide film **122** is formed by, e.g., high density plasma-enhanced CVD.

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Next, a silicon oxide film **124** is formed by TEOSCVD. The silicon oxide film **122** and the silicon oxide film **124** form the inter-layer insulation film **56**.

Then, by photolithography, the contact holes **58** arriving at the interconnections **54** are formed in the inter-layer insulation film **56**.

Then, the barrier film (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **60** is formed on the entire surface by, e.g., CVD.

Next, the tungsten film **60** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **56** is exposed. Thus, the conductor plugs **60** of, e.g., tungsten are buried in the contact holes **58**.

Next, by sputtering, a layer film **62** is formed on the inter-layer insulation film **56** with the conductor plugs **60** buried in.

Then, the layer film **62** is patterned by photolithography. Thus, the interconnections (the third metal interconnection layer) **62** of the layer film are formed.

Next, a silicon oxide film **126** is formed by, e.g., high density plasma-enhanced CVD.

Next, a silicon oxide film **128** is formed by TEOSCVD. The silicon oxide film **126** and the silicon oxide film **128** form the inter-layer insulation film **130**.

Then, by photolithography, the contact hole **132** arriving at the interconnection **62** is formed in the inter-layer insulation film **130**.

Next, the barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Next, a 300 nm-thickness tungsten film **134** is formed on the entire surface by, e.g., CVD.

Then, the tungsten film **134** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **130** is exposed. Thus, the conductor plug **134** of, e.g., tungsten is buried in the contact hole **132**.

Then, on the inter-layer insulation film **130** with the conductor plug **134** buried in, a layer film **136** is formed by, e.g., sputtering.

Next, the layer film **136** is patterned by photolithography. Thus, the interconnections (the fourth metal interconnection layer) **136** of the layer film are formed.

Next, a silicon oxide film **138** is formed by, e.g., high density plasma-enhanced CVD.

Next, a silicon oxide film **140** is formed by TEOSCVD. The silicon oxide film **138** and the silicon oxide film **140** form the inter-layer insulation film **142**.

Then, by photolithography, the contact holes **143** arriving at the interconnections **136** are formed in the inter-layer insulation film **142**.

Next, the barrier layer (not illustrated) of a Ti film and a TiN film is formed on the entire surface by sputtering.

Then, a 300 nm-thickness tungsten film **146** is formed on the entire surface by, e.g., CVD.

Then, the tungsten film **146** and the barrier film are polished by CMP until the surface of the inter-layer insulation film **142** is exposed. Thus, the conductor plugs **144** of, e.g., tungsten are buried in the contact holes **143**.

Then, by, e.g., sputtering, the layer film **145** is formed on the inter-layer insulation film **142** with the conductor plugs **144** buried in.

Then, the layer film **145** is patterned by photolithography. Thus, the interconnections (the fifth metal interconnection layer) **145** of the layer film are formed.

Then, a silicon oxide film **146** is formed by, e.g., high density plasma-enhanced CVD.

Next, a 1 μm -thickness silicon nitride film **148** is formed by plasma-enhanced CVD.

Thus, the nonvolatile semiconductor memory device according to the present embodiment is manufactured.

The nonvolatile semiconductor memory device according to an eleventh embodiment, and the reading method, the writing method and the erasing method will be explained with reference to FIG. 65 and FIG. 66. FIG. 65 is the circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the tenth embodiments are represented by the same reference numbers not to repeat or to simplify their explanation.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the sources of the memory cell transistors MT present in rows adjacent to each other are connected by a common source line SL.

As illustrated in FIG. 65, a plurality of memory cells MC_n are arranged in the n^{th} row. In the $n+1^{th}$ row, a plurality of memory cells MC_{n+1} are arranged. In the $n+2^{th}$ row, a plurality of memory cells MC_{n+2} are arranged. In the $n+3^{th}$ row, a plurality of memory cells MC_{n+3} are arranged. Similarly, in the $n+m^{th}$ row, a plurality of memory cells MC_{n+m} are arranged.

The sources of the memory cell transistors MT of the memory cells MC_n of the n^{th} row and the sources of the memory cell transistors MT of the memory cells MC_{n+1} of the $n+1^{th}$ row are connected by a common source line SL.

The sources of the memory cell transistors MT of the memory cells MC_{n+2} of the $n+2^{th}$ row and the sources of the memory cell transistors MT of the memory cells MC_{n+3} of the $n+3^{th}$ row are connected by a common source line SL.

That is, in the present embodiment, the sources of the memory cell transistors MT present in rows adjacent to each other are connected by a common source line SL.

The respective source lines are connected to the third row decoder 18.

According to the present embodiment, the sources of the memory cell transistors MT present in the rows adjacent to each other are connected by a common source line SL, whereby the area of the memory cell array region can be reduced, and the nonvolatile semiconductor memory device can be downsized.

According to the present embodiment, the number of the source lines SL to be controlled by the third row decoder 18 can be small, whereby the third row decoder 18 can be simplified.

(Operations of Nonvolatile Semiconductor Memory Device)

Next, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 66. FIG. 66 is the view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 66, the voltages in the parentheses are the potentials of the non-selected lines.

(Reading Method)

First, the reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 66.

When information written in the memory cell transistor MT is read, the potentials of the respective parts are set as follows. That is, the potential of the bit line BL connected to a memory cell MC_n to be selected is set at V_{cc} (the first potential). The potential of the bit lines BL other than the selected bit line is set at 0 V. The potential of all the source

lines SL is set at 0 V. The potential of all the first word line WL1 on standby for read is constantly V_{cc} . The potential of the second word line WL2 connected to the memory cell MC_n to be selected is set at V_{cc} . The potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V. The potential of all the wells 26 is set at 0 V. In the present embodiment, the potential of the source lines SL is set at 0 V on standby for read, and the potential of the first word lines WL1 on standby for read is constantly set at V_{cc} , which permits information written in the memory cell transistor MT to be read only by controlling the potential of the bit lines BL and the potential of the second word lines WL2. In the present embodiment, the column decoder 12 for controlling the potential of the bit lines BL is formed of the low voltage circuit as described above, the bit lines BL can be controlled at high speed. The second row decoder 16 for controlling the potential of the second word lines WL2 is formed of the low voltage circuit, whereby the second word lines WL2 can be controlled at high speed. Furthermore, the gate insulation film 174 of the selecting transistors ST is formed relatively thin, whereby the selecting transistors ST can operate at high speed. Thus, according to the present embodiment, information written in the memory cell transistors MT can be read at high speed.

When information is written into a memory cell transistor MT, i.e., the information in the memory cell transistor is "0", charges are stored in the charge storage layer 162 of the memory cell transistor MT. In this case, no current flows between the source diffused layer 36a of the memory cell transistor MT and the drain diffused layer 36c of the selecting transistor ST, and no current flows in the selected bit line BL. In this case, the information in the memory cell transistor MT is judged to be "0".

On the other hand, when information written in a memory cell transistor MT has been erased, i.e., when the information in the memory cell is "1", no charges are stored in the charge storage layer 162 of the memory cell transistor MT. In this case, current flows between the source diffused layer 36a of the memory cell transistor MT and the drain diffused layer 36c of the selecting transistor ST, and current flows in the selected bit line BL. The current flowing in the selected bit line BL is detected by the sense amplifier 13. In this case, the information in the memory cell transistor MT is judged to be "1".

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 66.

When information is written into a memory cell transistor MT, the potential of the respective parts are set as follows.

That is, the potential of the bit line BL connected to the memory cell MC_n to be selected is set at 0 V (ground voltage). On the other hand, the bit lines BL other than the selected bit line BL is set at V_{cc} .

To the source line SL connected to the memory cell MC_n to be selected, the second voltage in pulses as illustrated in FIG. 45 is applied. The pulsed second voltage to be applied to the source line SL is, e.g., 5 V. On the other hand, the potential of the source lines SL other than the selected source line is set at 0 V (ground voltage).

To the first word line WL1 connected to the memory cell MC_n to be selected, as illustrated in FIG. 45, FIG. 47 and FIG. 48, the first voltage V_{step} which gradually rises is applied. On the other hand, the potential of the first word lines WL1 other than the selected first word line WL1 is set at 0 V (ground voltage).

The potential of the second word line WL2 connected to the memory cell MC_n to be selected is set at V_{CC} (the first potential). On the other hand, the potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V (ground voltage).

The potential of all the wells is set at 0 V (ground voltage).

Thus, information is written into the memory cell transistor MT of the selected memory cell MC_n.

(Erasing Method)

Next, the erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 66.

When information written in the memory cell array 10 is erased, the potentials of the respective parts are set as follows.

That is, the potential of all the bit lines BL is set at 0 V (ground voltage). The potential of all the source lines SL is set at 5 V. The potential of all the first word line WL is set at, e.g., -5 V. The potential of all the second word lines WL2 is set at 0 V (ground voltage). The potential of all the wells 26 is set at 0 V (ground voltage).

When the potentials of the respective parts are set as above, charges are drawn out of the charge storage layer 162 of the memory cell transistor MT. Thus, the charge storage layer 162 of the memory cell transistor MT stores no charges, and the information in the memory cell transistor MT is erased.

[1] Twelfth Embodiment

The nonvolatile semiconductor memory device according to a twelfth embodiment, and the reading method, the writing method and the erasing method will be explained with reference to FIG. 67 and FIG. 68. FIG. 67 is the circuit diagram of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the eleventh embodiments illustrated in FIGS. 1 to 66 are represented by the same reference numbers not to repeat or to simplify their explanation.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the potential of a plurality of the first word lines WL1 is controlled at once by a voltage application circuit 15.

As illustrated in FIG. 67, a plurality of memory cells MC_n are arranged in the nth row. In the n+1th row, a plurality of memory cell MC_{n+1} are arranged. In the n+2th row, a plurality of memory cells MC_{n+2} are arranged. In the n+3th row, a plurality of memory cells MC_{n+3} are arranged. Similarly, in the n+mth row, a plurality of memory cell MC_{n+m} are arranged.

The sources of the memory cell transistors MT of the memory cells MC_n in the nth row and the sources of the memory cell transistors MT of the memory cell MC_{n+1} in the n+1th row are connected by a common source line SL.

The sources of the memory cell transistors MT of the memory cells MC_{n+2} in the n+2th row and the sources of the memory cell transistors MT of the memory cells MC_{n+3} in the n+3th row are connected by a common source line SL.

That is, in the present embodiment, the sources of the memory cell transistors MT present in rows adjacent to each other are connected by a common source line SL.

The respective source lines are connected to the third row decoder 18.

The memory cell transistors MT of a plurality of memory cells MC_n present in the nth row are connected by the nth row first word line WL1_n.

The memory cell transistors MT of a plurality of memory cells MC_{n+1} present in the n+1th row are connected by the n+1th row first word line WL1_{n+1}.

The memory cell transistors MT of a plurality of memory cells MC_{n+2} present in the n+2th row are connected by the n+2th row first word line WL1_{n+2}.

The memory cell transistors MT of a plurality of memory cells MC_{n+3} present in the n+3th row are connected by the n+3th row first word line WL1_{n+3}.

The voltage to be applied to the nth row first word line WL1_n, the n+1th row first word line WL1_{n+1}, the n+2th row first word line WL1_{n+2} and the n+3th row first word line WL1_{n+3} is controlled at once by the voltage application circuit 15.

The nonvolatile semiconductor memory device according to the present embodiment has been explained here by means of the example that the potential of 4 of the first word lines WL1_n-WL1_{n+4} is controlled at once by the voltage application circuit 15. However, as long as no erroneous operations take place, more of the first word lines may be controlled at once by the voltage application circuit 15. For example, the potential of 8 of the first word lines WL1 may be controlled at once by the voltage application circuit 15. Furthermore, the potential of 16 of the first word lines WL1 may be controlled at once by the voltage application circuit 15.

According to the present embodiment, the potential of a plurality of the first word lines WL1 is controlled at once by the voltage application circuit 15. The voltage application circuit 15 which can control the potential of a plurality of the first word lines WL1 at once has a simpler circuit constitution in comparison with the first row decoder 14 (see FIG. 1) which controls the potential of the respective first word lines WL1. Thus, according to the present embodiment, the nonvolatile semiconductor memory device can be downsized and less costs.

(Operations of Nonvolatile Semiconductor Memory Device)

Then, the operation methods of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 68. FIG. 68 is a view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 68, the voltages in the parentheses are the potentials of the non-selected lines.

(Reading Method)

The reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 68.

When information written in a memory cell transistor MT is read, the potentials of the respective parts are set as follows. That is, the potential of the bit line BL connected to a memory cell MC_n to be selected is set at V_{CC} (the first potential). The potentials of the bit lines BL other than the selected bit line is set at 0 V. The potential of all the source lines SL is set at 0 V.

The potential of the first word lines WL1 on standby for read is constantly V_{CC}. The potential of the first word line WL1 is controlled at once by the voltage application circuit 15. The potential of the second word line WL2 connected to the memory cell MC_n to be selected is set at V_{CC}. On the other hand, the potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V. The potential of all the wells 26 is 0 V. In the present embodiment, the potential of the source lines SL on standby for read is set at 0 V, and the potential of the first word lines WL1 on standby for read is constantly V_{CC}, whereby information written in the memory cell transistors MT can be read only by controlling

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the potential of the bit lines BL and the potential of the second word lines WL2. In the present embodiment, the column decoder 12 for controlling the potential of the bit lines BL is formed of the low voltage circuit as described above, whereby the bit lines BL can be controlled at high speed. The second row decoder 16 for controlling the potential of the second word lines WL2 is formed of the low voltage circuit, whereby the second word lines WL2 can be controlled at high speed. Besides, the gate insulation film 174 of the selecting transistors ST is formed relatively thin, whereby the selecting transistors ST are operative at high speed. Thus, according to the present embodiment, information written in the memory cell transistors MT can be read at high speed.

When information is written into a memory cell transistor MT, i.e., when the information in the memory cell transistor MT is "0", charges are stored in the charge storage layer 162 of the memory cell transistor MT. In this case, no current flows between the source diffused layer 36a of the memory cell transistor MT and the drain diffused layer 36c of the selecting transistor ST, and no current flows in the selected bit line BL. In this case, the information in the memory cell transistor MT is judged to be "0".

On the other hand, when information written in a memory cell transistor MT has been erased, i.e., information in the memory cell is "1", no charges are stored in the charge storage layer 162 of the memory cell transistor MT. In this case, current flows between the source diffused layer 36a of the memory cell transistor MT and the drain diffused layer 36c of the selecting transistor ST, and current flows in the selected bit line BL. The current flowing in the selected bit line BL is detected by the sense amplifier 13. In this case, the information in the memory cell transistor MT is judged to be "1".

(Writing Method)

Next, the writing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 68.

When information is written into a memory cell transistor MT, the potentials of the respective parts are set as follows.

That is, the potential of the bit line BL connected to the memory cell MC_n to be selected is set at 0 V (ground voltage). On the other hand, the potential of the bit lines BL other than the selected bit line BL is set at V_{CC}.

To the source line SL connected to the memory cell MC_n to be selected, the second voltage is applied in pulses as illustrated in FIG. 45. The pulsated second voltage to be applied to the source line SL is, e.g., 5.5 V. On the other hand, the potential of the source lines SL other than the selected source line SL is set at 0 V (ground voltage).

To the first word lines WL1, as illustrated in FIG. 45, FIG. 47 and FIG. 48, the first voltage V_{step} which gradually rises is applied. The potential of the first word lines WL1 is controlled at once by the voltage application circuit 15.

The potential of the second word line WL2 connected to the memory cell MC_n to be selected is set at V_{CC} (the first potential). On the other hand, the potential of the second word lines WL2 other than the selected second word line WL2 is set at 0 V (ground voltage).

The potential of all the wells is 0 V (ground voltage).

Thus, information is written into the memory cell transistor MT of the selected memory cell MC_n.

(Erasing Method)

Next, the erasing method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 68.

When information written in the memory cell array 10 is erased, the potentials of the respective parts are set as follows.

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That is, the potential of all the bit lines BL is set at 0 V (ground voltage). The potential of all the source lines SL is set at 5V. The potential of all the first word lines WL1 is set at, e.g., -5 V. The potential of the first word lines WL1 is controlled at once by the voltage application circuit 15. The potential of the second word lines WL2 is set at 0 V (ground voltage). The potential of the wells 26 is 0 V (ground voltage).

When the potentials of the respective parts are set as above, charges are drawn out of the charge storage layers 162 of the memory cell transistors MT. Thus, no charges are stored in the charge storage layers 162 of the memory cell transistors MT, and information in the memory cell transistors MT is erased.

[m] Thirteenth Embodiment

The nonvolatile semiconductor memory device according to a thirteenth embodiment, and the reading method, the writing method and the erasing method will be explained with reference to FIG. 69. FIG. 69 is the view illustrating the reading method, the writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment. In FIG. 69, the voltages in the parentheses are the potentials of the non-selected lines. The same members of the present embodiment as those of the nonvolatile semiconductor memory device, etc. according to the first to the twelfth embodiments illustrated in FIGS. 1 to 68 are represented by the same reference numbers not to repeat or to simplify their explanation.

(Reading Method)

First, the reading method of the nonvolatile semiconductor memory device according to the present embodiment will be explained with reference to FIG. 69.

When information written in a memory cell transistor MT is read, the potentials of the respective parts are set as follows. That is, the potential of the bit line BL connected to a memory cell MC to be selected is set at V_{CC} (the first potential). On the other hand, the potential of the bit lines BL other than the selected bit line is set at 0 V. The potential of all the source lines SL is set at 0 V. The potential of all the first word lines WL1 on standby for read is constantly V_r. The V_r is a voltage which is higher than a power supply voltage V_{CC} of the logic circuit.

When two kinds of electric power supplies to be supplied to the nonvolatile semiconductor memory device are present, the higher one of the two kinds of electric power supplies can be used to apply a voltage V_r to the first word lines WL1. When the electric power supply to be supplied to the nonvolatile semiconductor memory device is higher than the power supply voltage V_{CC} of the logic circuit, such electric power supply can be used to apply the voltage V_r to the first word lines WL1. The electric power supply to be supplied to the nonvolatile semiconductor memory device may be applied as it is to the first word lines WL1, or the electric power supply to be supplied to the nonvolatile semiconductor memory device may be applied as lowered to the first word lines WL1.

According to the present embodiment, the voltage V_r which is higher than the power supply voltage V_{CC} of the logic circuit is applied to the first word lines WL1, whereby the read current can be increased, and resultantly, the reading time can be decreased.

(Writing Method and Erasing Method)

The writing method and the erasing method of the nonvolatile semiconductor memory device according to the present embodiment may be the same as any one of the tenth to the twelfth embodiment. The writing method and the erasing

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method of the nonvolatile semiconductor memory device according to the present embodiment are not explained here.

[n] A Fourteenth Embodiment

The nonvolatile semiconductor memory device according to a fourteenth embodiment, and its reading method will be explained with reference to FIG. 70. FIG. 70 is a sectional view of the nonvolatile semiconductor memory device according to the present embodiment. The same members of the present embodiment as those of the nonvolatile semiconductor memory device according to the first to the thirteenth embodiments are represented by the same reference numbers not to repeat or to simplify the explanation.

The nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that a P-type dopant impurity is implanted in a region where an N-type source diffused layer 36a is formed, whereby a P-type impurity diffused layer 35 is formed.

As illustrated in FIG. 70, a P-type dopant impurity is implanted in a region containing the region for the N-type source diffused layer 36a is formed. Thus, in the region containing the region for the N-type source diffused layer 36a formed in, the P-type impurity diffused layer 35 is formed.

In the present embodiment, the P-type impurity diffused layer 35 is formed in the region containing the region for the N-type source diffused layer 36a formed in for the following reason.

That is, The P-type impurity diffused layer 35 is formed in the region containing the region for the N-type source diffused layer 36a formed in, whereby the expansion of the depletion layer from the N-type source diffused layer 36a can be suppressed. The expansion of the depletion layer from the N-type source diffused layer 36a is suppressed, whereby the electric field intensity is increased near the N-type source diffused layer 36a, and carriers can be abruptly accelerated near the N-type source diffused layer 36a. In the present embodiment, carriers can be abruptly accelerated, whereby the write speed of writing information in the memory cell transistors MT can be increased.

The P-type dopant impurity is not implanted in the region where the source/drain diffused layers 36b, 36c of the selecting transistor ST are formed, whereby the selecting transistor ST is never influenced by the P-type dopant impurity. Accordingly, the threshold value of the selecting transistor ST never rises, and the selecting transistor ST can operate at high speed.

(Reading Method)

The reading method of the nonvolatile semiconductor memory device according to the present embodiment is characterized mainly in that the voltage V_r , higher than the power supply voltage V_{CC} of the logic circuit is applied to the first word lines WL1.

In the present embodiment, the P-type impurity diffused layer 35 is formed in the region containing the N-type source diffused layer 36a of the memory cell transistor MT, whereby the threshold voltage of the memory cell transistor MT is relatively high. Accordingly, when the V_{CC} , which is a relatively low voltage, is applied to the first word line WL1, there is a risk that sufficient current might not flow between the source and the drain of the memory cell transistor MT.

Thus, in the present embodiment, when information written in a memory cell transistor MT is read, the voltage V_r , higher than the power supply voltage V_{CC} of the logic circuit is applied to the first word line WL1. The relatively high voltage V_r is applied to the first word line WL1, whereby sufficient current can flow between the source and the drain of

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the memory cell transistor MT, and information written in the memory cell transistor MT can be stably read.

The reading method has been explained by means of the example that the voltage V_r , higher than the power supply voltage V_{CC} of the logic circuit is applied to the word line WL1, but in the case that even when the V_{CC} is applied to the first word line WL1, sufficient current flows between the source and the drain of the memory cell transistor MT, the V_{CC} may be applied to the first word line WL1.

Modified Embodiments

The present invention is not limited to the above-described embodiments and can cover other various modifications.

For example, in the sixth embodiment, when information is written into a memory cell transistor MT, the potential (the first potential) of the second word line WL2 is set at 4 V. However, the potential (the first potential) of the second word line WL2 at the time when information is written into a memory cell transistor MT is not limited to 4 V. The potential (the first potential) of the second word line WL2 at the time when information is written into a memory cell transistor MT may be higher than the power supply voltage V_{CC} of the low voltage circuit. A voltage higher than the power supply voltage V_{CC} of the low voltage circuit is applied to the second word line WL2, whereby the current flowing in the channel of the selecting transistor ST can be increased, and the write speed can be increased.

In the seventh embodiment, when information is written into a memory cell transistor MT, the potential (the third potential) of the third control line CL3 is set at 6 V. However, the potential (the third potential) of the third control line CL3 at the time when information is written into a memory cell transistor MT is not limited to 6 V. The potential (the third potential) of the third control line CL3 at the time when information is written into a memory cell transistor MT may be set at a potential higher than the potential (the first potential) of the selected source line SL. A potential higher than the potential (the first potential) of at least the selected source line SL is applied to the third control line CL3, whereby the bypass transistor 158 can be turned on-state.

In the eighth embodiment, when information is written into a memory cell transistor MT, the potential (the third potential) of the third control line CL3 is set at 10 V. The potential of the third control line CL3 at the time when information is written into a memory cell transistor MT is not limited to 10 V.

In the first to the ninth embodiments, the voltage of the respective plural first word lines WL1 is controlled by the first row decoder 14. However, as in the nonvolatile semiconductor memory device according to the twelfth embodiment described above with reference to FIG. 67, the voltage of the plural first word lines WL1 may controlled at once by the voltage application circuit 15. The voltage application circuit 15 (see FIG. 67) for controlling the voltage of the plural first word lines WL1 has a simple circuit structure than the first row decoder 14 for controlling the potential of the respective first word lines WL1. The voltage application circuit which controls the voltage of the plural first word lines WL1 at once is used, whereby the nonvolatile semiconductor memory device can be downsized and costs less.

All examples and conditional language recited herein are intended for pedagogical purposes to aid the reader in understanding the invention and the concepts contributed by the inventor to furthering the art, and are to be construed as being without limitation to such specifically recited examples and conditions, nor does the organization of such examples in the specification relate to a illustrating of the superiority and

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inferiority of the invention. Although the embodiments of the present inventions have been described in detail, it should be understood that the various changes, substitutions, and alterations could be made hereto without departing from the spirit and scope of the invention.

What is claimed is:

1. A nonvolatile semiconductor memory device comprising:

a memory cell array having a plurality of memory cells arranged in a matrix, which include a plurality of selecting transistors and a plurality of memory cell transistors, each of the plurality of memory cell transistors being connected in series to respective one of the plurality of selecting transistors;

a first bit line connecting to drains of a first set of the plurality of the selecting transistors arranged in a first column;

a second bit line connecting to drains of a second set of the plurality of the selecting transistors arranged in a second column;

a first plurality of word lines coupled to a first row decoder controlling a first potential of the first plurality of word lines, the first plurality of word lines includes:

(i) a first word line connecting to gate electrodes of a first set of the plurality of memory cell transistors arranged in a first row and

(ii) a second word line connecting to gate electrodes of a second set of the plurality of memory cell transistors arranged in a second row;

a second plurality of word lines coupled to a second row decoder controlling a second potential of the second plurality of word lines, the second plurality of word lines includes:

(i) a third word line connecting to gate electrodes of a third set of the plurality of selecting transistors arranged in a third row and

(ii) a fourth word line connecting to gate electrodes of a fourth set of the plurality of selecting transistors arranged in a fourth row;

a plurality of source lines coupled to a third row decoder controlling a third potential of the plurality of source lines, the plurality of source lines include:

(i) a first source line connecting to sources of the first set of the plurality of memory cell transistors arranged in the first row and

(ii) a second source line connecting to sources of the second set of the plurality of memory cell transistors arranged in the second row;

a column decoder coupled to the first and second bit lines and controlling a potential of said bit lines,

wherein the column decoder includes a low withstand voltage transistor having a gate insulation film whose thick-

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ness is thinner than a thickness of a gate insulating film of a transistor included in either the first row decoder or the third row decoder,

the second row decoder includes a low withstand voltage transistor having a gate insulation film whose thickness is thinner than the thickness of the gate insulating film of the transistor included in either the first row decoder or the third row decoder and wherein

information is written into a selected one of the memory cells by applying a first voltage which gradually rises selectively to one of the first word lines by the voltage application circuit; and applying a second voltage to one of the source lines by the second row decoder.

2. The nonvolatile semiconductor memory device according to claim 1, wherein

the memory cell transistor includes a floating gate formed over a semiconductor substrate with a tunnel insulation film formed therebetween;

a gate electrode formed over the floating gate with an insulation film formed therebetween; a first impurity diffused layer formed in the semiconductor substrate on one side of the floating gate and forming a source; and a second impurity diffused layer formed in the semiconductor substrate on the other side of the floating gate.

3. The nonvolatile semiconductor memory device according to claim 1, wherein

the memory cell transistor includes a gate electrode formed over a semiconductor substrate with a charge storage layer formed therebetween;

a first impurity diffused layer formed in the semiconductor substrate on one side of the gate electrode and forming a source; and

a second impurity diffused layer formed in the semiconductor substrate on the other side of the gate electrode.

4. The nonvolatile semiconductor memory device according to claim 3, wherein

the charge storage layer includes a first silicon oxide film formed over the semiconductor substrate, a silicon nitride film formed over the first silicon oxide film, and a second silicon oxide film formed over the silicon nitride film.

5. The nonvolatile semiconductor memory device according to claim 1, wherein

the first row decoder controls at once the potential of said plurality of first word lines.

6. The nonvolatile semiconductor memory device according to claim 1, wherein the information is written into a selected one of the memory cells by applying the second voltage at the fixed time of an interval.

7. The nonvolatile semiconductor memory device according to claim 6, wherein the information is written into a selected one of the memory cells by applying the second voltage in pluses.

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